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## **Xyce™ Parallel Electronic Simulator Users' Guide, Version 6.0**

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## Abstract

This manual describes the use of the **Xyce** Parallel Electronic Simulator. **Xyce** has been designed as a SPICE-compatible, high-performance analog circuit simulator, and has been written to support the simulation needs of the Sandia National Laboratories electrical designers. This development has focused on improving capability over the current state-of-the-art in the following areas:

- Capability to solve extremely large circuit problems by supporting large-scale parallel computing platforms (up to thousands of processors). This includes support for most popular parallel and serial computers.
- A differential-algebraic-equation (DAE) formulation, which better isolates the device model package from solver algorithms. This allows one to develop new types of analysis without requiring the implementation of analysis-specific device models.
- Device models that are specifically tailored to meet Sandia's needs, including some radiation-aware devices (for Sandia users only).
- Object-oriented code design and implementation using modern coding practices.

**Xyce** is a parallel code in the most general sense of the phrase — a message passing parallel implementation — which allows it to run efficiently a wide range of computing platforms. These include serial, shared-memory and distributed-memory parallel platforms. Attention has been paid to the specific nature of circuit-simulation problems to ensure that optimal parallel efficiency is achieved as the number of processors grows.

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Written by Alan Hindmarsh, Allan Taylor, Radu Serban.

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**Xyce**'s expression library is based on that inside Spice 3F5 developed by the EECS Department at the University of California.

The EKV3 MOSFET model was developed by the EKV Team of the Electronics Laboratory-TUC of the Technical University of Crete.

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# 1. Introduction

## Welcome to **Xyce**

The **Xyce** Parallel Electronic Simulator is a SPICE-compatible [1] [2] circuit simulator that has been written to support the unique simulation needs of electrical designers at Sandia National Laboratories. It is specifically targeted to run on large-scale parallel computing platforms, but is also available on a variety of architectures including single processor workstations. It aims to support a variety of devices and models specific to Sandia needs, as well as standard capabilities available from current commercial simulators.

## 1.1 Xyce Overview

The **Xyce** Parallel Electronic Simulator project was started in 1999 to support the simulation needs of electrical designers at Sandia National Laboratories and has evolved into a mature platform for large-scale circuit simulation.

**Xyce** includes several unique features. An important driver has been the need to simulate very large-scale circuits (100,000 devices or more) on the transistor level. To this end, scalable algorithms for simulating large circuits in parallel have been developed. In addition **Xyce** includes novel approaches to numerical kernels including model-order reduction, continuation algorithms, time-integration, nonlinear and linear solvers. Also, unlike most SPICE-based codes, **Xyce** uses a differential-algebraic-equation (DAE) formulation, which better isolates the device model package from solver algorithms.

## 1.2 Xyce Capabilities

### 1.2.1 Support for Large-Scale Parallel Computing

**Xyce** is a truly parallel simulation code, designed and written from the ground up to support large-scale parallel computing architectures with up to thousands of processors. This provides **Xyce** the capability to solve large circuit problems with quick enough runtimes to make these simulations practical. **Xyce** uses a message passing parallel implementation, allowing it to run efficiently on a variety of parallel computing platforms. These include serial, shared-memory and distributed-memory parallel. Careful attention has been paid to the specific nature of circuit-simulation problems to ensure optimal parallel efficiency, even as the number of processors increases.

### 1.2.2 Differential-Algebraic Equation (DAE) formulation

**Xyce** has been designed to use a DAE formulation. Among other advantages, this has the benefit of allowing the device models to be nearly independent of the type analysis to be performed, and allows a lot of encapsulation between the models and the solver layers of the source code. In a SPICE-based code, new device functions are created for each type of analysis, such as transient and AC analysis. With **Xyce**'s DAE implementation, this is not necessary. The same device load functions can be used for all analysis types, resulting in faster development time for new types of analysis.

### 1.2.3 Device Model Support

The **Xyce** development team continually adds new device models to **Xyce** to meet the needs of Sandia users. This includes the full set of models that can be found in most SPICE-based codes. For current device availability, consult The **Xyce** Reference Guide [3].



## 1.3 Reference Guide

The **Xyce** User's Guide companion document, the **Xyce** Reference Guide [3], contains detailed information including a netlist reference for **Xyce**-supported input-file commands and elements; a command line reference, which describes the available command line arguments; and quick-references for users of other circuit codes, such as Orcad's PSpice [4].

## 1.4 How to Use this Guide

This guide is designed to enable one to quickly find the information needed to use **Xyce**. It assumes familiarity with basic Unix-type commands, and how Unix manages applications and files to perform routine tasks (e.g., starting applications, opening files, and saving work).

### Typographical conventions

Table 1.1 defines the typographical conventions used in this guide.

**Table 1.1.** Xyce typographical conventions.

Notation	Example	Description
Typewriter text	xmpirun -np 4	Commands entered from the keyboard on the command line or text entered in a netlist.
<b>Bold Roman Font</b>	Set nominal temperature using the <b>TNOM</b> option.	SPICE-type parameters used in models, etc.
Gray Shaded Text	<b>DEBUGLEVEL</b>	Feature that is designed primarily for use by <b>Xyce</b> developers.
[text in brackets]	Xyce [options] <netlist>	Optional parameters.
<text in angle brackets>	Xyce [options] <netlist>	Parameters to be inserted by the user.
<object with asterisk>*	K1 <ind. 1> [<ind. n>*]	Parameter that may be multiply specified.
<TEXT1 TEXT2>	.PRINT TRAN + DELIMITER=<TAB COMMA>	Parameters that may only take specified values.

## 1.5 Third Party License Information

A portion of the DAE time integrator code is derived from Lawrence Livermore National Laboratories' IDA code, which has the following license.

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# 2. Installing and Running Xyce

## Chapter Overview

This chapter describes the basic mechanics of installing and running **Xyce**. It includes the following sections:

- Section 2.1, **Xyce Installation**
- Section 2.2, **Running Xyce**

## 2.1 Xyce Installation

**Xyce** is distributed in two ways: source code and binary installers. At this time, binary installers are available only to Sandia users.

Installation from binary installers is described in the **Xyce** Installation Guide, which should have been provided to you along with the installer.

Installation from source code is described in the **Xyce** Building Guide, and is available on the **Xyce** web site along with the source code.

## 2.2 Running Xyce

While it is possible to connect **Xyce** to graphical interfaces, such as gEDA [5], **Xyce** is not provided with any graphical user interface. It is primarily used as a command-line-only program across all supported platforms, including traditionally “GUI-centered” platforms such as Mac OS X and Microsoft Windows.

This section describes how **Xyce** is run from the command line, for serial and MPI parallel simulations.

### 2.2.1 Command Line Simulation

Running **Xyce** from the command line is straightforward. The scripts `xmpirun` and `runxyce` set up the runtime environment and execute **Xyce**. Depending on whether one uses a version compiled with MPI support or a serial version, there are two ways to begin running **Xyce**:

- Running serial **Xyce**:

```
> runxyce [options] <netlist filename>
```

- Running **Xyce** in parallel:

```
> xmpirun -np <# procs> [options] <netlist filename>
```

where [options] are the command line arguments for **Xyce**. For example, to log output to a file named `sample.log` type:

```
> runxyce -l sample.log <netlist filename>
```

The next example runs parallel **Xyce** on four processors and places the results into a comma separated value file named `results.csv`:

```
> xmpirun -np 4 -delim COMMA -o results.csv <netlist filename>
```

While **Xyce** is running, simulation progress is output to the command line window.

The above examples assume that `<netlist filename>` is either in the current working directory, or includes the path (full or relative) to the netlist file. Enclose the filename in quotation marks (") if the path contains spaces. Help is accessible with the `-h` option.

For MPI runs, `[options]` may also include command line arguments to `mpirun`. Consult the documentation installed with MPI on the user's platform for more details concerning MPI options. The `-np <# procs>` denotes the number of processors to use for the simulation. *NOTE: It is critical that the number of processors used must be smaller than the number of devices and voltage nodes in the netlist.*

Table 2.1 lists appropriate scripts used to run **Xyce** for each supported platform.

**Table 2.1.** Platform scripts for running **Xyce**.

Architecture	OS	Serial Executable	MPI Executable
x86-64	OSX	runxyce	xmpirun
x86 and x86-64	Linux		
x86	Microsoft Windows	runxyce.bat	not available

Sandia HPC platform (TLCC, Glory, Red Sky) users must set several environment variables to run **Xyce**. A system module is available to handle this. To load the **xyce** module, use the command:

```
module load xyce
```

Consult the system documentation for help with submitting jobs on these platforms

<https://computing.sandia.gov>

## Guidance for Running **Xyce** in Parallel

The basic mechanics of running **Xyce** in parallel has been discussed above. For general guidance regarding solver options, partitioning options, and other parallel issues, refer to chapter 10. Distributed memory circuit simulation still contains a number of research issues, so obtaining an optimal simulation in parallel is a bit of an art.

## 2.2.2 Command Line Options

**Xyce** supports a handful of command line options that must be given *before* the netlist filename. Table 2.2 lists **Xyce** core options.

Table 2.2: List of **Xyce** command line arguments.

Argument	Description	Usage	Default
-h	Help option. Prints usage and exits.	-h	-
-v	Prints the version banner and exits.	-v	-
-delim	Set the output file field delimiter.	-delim <TAB COMMA string>	-
-o	Place the results into specified file.	-o <file>	-
-l	Place the log output into specified file.	-l <file>	-
-r	Output a binary rawfile.	-r <file>	-
-a	Use with -r to output a readable (ascii) rawfile.	-r <file> -a	-
-nox	Use the NOX nonlinear solver.	-nox <ON OFF>	on
-info	Output information on parameters.	-info [device prefix] [level] [ON OFF]	-
-linsolv	Set the linear solver.	-linsolv <KLU  SUPERLU AZTECOO>	klu(serial) and aztecoo(parallel)
-param	Print a terse summary of model parameters, device parameters and default values.	-param	-
-syntax	Check netlist syntax and exit.	-syntax	-
-norun	Netlist syntax and topology and exit.	-norun	-
-maxord	Maximum time integration order.	-maxord <1..5>	-
-gui	GUI file output.	-gui	-
-jacobian_test	Jacobian matrix diagnostic.	-jacobian_test	-

While these options are intended for general use, others may exist for new features that are disabled by default, and older, deprecated features. The **Xyce** Reference Guide provides a comprehensive list, including trial and deprecated options.

# 3. Simulation Examples with **Xyce**

## Chapter Overview

This chapter provides several simple examples of **Xyce** usage. An example circuit is provided for each available analysis type.

- Section 3.1, *Example Circuit Construction*
- Section 3.2, *DC Sweep Analysis*
- Section 3.3, *Transient Analysis*



## 3.1 Example Circuit Construction

This section describes how to use **Xyce** to create the simple diode clipper circuit shown in figure 3.2.

**Xyce** only supports circuit creation via netlist editing. **Xyce** supports most of the standard netlist entries common to Berkeley SPICE 3F5 and Orcad PSpice. For users familiar with PSpice netlists, the **Xyce** Reference Guide [3] lists the differences between PSpice and **Xyce** netlists.

### Example: diode clipper circuit

Using a plain text editor (e.g., VI, Emacs, Notepad) but not a word processor (e.g., OpenOffice or Microsoft Word), create a file containing the netlist of figure 3.1. For this example, the file is named `clipper.cir`

The netlist in figure 3.1 illustrates some of the syntax of a netlist input file. Netlists always begin with a title line (e.g. "Diode Clipper Circuit"), and may contain comments (lines beginning with the "\*" character), devices, and model definitions. Netlists must always end with the ".END" statement.

The diode clipper circuit contains two-terminal devices (diodes, resistors, and capacitors), each of which specifies two connecting nodes and either a model (for the diode) or a value (resistance or capacitance). The netlist of figure 3.1 describes the circuit in the schematic of figure 3.2

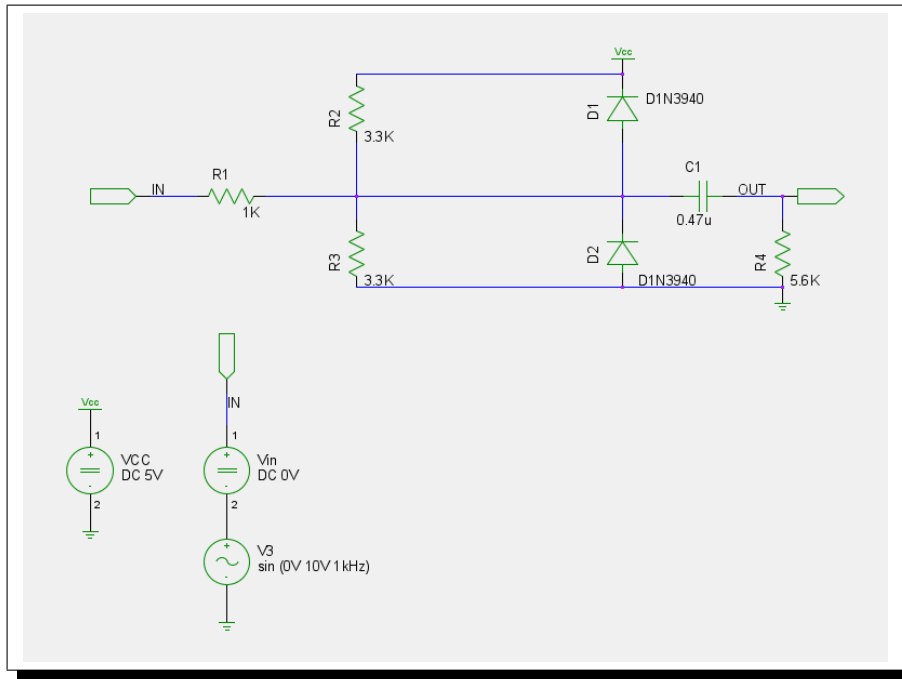
This netlist file is not yet complete and will not run properly using **Xyce** (see section 2.2 for instructions on running **Xyce**) as it lacks an analysis statement. This chapter later describes how to add the appropriate analysis statement and run the clipper circuit.

```

Diode Clipper Circuit
*
* Voltage Sources
VCC 1 0 5V
VIN 3 0 0V
* Diodes
D1 2 1 D1N3940
D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
*
* GENERIC FUNCTIONAL EQUIVALENT = 1N3940
* TYPE: DIODE
* SUBTYPE: RECTIFIER
.MODEL D1N3940 D(
+      IS = 4E-10
+      RS = .105
+      N = 1.48
+      TT = 8E-7
+      CJO = 1.95E-11
+      VJ = .4
+      M = .38
+      EG = 1.36
+      XTI = -8
+      KF = 0
+      AF = 1
+      FC = .9
+      BV = 600
+      IBV = 1E-4)
*
.END

```

**Figure 3.1.** Diode clipper circuit netlist



**Figure 3.2.** Schematic of diode clipper circuit with DC and transient voltage sources.

## 3.2 DC Sweep Analysis

This section includes an example of DC sweep analysis using **Xyce**. The DC response of the clipper circuit is obtained by sweeping the DC voltage source ( $V_{in}$ ) from -10 to 15 volts in one-volt steps. Chapter 7.2 provides more details about DC analysis, as does the **Xyce** Reference Guide [3].

### Example: DC sweep analysis

To set up and run a DC sweep analysis using the diode clipper circuit:

1. Open the diode clipper circuit netlist file (`clipper.cir`) using a standard text editor (*e.g.* VI, Emacs, Notepad, *etc.*).
2. Enter the analysis control statement in the netlist:

```
.DC VIN -10 15 1
```

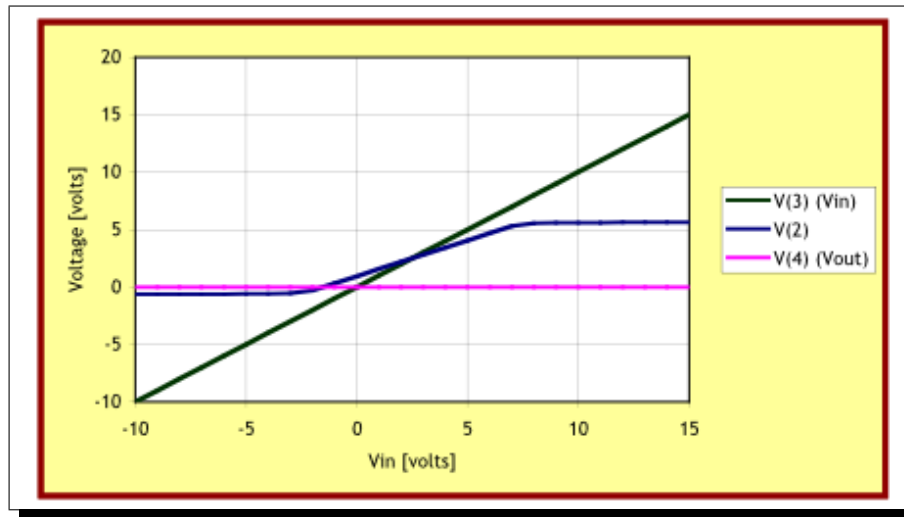
3. Enter the output control statement:

```
.PRINT DC V(3) V(2) V(4)
```

4. Save the netlist file and run **Xyce** on the circuit. For example, to run serial **Xyce**:

```
> runxyce clipper.cir
```

5. Open the results file (`clipper.cir.prn`) and examine (or plot) the output voltages that were calculated for nodes 3 ( $V_{in}$ ), 2 and 4 ( $V_{out}$ ). Figure 3.4 shows the output plotted as a function of the swept variable  $V_{in}$ .



**Figure 3.4.** DC sweep voltages at  $V_{in}$ , node 2, and  $V_{out}$

## 3.3 Transient Analysis

This section contains an example of transient analysis in **Xyce**. In this example the DC clipper circuit of the previous section has been modified so the input voltage source ( $V_{in}$ ) is a time-dependent sinusoidal input source. The frequency of  $V_{in}$  is 1 kHz, and has an amplitude of 10 volts. For more details about transient analysis see chapter 7.3, or the **Xyce** reference guide [3].

### Example: transient analysis

To set up and run a transient analysis using the diode clipper circuit:

1. Open the diode clipper circuit netlist file (`clipper.cir`) using a standard text editor (e.g. VI, Emacs, Notepad, etc.).
2. Remove DC analysis and output statements if added in the previous example (figure 3.4).
3. Enter the analysis control in the netlist:

```
.TRAN 2ns 2ms
```

```

Diode Clipper Circuit with DC sweep analysis statement
*
* Voltage Sources
VCC 1 0 5V
VIN 3 0 0V
* Analysis Command
.DC VIN -10 15 1
* Output
.PRINT DC V(3) V(2) V(4)
* Diodes
D1 2 1 D1N3940
D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
*
* GENERIC FUNCTIONAL EQUIVALENT = 1N3940
* TYPE: DIODE
* SUBTYPE: RECTIFIER
.MODEL D1N3940 D(
+      IS = 4E-10
+      RS = .105
+      N = 1.48
+      TT = 8E-7
+      CJO = 1.95E-11
+      VJ = .4
+      M = .38
+      EG = 1.36
+      XTI = -8
+      KF = 0
+      AF = 1
+      FC = .9
+      BV = 600
+      IBV = 1E-4)
*
.END

```

**Figure 3.3.** Diode clipper circuit netlist for DC sweep analysis

4. Enter the output control statement:

```
.PRINT TRAN V(3) V(2) V(4)
```

5. Modify the input voltage source ( $V_{in}$ ) to generate the sinusoidal input signal:

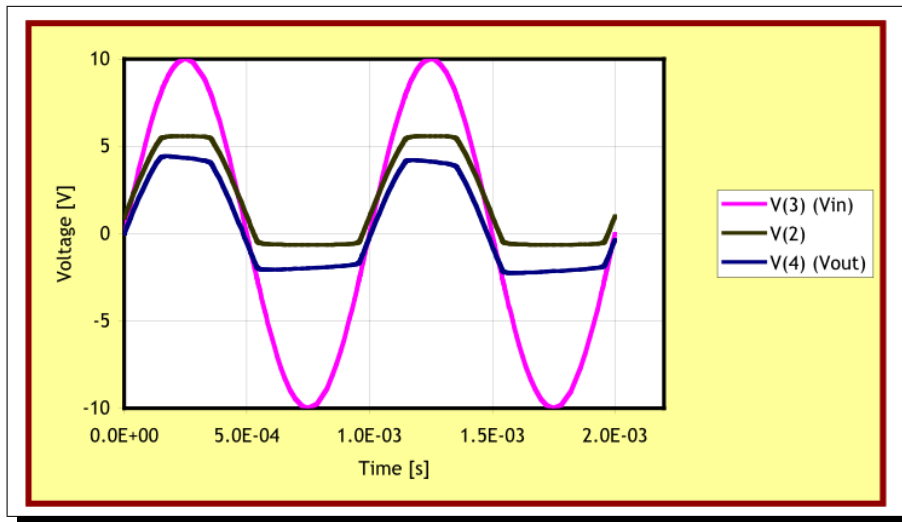
```
VIN 3 0 SIN(0V 10V 1kHz)
```

6. At this point, the netlist should look similar to the netlist in figure 3.5. Save the netlist file and run **Xyce** on the circuit. For example, to run serial **Xyce**:

```
> runxyce clipper.cir
```

7. Open the results file and examine (or plot) the output voltages for nodes 3 ( $V_{in}$ ), 2, and 4 ( $V_{out}$ ). The plot in figure 3.6 shows the output plotted as a function of time.

Figure 3.5 shows the modified netlist and figure 3.6 shows the corresponding results.



**Figure 3.6.** Sinusoidal input signal and clipped outputs

```

Diode clipper circuit with transient analysis statement
*
* Voltage Sources
VCC 1 0 5V
VIN 3 0 SIN(0V 10V 1kHz)
* Analysis Command
.TRAN 2ns 2ms
* Output
.PRINT TRAN V(3) V(2) V(4)
* Diodes
D1 2 1 D1N3940
D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
*
* GENERIC FUNCTIONAL EQUIVALENT = 1N3940
* TYPE: DIODE
* SUBTYPE: RECTIFIER
.MODEL D1N3940 D(
+      IS = 4E-10
+      RS = .105
+      N = 1.48
+      TT = 8E-7
+      CJO = 1.95E-11
+      VJ = .4
+      M = .38
+      EG = 1.36
+      XTI = -8
+      KF = 0
+      AF = 1
+      FC = .9
+      BV = 600
+      IBV = 1E-4)
*
.END

```

**Figure 3.5.** Diode clipper circuit netlist for transient analysis

# 4. Netlist Basics

## Chapter Overview

This chapter contains introductory material on netlist syntax and usage. Sections include:

- Section 4.1 *General Overview*
- Section 4.2 *Devices Available for Simulation*
- Section 4.3 *Parameters and Expressions*



# 4.1 General Overview

## 4.1.1 Introduction

Using a netlist to describe a circuit for **Xyce** is the primary method for running a circuit simulation. Netlist support within **Xyce** largely conforms to that used by Berkeley SPICE 3F5 with several new options for controlling functionality unique to **Xyce**.

In a netlist, the circuit is described by a set of *element lines* defining circuit elements and their associated parameters, the circuit topology (i.e., the connection of the circuit elements), and a variety of control options for the simulation. The first line in the netlist file must be a title and the last line must be “.END”. Between these two constraints, the order of the statements is irrelevant.

## 4.1.2 Nodes

Nodes and elements form the foundation for the circuit topology. Each node represents a point in the circuit that is connected to the leads of multiple elements (devices). Each lead of every element is connected to a node, and each node is connected to multiple element leads.

A node is simply a named point in the circuit. The naming of normal nodes is only known within the level of circuit hierarchy where they appear; normal nodes defined in the main circuit are not visible to subcircuits, nor are nodes defined in a subcircuit visible to the top-level circuit. Nodes can be passed into subcircuits through an argument list, and in this case subcircuits are given limited access to nodes from the upper-level circuit.

### Global Nodes

For cases where a particular node is used widely throughout various subcircuits it can be more convenient to use a global node, which is referenced by the same name throughout the circuit. This is often the case for power rails such as VDD or VSS.

Global nodes start with the prefix \$G. Examples of global node names would be: \$G\_VDD or \$G1. Nodes or global nodes require no declaration, as they are declared implicitly by appearing in *element lines*.

## 4.1.3 Elements

An *element line* defines each circuit element instance. While each element type determines the specific format, the general format is given by:

```
<type><name> <node information> <element information...>
```

The <type> must be a letter (A through Z) with the <name> immediately following. For example, RAREISTOR specifies a device of type “R” (for “Resistor”) with a name AREISTOR. Nodes are

separated by spaces, and additional element information required by the device is given after the node list as described in the Netlist Reference section of the **Xyce** Reference Guide [3]. **Xyce** ignores character case when reading a netlist such that RARESISTOR is equivalent to raresistor. The only exception to this case insensitivity occurs when including external files in a netlist where the filename specified in the netlist must have the same case as the actual filename.

A number field may be an integer or a floating-point value. Either one may be followed by one of the following scaling factors:

Symbol	Equivalent Value
T	$10^{12}$
G	$10^9$
Meg	$10^6$
K	$10^3$
mil	$25.4^{-6}$
m	$10^{-3}$
u ( $\mu$ )	$10^{-6}$
n	$10^{-9}$
p	$10^{-12}$
f	$10^{-15}$

Node information is given in terms of node names, which are arbitrary character strings. The only requirement is that the ground node is named '0'. There is one restriction on the circuit topology: there can be no loop of voltage sources and/or inductors. In addition to this requirement, the following additional topology constraints are highly recommended:

- Every node has a DC path to ground.
- Every node has at least two connections (with the exception of unterminated transmission lines and MOSFET substrate nodes).

While **Xyce** can theoretically handle netlists that violate the above two constraints, such topologies are typically the result of human error in creating a netlist file, and will often lead to convergence failures. Chapter 14 provides more information on this topic.

The following line provides an example of an element line that defines a resistor between nodes 1 and 3 with a resistance value of 10k $\Omega$ .

**Example:**        RARESISTOR 1 3 10K

## Title, Comments and End

The first line of the netlist is the title line of the netlist. This line is treated as a comment even if it does not begin with an asterisk. It is a common mistake to forget the meaning of this first line and begin the circuit elements on the first line; doing so will probably result in a parsing error.

**Example:**            Test RLC Circuit

The “.END” line must be the last line in the netlist.

**Example:**            .END

Comments are supported in netlists and are indicated by placing an asterisk at the beginning of the comment line. They may occur anywhere in the netlist *but* they must be at the beginning of a line. **Xyce** also supports *in-line* comments. An in-line comment is designated by a semicolon and may occur on any line. **Xyce** ignores everything after a semicolon. **Xyce** also considers lines beginning with a leading white space as comments.

**Example:**            \* This is a netlist comment.

**Example:**            **WRONG:**.DC .... \* This type of in-line comment is *not supported*.

**Example:**            .DC .... ; This type of in-line comment is supported.

## Continuation Lines

Continuation lines begin with a + symbol, and their contents are appended to those of the previous line. If the previous line or lines were comments, the continuation line is appended to the first noncomment line preceding it.

## Netlist Commands

Command elements are used to describe the analysis being defined by the netlist. Examples include analysis types, initial conditions, device models, and output control. The **Xyce** Reference Guide [3] contains a reference for these commands.

**Example:**            .PRINT TRAN V(Vout)

## Analog Devices

**Xyce**-supported analog devices include most of the standard circuit components normally found in circuit simulators, such as SPICE 3F5, PSpice, etc., plus several Sandia-specific devices.

**Example:** D\_CR303 N\_0065 0 D159700

The **Xyce** Reference Guide [3] provides more information concerning analog devices.

## 4.2 Devices Available for Simulation

This section describes the different types of **Xyce**-supported analog devices, such as standard analog devices, sources (dependent and independent), and subcircuits. Each device description contains the following information:

- A description and an example of the netlist syntax.
- Corresponding model types and descriptions, where applicable
- Corresponding lists of model parameters and descriptions, where applicable
- Associated schematic symbol and model equations, as necessary.

These analog devices include all of the standard circuit components needed for most analog circuits. User-defined models may also be implemented using the `.MODEL` (model definition) statement and macromodels as subcircuits using the `.SUBCKT` (subcircuit) statement.

### 4.2.1 Analog Devices

**Xyce** supports many analog devices, including sources, subcircuits, and behavioral models. The devices are classified into device types, each of which can have one or more model types. For example, the BJT device type has two model types: NPN and PNP.

The device element statements in the netlist always start with the name of the individual device instance. The first letter of the name determines the device type. The format of the subsequent information depends on the device type and its parameters. Table 4.1 provides a quick reference to the analog devices and the form of their netlist formats supported by **Xyce**. Except where noted, the devices are based upon those found in [6]. The **Xyce** Reference Guide [3] provides a more complete description of the syntax for supported devices.

Table 4.1: Analog Device Quick Reference.

Device Type	Designator Letter	Typical Netlist Format
Nonlinear Dependent Source (B Source)	B	B<name> <+ node> <- node> + <I or V>={<expression>}
Capacitor	C	C<name> <+ node> <- node> [model name] <value> + [IC=<initial value>]
Diode	D	D<name> <anode node> <cathode node> + <model name> [area value]

Table 4.1: Analog Device Quick Reference.

Device Type	Designator Letter	Typical Netlist Format
Voltage Controlled Voltage Source	E	E<name> <+ node> <- node> <+ controlling node> + <- controlling node> <gain>
Current Controlled Current Source	F	F<name> <+ node> <- node> + <controlling V device name> <gain>
Voltage Controlled Current Source	G	G<name> <+ node> <- node> <+ controlling node> + <- controlling node> <transconductance>
Current Controlled Voltage Source	H	H<name> <+ node> <- node> + <controlling V device name> <gain>
Independent Current Source	I	I<name> <+ node> <- node> [[DC] <value>] + [AC [magnitude value [phase value] ] ] + [transient specification]
Mutual Inductor	K	K<name> <inductor 1> [<ind. n>*] + <linear coupling or model>
Inductor	L	L<name> <+ node> <- node> [model name] <value> + [IC=<initial value>]
JFET	J	J<name> <drain node> <gate node> <source node> + <model name> [area value]
MOSFET	M	M<name> <drain node> <gate node> <source node> + <bulk/substrate node> [SOI node(s)] + <model name> [common model parameter]*
Lossy Transmission Line (LTRA)	O	O<name> <A port (+) node> <A port (-) node> + <B port (+) node> <B port (-) node> + <model name>
Bipolar Junction Transistor (BJT)	Q	Q<name> <collector node> <base node> + <emitter node> [substrate node] + <model name> [area value]
Resistor	R	R<name> <+ node> <- node> [model name] <value> + [L=<length>] [W=<width>]
Voltage Controlled Switch	S	S<name> <+ switch node> <- switch node> + <+ controlling node> <- controlling node> + <model name>
Transmission Line	T	T<name> <A port + node> <A port - node> + <B port + node> <B port - node> + <ideal specification>
Independent Voltage Source	V	V<name> <+ node> <- node> [[DC] <value>] + [AC [magnitude value [phase value] ] ] + [transient specification]
Subcircuit	X	X<name> [node]* <subcircuit name> + [PARAMS:[<name>=<value>]*]
Current Controlled Switch	W	W<name> <+ switch node> <- switch node> + <controlling V device name> <model name>

Table 4.1: Analog Device Quick Reference.

Device Type	Designator Letter	Typical Netlist Format
Digital Devices	Y<name>	Y<name> [node]* <model name>
PDE Devices	YPDE	YPDE <name> [node]* <model name>
ROM Devices	YROM	YROM <name> <+ node> <- node> + BASE_FILENAME=<filename> + [MASK_VARS=<true/false>] + [USE_PORT_DESCRIPTION=<0/1>]
Accelerated masses	YACC	YACC <name> <acceleration> <velocity> <position> +[x0=<initial position>] [v0=<initial velocity>]
MESFET	Z	Z<name> <drain node> <gate node> <source node> + <model name> [area value]

## 4.3 Parameters and Expressions

In addition to explicit values, the user may use parameters and expressions to symbolize numeric values in the circuit design.

### 4.3.1 Parameters

A parameter is a symbolic name representing a numeric value. Parameters must start with a letter or underscore. The characters after the first can be letter, underscore, or digits. Once a parameter is defined (by having its name declared and having a value assigned to it) at a particular level in the circuit hierarchy, it can be used to represent circuit values at that level or any level directly beneath it in the circuit hierarchy. One way to use parameters is to apply the same value to multiple part instances.

### 4.3.2 How to Declare and Use Parameters

For using a parameter in a circuit, one must:

- Define the parameter using a `.PARAM` statement within a netlist
- Replace an explicit value with the parameter in the circuit

**Xyce** reserves the following keywords that may not be used as parameter names:

- Time

- Vt
- Temp
- GMIN.

Though `Vt` and `GMIN` are reserved and may not be used as parameter names, neither is actually defined and usable in **Xyce** at this time. Both `Time` and `TEMP` are defined and may be used in time- or temperature-dependent expressions, where such expressions are permitted.

### Example: Declaring a parameter

1. Locate the level in the circuit hierarchy at which the `.PARAM` statement declaring a parameter will be placed. To declare a parameter capable of being used anywhere in the netlist, place the `.PARAM` statement at the top-most level of the circuit.
2. Name the parameter and give it a value. The value can be numeric or given by an expression:

```
.SUBCKT subckt1 n1 n2 n3
.PARAM res = 100
*
* other netlist statements here
*
.ENDS
```

3. NOTE: The parameter `res` can be used anywhere within the subcircuit `subckt1`, including subcircuits defined within it, but cannot be used outside of `subckt1`.

### Example: Using a parameter in the circuit

1. Locate the numeric value (a device instance parameter value, model parameter value, etc.) that is to be replaced by a parameter.
2. Replace the numeric value with the parameter name contained within braces (`{}`) as in:

```
R1 1 2 {res}
```

NOTE: Ensure the value being replaced remains accessible within the current hierarchy level.

### Limitations on parameter definitions

As chapter 6 describes, there is considerable flexibility in the use of parameters. They can be set to expressions containing other parameters, and can be passed down the hierarchy into subcircuits. Fundamentally, however, parameters are constants evaluated at the beginning of a run; therefore, all terms in the expression defining the parameter must be constants known at the beginning of the run. It is not legal to use time-dependent expressions in parameter declarations (either by including voltage nodes or currents, or by including reference to the variable `TIME`).

Parameters defined within a given scope can be used in any expression within that scope. The only limitation on ordering is for the use of a parameter in an expression that defines the value of another parameter. In that case, all parameters used in the expression must be defined before being used to define another parameter. So, in the following example:

```
R1 1 0 {B+C} ; OK because the expression is not used to define a param
.PARAM A=3
.PARAM B={A+1} ; OK because A is defined above
.PARAM D={C+2} ; Illegal because C is not yet known
.PARAM C=2
```

### 4.3.3 Global Parameters

A normal parameter defined at the main circuit level will have global scope. Such parameters suffer from limitations, such as: (1) they are constant during the simulation, and (2) the parameter may be redefined within a subcircuit, which would change the value in the subcircuit and below. Global parameters address these limitations.

A global parameter differs from a normal parameter in that it can only be defined at the main circuit level, and it is allowed to change during a simulation. Global parameters act as variables rather than constants during the simulation. Examples of some global parameter usages are:

```
.param dTdt=100
.global_param T={27+dTdt*time}
R1 1 2 RMOD TEMP={T}
```

or

```
.global_param T=27
R1 1 2 RMOD TEMP={T}
C1 1 2 CMOD TEMP={T}
.step T 20 50 10
```

In these examples, T is used to represent an environmental variable that changes.

NOTE: Normal parameters may be used in expressions defining global parameters, but the opposite is not allowed.

### 4.3.4 Expressions

In **Xyce**, an expression is a mathematical relationship that may be used any place one would use a number (numeric or boolean). Except in the case of expressions used in analog behavioral modeling sources (see chapter 6) **Xyce** evaluates the expression to a value when it reads in the circuit netlist, not each time its value is needed. Therefore, all terms in an expression must be known at the beginning of a run.



To use an expression in a circuit netlist:

1. Locate the value to be replaced (component, model parameter, etc.).
2. Substitute the value with an expression using the {} syntax:

`{expression}`

where *expression* can contain any of the following:

- Available operators (table 4.2)
- Included functions (tables 4.3, 4.5, and 4.6)
- User-defined functions
- User-defined parameters within scope
- Literal operands.

The braces ({} ) instruct **Xyce** to evaluate the expression and use the resulting value. Additional time-dependent constructs are available in expressions used in analog behavioral modeling sources (see chapter 6).

### Example: Using an expression

Scaling the DC voltage of a 12V independent voltage source, designated VF, by some factor can be accomplished by the following netlist statements (in this example the factor is 1.5):

```
.PARAM FACTORV=1.5
VF 3 4 {FACTORV*12}
```

**Xyce** will evaluate the expression to 12 \* 1.5 or 18 volts.

---

<sup>1</sup>Logical and relational operators are used only with the IF() function.

**Table 4.2.** Expression operators

Class of operator	Operator	Meaning
arithmetic	+	addition or string concatenation
	-	subtraction
	*	multiplication
	/	division
	**	exponentiation
logical <sup>1</sup>	~	unary NOT
		boolean OR
	^	boolean XOR
	&	boolean AND
relational	==	equality
	!=	non-equality
	>	greater-than
	>=	greater-than or equal
	<	less-than
	<=	less-than or equal

**Table 4.3.** Arithmetic functions in expressions

Function	Meaning	Explanation
ABS(x)	$ x $	absolute value of $x$
DDT(x)	$\frac{d}{dt}x(t)$	time derivative of $x$
DDX(f(x),x)	$\frac{\partial}{\partial x}f(x)$	partial derivative of $f(x)$ with respect to $x$
IF(t,x,y)	$x$ if $t$ is true, $y$ otherwise	$t$ is an expression using the relational operators in Table 4.2
INT(x)	$\text{sgn}(x)[ x ]$	integer part of the real variable $x$
LIMIT(x,y,z)	$y$ if $x < y$ $x$ if $y < x < z$ $z$ if $x > z$	$x$ limited to range $y$ to $z$
M(x)	$ x $	absolute value of $x$
MIN(x,y)	$\min(x, y)$	minimum of $x$ and $y$
MAX(x,y)	$\max(x, y)$	maximum of $x$ and $y$
PWR(x,y)	$x^y$	$x$ raised to $y$ power
POW(x,y)	$x^y$	$x$ raised to $y$ power
PWRS(x,y)	$x^y$ if $x > 0$ 0 if $x = 0$ $-(-x)^y$ if $x < 0$	sign corrected $x$ raised to $y$ power

**Table 4.4.** Arithmetic functions in expressions (cont'd)

Function	Meaning	Explanation
RAND()	$0 < result < 1$	random constant number between 0 and 1
SDT(x)	$\int x(t)dt$	time integral of $x$
SGN(x)	+1 if $x > 0$ 0 if $x = 0$ -1 if $x < 0$	sign value of $x$
SIGN(x,y)	$sgn(y) x $	sign of $y$ times absolute value of $x$
STP(x)	1 if $x > 0$ 0 otherwise	step function
SQRT(x)	$\sqrt{x}$	square root of $x$
TABLE(x,y,z,*)	$f(x)$ where $f(y) = z$	piecewise linear interpolation, multiple $(y,z)$ pairs can be specified
URAMP(x)	$x$ if $x > 0$ 0 otherwise	ramp function

**Table 4.5.** Exponential, logarithmic, and trigonometric functions in expressions

Function	Meaning	Explanation
ACOS(x)	$\arccos(x)$	result in radians
ACOSH(x)	$\cosh^{-1}(x)$	hyperbolic arccosine of $x$
ARCTAN(x)	$\arctan(x)$	result in radians
ASIN(x)	$\arcsin(x)$	result in radians
ASINH(x)	$\sinh^{-1}(x)$	hyperbolic arcsine of $x$
ATAN(x)	$\arctan(x)$	result in radians
ATANH(x)	$\tanh^{-1}(x)$	hyperbolic arctangent of $x$
ATAN2(x,y)	$\arctan(x/y)$	result in radians
COS(x)	$\cos(x)$	$x$ in radians
COSH(x)	$\cosh(x)$	hyperbolic cosine of $x$
EXP(x)	$e^x$	$e$ to the $x$ power
LN(x)	$\ln(x)$	log base $e$
LOG(x)	$\log(x)$	log base 10
LOG10(x)	$\log(x)$	log base 10
SIN(x)	$\sin(x)$	$x$ in radians
SINH(x)	$\sinh(x)$	hyperbolic sine of $x$
TAN(x)	$\tan(x)$	$x$ in radians
TANH(x)	$\tanh(x)$	hyperbolic tangent of $x$

**Table 4.6.** SPICE compatibility functions in expressions

<b>Function</b>	<b>Explanation</b>
SPICE_EXP(V1,V2,TD1,TAU1,TD2,TAU2)	SPICE style transient exponential V1 = initial value V2 = pulsed value TD1 = rise delay time TAU1 = rise time constant TD2 = fall delay time TAU2 = fall time constant
SPICE_PULSE(V1,V2,TD,TR,TF,PW,PER)	SPICE style transient pulse V1 = initial value V2 = pulsed value TD = delay TR = rise time TF = fall time PW = pulse width PER = period
SPICE_SFFM(V0,VA,FC,MDI,FS)	SPICE style transient single frequency FM V0 = offset VA = amplitude FC = carrier frequency MDI = modulation index FS = signal frequency
SPICE_SIN(V0,VA,FREQ,TD,THETA)	SPICE style transient sine wave V0 = offset VA = amplitude FREQ = frequency (hz) TD = delay THETA = damping factor

# 5. Working with Subcircuits and Models

## Chapter Overview

This chapter provides model ideas and summarizes ways to create and modify models. Sections include:

- Section 5.1, *Model Definition*
- Section 5.2, *Subcircuit Creation*
- Section 5.3, *Model Organization*
- Section 5.4, *Model Interpolation*

## 5.1 Model Definitions

A model describes the electrical performance of a *part*, such as a specific vendor's version of a 2N2222 transistor. To simulate a part requires specification of *simulation properties*. These properties define the model of the part.

Depending on the given device type and the requirements of the circuit design, a model is specified using a model parameter set, a subcircuit netlist, or both.

In general, *model parameter sets* define the parameters used in ideal models of specific device types, while *subcircuit netlists* allow the user to combine ideal device models to simulate more complex effects. For example, one could simulate a bipolar transistor using the Xyce BJT device by specifying model parameters extracted to fit the simulation behavior to the behavior of the part used. One could also develop a subcircuit macro-model of a capacitor that adds effects such as lead inductance and resistance to the basic capacitor device.

Both methods of defining a model use a netlist format, with precise syntax rules. In this section we give an overview of how to define model parameter sets in **Xyce**. A subsequent section will provide a similar overview of how to define subcircuit models. For full details, consult the Reference Guide [3].

### Defining models using model parameters

Although **Xyce** has no built-in part models, models can be defined for a device by changing some or all of the *model parameters* from their defaults via the `.MODEL` statement. For example:

```
M5 3 2 1 0 MLOAD1
.MODEL MLOAD1 NMOS (LEVEL=3 VTO=0.5 CJ=0.025pF)
```

This example defines a MOSFET device `M5` that is an instance of a part described by the model parameter set `MLOAD1`. The `MLOAD1` parameter set is defined in the `.MODEL` statement.

Most device types in **Xyce** support some form of model parameters. Consult the **Xyce** Reference Guide [3] for the model parameters supported by each device type.

### Defining models using subcircuit netlists

In **Xyce**, models may also be defined using the `.SUBCKT/.ENDS` subcircuit syntax. This syntax allows the creation of *Netlists*, which define the configuration and function of the part, and the use of *Variable input parameters*, which can be used to create device-specific implementations of the model. The `.SUBCKT` syntax, and an example of how to use `.SUBCKT` to implement a model, are given in Section 5.2.



## 5.2 Subcircuit Creation

A subcircuit can be created within **Xyce** using the `.SUBCKT` keyword. The `.ENDS` keyword is used to mark the end of the subcircuit. All the lines between the two keywords are considered to be part of the subcircuit. Figure 5.1 provides an example of how a subcircuit is defined and used.

```
****other devices
X5 5 6 7 8 l3dsc1 PARAMS: ScaleFac=2.0
X6 9 10 11 12 l3dsc1
****more netlist commands

*** SUBCIRCUIT: l3dsc1
*** Parasitic Model: microstrip
*** Only one segment
.SUBCKT l3dsc1 1 3 2 4 PARAMS: ScaleFac=1.0
C01 1 0 4.540e-12
RG01 1 0 7.816e+03
L1 1 5 3.718e-08
R1 5 2 4.300e-01
C1 2 0 4.540e-12
RG1 2 0 7.816e+03
C02 3 0 4.540e-12
RG02 3 0 7.816e+03
L2 3 6 3.668e-08
R2 6 4 4.184e-01
C2 4 0 4.540e-12
RG2 4 0 7.816e+03
CM012 1 3 5.288e-13
KM12 L1 L2 2.229e-01
CM12 2 4 {5.288e-13*ScaleFac}
.ENDS
```

**Figure 5.1.** Example subcircuit model.

In this example, a subcircuit model named `l3dsc1`, which implements one part of a microstrip transmission line, is defined between the `.SUBCKT/.ENDS` lines; and two different instances of the subcircuit are used in the `X` lines. This somewhat artificial example shows how input parameters are used, where the last capacitor in the subcircuit is scaled by the input parameter `ScaleFac`. If input parameters are not specified on the `X` line (as in the case of device `X6`), then the default values specified on the `.SUBCKT` line are used. Non-default values are specified on the `X` line using the `PARAMS:` keyword. Consult the **Xyce** Reference Guide [3] for precise syntax.

In addition to devices, a subcircuit may contain definitions, such as models via the `.MODEL` statement, parameters via the `.PARAM` statement, and functions via the `.FUNC` statement. **Xyce** also

supports the definition of one or more subcircuits within another subcircuit. Subcircuits can be nested to an arbitrary extent, where one subcircuit can contain another subcircuit, which can contain yet another subcircuit, and so on.

The creation of nested subcircuits requires an understanding of “scope,” such that each subcircuit defines the scope for the definitions it contains. That is, *the definitions contained within a subcircuit can be used within that subcircuit and within any subcircuit it contains, but not at any higher level.* Definitions occurring in the main circuit have global scope and can be used anywhere in the circuit. A name, such as a model, parameter, function, or subcircuit name, occurring in a definition at one level of a circuit hierarchy can be redefined at any lower level contained directly by the subcircuit. In this case, the new definition applies at the given level and those below.

The idea of “scope” is best provided by an example. In the netlist provided in Figure 5.2, the model named MOD1 can be used in subcircuits SUB1 and SUB2, but not in the subcircuit SUB3. The parameter P1 has a value of 10 in subcircuit SUB1 and a value of 20 in subcircuit SUB2. In subcircuit SUB3, P1 has no meaning.

```
.SUBCKT SUB1 1 2 3 4
.MODEL MOD1 NMOS(LEVEL=2)
.PARAM P1=10
*
* subcircuit devices omitted for brevity
*
.SUBCKT SUB2 1 3 2 4
.PARAM P1=20
*
* subcircuit devices omitted for brevity
*
.ENDS
.ENDS

.SUBCKT SUB3 1 2 3 4
*
* subcircuit devices omitted for brevity
*
.ENDS
```

**Figure 5.2.** Example subcircuit heirarchy.

## 5.3 Model Organization

While it is always possible to make a self-contained netlist in which all models for all parts are included along with the circuit definition, **Xyce** provides a simple mechanism to conveniently organize frequently used models into separate model libraries. Models are simply collected into model library files, and then accessed by netlists as needed by inserting an `.INCLUDE` directive. This section describes the process in detail.

### 5.3.1 Model Libraries

Device model and subcircuit definitions may be organized into model libraries as text files (similar to netlist files) with one or more model definitions. Many users choose to name model library files ending with `.lib`, but they may be named using any convention.

In general, most users create model libraries files that include similar model types. In these files, the *header comments* describe the models therein.

### 5.3.2 Model Library Configuration using `.INCLUDE`

**Xyce** uses model libraries by inserting an `.INCLUDE` statement into a netlist. Once a file is included, its contents become available to the netlist just as if the entire contents had been inserted directly into the netlist.

As an example, one might create the following model library file called `bjtmodels.lib`, containing `.MODEL` statements for common types of bipolar junction transistors:

```
*bjtmodels.lib
* Bipolar transistor models
.MODEL Q2N2222 NPN (Is=14.34f Xti=3 Eg=1.11 Vaf=74.03 Bf=5 Ne=1.307
+  Ise=14.34f Ikf=.2847 Xtb=1.5 Br=6.092 Nc=2 Isc=0 Ikr=0 Rc=1
+  Cjc=7.306p Mjc=.3416 Vjc=.75 Fc=.5 Cje=22.01p Mje=.377 Vje=.75
+  Tr=46.91n Tf=411.1p Itf=.6 Vtf=1.7 Xtf=3 Rb=10)

.MODEL 2N3700 NPN (IS=17.2E-15 BF=100)

.MODEL 2N2907A PNP (IS=1.E-12 BF=100)
```

The models `Q2N2222`, `2N3700` and `2N2907A` could then be used in a netlist by including the `bjtmodels.lib` file.

```
.INCLUDE "bjtmodels.lib"
Q1 1 2 3 Q2N2222
Q2 5 6 7 2N3700
```

```

Q3 8 9 10 2N2907A
*other netlist entries
.END

```

Because the contents of an included file are simply inserted into the netlist at the point where the `.INCLUDE` statement appears, the scoping rules for `.INCLUDE` statements are the same as for other types of definitions as outlined in the preceding sections.

NOTE: The path to the library file is assumed to be relative to the execution directory, but absolute pathnames are permissible. The entire file name, including its “extension” must be specified. There is no assumed default extension.

### 5.3.3 Model Library Configuration using `.LIB`

An alternative technique for organizing model libraries employs the `.LIB` command. With `.LIB`, a library file can contain multiple versions of a model and specific versions may be selected at the top level using a keyword on the `.LIB` line.

There are two different uses for the `.LIB` command. In the main netlist, `.LIB` functions in a similar manner to `.INCLUDE`: it reads in a file. Inside that file, `.LIB` and `.ENDL` are used to specify blocks of model code that may be included independently of other parts of the same file.

As an example, if you had two different 2N2222 transistor models extracted at different `TNOM` values, you could define them in a model library inside `.LIB/.ENDL` pairs:

```

* transistors.lib file
.lib roomtemp
.MODEL Q2N2222 NPN (TNOM=27 Is=14.34f Xti=3 Eg=1.11 Vaf=74.03 Bf=5 Ne=1.307
+ Ise=14.34f Ikf=.2847 Xtb=1.5 Br=6.092 Nc=2 Isc=0 Ikr=0 Rc=1
+ Cjc=7.306p Mjc=.3416 Vjc=.75 Fc=.5 Cje=22.01p Mje=.377 Vje=.75
+ Tr=46.91n Tf=411.1p Itf=.6 Vtf=1.7 Xtf=3 Rb=10)
.endl

.lib hightemp
.MODEL Q2N2222 NPN (TNOM=55 [...parameters omitted for brevity...])
.endl

```

Note that both models are given identical names, but are enclosed within `.LIB/.ENDL` pairs with different names. When this file is used in a netlist, a specific model can be used by specifying it on the `.LIB` line in the main netlist.

```

*This netlist uses only the high temperature model from the library
.lib transistors.lib hightemp
Q1 collector base emitter Q2N2222
[...]

```

The exact format and usage of the `.LIB` command is documented in the **Xyce** Reference Guide [3].

## 5.4 Model Interpolation

Traditionally, SPICE simulators handle thermal effects by coding temperature dependence of model parameters into each device. These expressions modify the nominal device parameters given in the `.MODEL` card when the ambient temperature is not equal to `TNOM`, the temperature at which parameters were extracted.

These temperature correction equations may be reasonable at temperatures close to `TNOM`, but Sandia users of **Xyce** have found them inadequate when simulations must be performed over a wide range of temperatures. To address this inadequacy, **Xyce** implements a model interpolation option that allows the user to specify multiple `.MODEL` cards, each extracted from real device measurements at a different `TNOM`. From these model cards, **Xyce** will interpolate parameters based on the ambient temperature using either linear or quadratic interpolation.

Interpolation of models is accessed through the model parameter `TEMPMODEL` in the models that support this capability. In the netlist, a base model is specified, and is followed by multiple models at other temperatures.

Interpolation of model cards in this fashion is currently implemented only in the BJT level 1, JFET, MESFET, and MOSFETS levels 1-6, 10, and 18.

The use of model interpolation is best shown by example:

```
Jtest 1a 2a 3 SA2108 TEMP= 40
*
.MODEL SA2108 PJF ( TEMPMODEL=QUADRATIC TNOM = 27
+ LEVEL=2 BETA= 0.003130 VTO = -1.9966 PB = 1.046
+ LAMBDA = 0.00401 DELTA = 0.578; THETA = 0;
+ IS = 1.393E-10          RS = 1e-3)
*
.MODEL SA2108 PJF ( TEMPMODEL=QUADRATIC TNOM = -55
+ LEVEL=2 BETA = 0.00365 VTO = -1.9360 PB = 0.304
+ LAMBDA = 0.00286 DELTA = 0.2540 THETA = 0.0
+ IS = 1.393E-10 RD = 0.0 RS = 1e-3)
*
.MODEL SA2108 PJF ( TEMPMODEL=QUADRATIC TNOM = 90
+ LEVEL=2 BETA = 0.002770 VTO = -2.0350 PB = 1.507
+ LAMBDA = 0.00528 DELTA = 0.630 THETA = 0.0
+ IS = 1.393E-10          RS = 5.66)
```

Note that the model names are all identical for the three `.MODEL` lines, and that they all specify `TEMPMODEL=QUADRATIC`, but with different `TNOM`. For parameters that appear in all three `.MODEL` lines, the value of the parameter will be interpolated using the `TEMP=` value in the

device line, which in this example is 40°C, in the first line. For parameters that are not interpolated, such as **RD**, it is not necessary to include these in the second and third `.MODEL` lines.

Currently, **QUADRATIC** and **PWL** (piecewise linear) are the only arguments for **TEMP-MODEL**. The quadratic method includes a limiting feature that prevents the parameter value from exceeding the range of values specified in the `.MODEL` lines. For example, the **RS** value in the example would take on negative values for most of the interval between -55 and 27, as the value at 90 is very high. This truncation is necessary as parameters can easily take on values (such as the negative resistance of **RS** in this example) that will cause a **Xyce** failure.

For certain parameters (currently only BJT parameters **IS** and **ISE**), interpolation is done not on the parameter itself, but on the the log of the parameter, which provides for excellent interpolation of these parameters that vary over many orders of magnitude, and with this type of temperature dependence.

The interpolation scheme used for model interpolation bases the interpolation on the difference between the ambient temperature and the **TNOM** value of the first model card in the netlist, which can sometimes lead to poorly conditioned interpolation. Thus it is often best that the first model card in the netlist be the one that has the “middle” **TNOM**, as in the example above. This assures that no matter where in the range of temperature values the ambient temperature lies, it is a minimal distance from the base point of the interpolation.

# 6. Analog Behavioral Modeling

## Chapter Overview

This chapter describes analog behavioral modeling in **Xyce**. Sections include:

- Section 6.1, *Overview of Analog Behavioral Modeling*
- Section 6.2, *Specifying ABM Devices*
- Section 6.3, *Guidance for ABM Use*

## 6.1 Overview of Analog Behavioral Modeling

The analog behavioral modeling capability of **Xyce** provides for flexible descriptions of electronic components or subsystems in terms of a transfer function or lookup table. In other words, a mathematical relationship is used to model a circuit segment removing the need for component-by-component design information for those components or subsystems.

The B device, or nonlinear dependent source, is the primary device used for analog behavioral modeling in **Xyce**. A B device can serve as either a voltage or current source, and by using expressions dependent on voltages and currents elsewhere in the circuit the user can produce a wide range of behaviors.

## 6.2 Specifying ABM Devices

ABM devices (B devices) are specified in a netlist the same way as other devices. Customizing the operational behavior of the device is achieved by defining an ABM expression describing how inputs are transformed into outputs.

For example, the following pair of lines would provide exactly the same behavior as a 10K resistor between nodes 1 and 2, and is written to be a current source with current specified using Ohm's law and the constant resistance value of 10K  $\Omega$ .

```
.PARAM Res1=10K
Blinearres 1 2 I={ (V(2)-V(1))/Res1 }
```

A nonlinear resistor could be specified similarly:

```
.PARAM R1=0.15
.PARAM R2=6
.PARAM E2 = {2*E1}
.PARAM delr = {R1-R0}
.PARAM k1 = {1/E1**2}
.PARAM r2 = {R0+sqrt(2)*delr}

.FUNC Rreg1(a,b,c,d) {a +(b-a)*c/d}
.Func Rreg2(a,b,c,d,f) {a+sqrt(2-b*(2*c-d)**2)*f}

Bnlr 4 2 V = { I(Vmon) * IF(
+ V(101) < E1, Rreg1(R0,R1,V(101),E1),
+ IF(
+ V(101) < E2, Rreg2(R0,k1,E1,V(101),delr), R2
+ )
```



+ )}

In this example, `Bn1r` provides a voltage between nodes 4 and 2, determined using Ohm's law with a resistance that is a function of the voltage on node 101 and a number of parameters. These two examples demonstrate how the `B` source can be used either as a voltage source (by specifying `V={expression}`) or as a current source (with `I={expression}`).

NOTE: Unlike expressions used in parameters or function declarations, expressions in the nonlinear dependent source may contain voltages and currents from other parts of the circuit, or even explicit time-dependent functions. **Xyce** evaluates these expressions when current or voltage through the ABM source is needed. Expressions used in parameters or function declarations are evaluated only once, prior to the start of the circuit simulation.

## 6.2.1 Additional constructs for use in ABM expressions

ABM expressions follow the same rules as other expressions in a netlist, with the additional ability to specify signals (node voltages and voltage source currents) and explicitly time-dependent functions in the expression. In ABM expressions, refer to signals by name. **Xyce** recognizes the following constructs in ABM expressions:

- `V(<node name>)`
- `V(<node name>, <node name>)` (the voltage difference between the first and second nodes)
- `I(<voltage source name>)`
- The variable, `TIME`
- The constants, `PI` and `EXP`, which equal  $\pi$  and  $e$ , respectively.
- Lookup tables

In a hierarchical circuit (a circuit with possibly nested levels of subcircuits), voltage source names in an ABM expression must be the name of a voltage source in the same subcircuit as the ABM device, or in a subcircuit instantiated by that subcircuit. Similarly, node names in an ABM expression must be the node names of one or more devices in the same subcircuit as the ABM device, or in a subcircuit instantiated by that subcircuit.

## 6.2.2 Examples of Analog Behavioral Modeling

A variety of examples of legal usage of analog behavioral modeling is probably the most effective means of demonstrating what is allowed. The following netlist fragment shows the range of simple items allowed in ABM expressions:

```
* Current through B1 given as expression of voltage drop between
* nodes 2 and 3 plus current through voltage source Vr4mon
```

```

B1 1 0 I={V(2,3) + I(Vr4mon)}
R4 2 0 10K
Vr4mon 2a 2 0V
* Voltage across device Em given as time-dependent expression
Em 3 2a VALUE={PAR3+1000*time}
* Voltage across device B2 set to current through device Em
B2 2a 0 V={I(Em)}
M3 Drain 6 0 NMOD
VdrainM3 DrainPrime Drain 0v
* Voltage across B3 is function of voltage on node two and current through
* device VdrainM3
B3 6 4 V={I(VdrainM3)+V(2)}
* Voltage across device B4 is function of an internal node named "5" of
* subcircuit instance X1
X1 1 3 mysubcircuit
B4 4 5 V={V(X1:5)}
* Current through device B5 taken from current through internal device V4
* of subcircuit instance X1
B5 4 5 I={I(X1:V4)}

```

The range of items that can be used in the current and voltage parameters of a B (or E, F, G, or H) source is far greater than what is allowed for expressions in other contexts. In particular, the use of solution values ( $V(*)$ ,  $V(*,*)$ ,  $I(V*)$ ) are prohibited in all other expressions because they lead to unstable behavior if used elsewhere beside ABM. Time-dependent expressions are allowed for some device parameters, but this feature should be used with caution, as the behavior of the non-ABM device cannot be guaranteed to be correct when its device parameters are not constant throughout the run.

In addition to these simple items, lookup tables provide a means of specifying a piecewise linear function in an expression. A table expression is specified with the keyword TABLE followed by an expression that is evaluated as the independent variable of the function, followed by a list of pairs of independent variable/dependent variable values. For example:

**Example:**        B1 1 0 V={TABLE {time} = (0, 0) (1, 2) (2, 4) (3, 6)}

An equivalent example uses the table function, which has a simpler syntax, but may be hard to read for long tables:

**Example:**        B1 1 0 V={TABLE(time, 0, 0, 1, 2, 2, 4, 3, 6)}

The previous two examples will produce a voltage source whose voltage is a simple linear function of time. At  $t = 0$  the voltage is 0 volts, at time  $t = 1s$  the voltage is 2 volts, and at times in between the voltage is determined by linear interpolation. Similarly, the voltage will be 4 volts at  $t = 2s$  and 6 volts at  $t = 3s$  with linear interpolation at times in between the tabulated values.

It is also possible to create ABM sources from files of time-value pairs by providing the name of the file containing the pairs between quotation marks ("):

**Example:**        Bfile 1 0 V="myfile"

The file provided must have one time-voltage pair per line, separated by spaces. Comma-separated files are not supported, and will not be parsed correctly. If the file "myfile" contains the following data:

```
0 0
1 2
2 4
3 6
```

then the "Bfile" example above will be identical to either of the "B1" examples above. The quoted-file syntax is in fact converted internally to precisely the same TABLE format as the first B1 example, with an independent variable of TIME and the given time-value pairs inserted.<sup>1</sup>

Finally, the independent variable of the table source does not have to be a simple expression:

**Example:**        Bcomplicated 1 0 V={TABLE {V(5)-V(3)/4+I(V6)\*Res1} = (0, 0) (1, 2) (2, 4) (3, 6)}

## 6.2.3 Alternate behavioral modeling sources

In addition to the primary nonlinear dependent source, the B source, **Xyce** also supports the PSpice extensions to the standard Spice voltage- and current-controlled sources, the E, F, G, and H sources. **Xyce** provides these sources for PSpice compatibility, and converts them internally into equivalent B sources. The **Xyce** Reference Guide [3]netlist reference chapter provides the syntax of these compatibility devices.

## 6.3 Guidance for ABM Use

### 6.3.1 ABM devices add equations to the system of equations used by the solver

As **Xyce** solves a complex nonlinear set of equations at each time step, it is important to remember this system of equations is solved iteratively to obtain a converged solution. Specifying an ABM

---

<sup>1</sup>The use of a B source in this manner is similar to using the FILE option to the PWL voltage source as documented in the Reference Guide, but unlike the PWL source, the file-based table function does *NOT* support reading comma-separated files.

device in a **Xyce** netlist adds one or more equations to the nonlinear problem that **Xyce** must solve.

When the nonlinear solver has converged, the expression given in the ABM device will be satisfied to within a solver tolerance. However, during the course of the iterative solve, the unconverged values of nodal voltages and currents, which are often inputs and outputs of ABM devices, are not guaranteed to be solutions to the system of equations.

During this preconverged phase, solution variables are not guaranteed to have physically reasonable values. They could, for example, temporarily have the wrong sign. Only at the end of a successful nonlinear iterative solve are the solution variables consistent, legal values. This convergence behavior motivates the caveats on ABM usage given in the next subsection.

### 6.3.2 Expressions used in ABM devices must be valid for any possible input

While ABM devices look temptingly like calculators, it is potentially dangerous to use them as such. The previous subsection stated that during the nonlinear solution of each timestep equations, nodal voltages and currents are usually not solutions to the full set of equations, and often violate Kirchhoff's laws. Only at the end of the nonlinear solution are all the constraints on voltages and currents satisfied. This has some important consequences to the user of ABM devices.

All expressions involving nodal voltages and currents used in ABM devices should be valid for any possible value they might see — even those that appear to be physically meaningless and those that a knowledgeable user might never expect to see in the real circuit. This is particularly important when using square roots or exponentiating to a fractional power. For example, consider the following netlist fragment:

```
*...other parts of more complex circuit deleted...
* potentially bad usage of ABM device
Vexample 1 0 5V
d1 1 0 diode_model
B1 2 0 V={sqrt(v(1))}
r1 2 0 10k
*...other parts of more complex circuit deleted...
```

This example demonstrates a potentially dangerous usage. It is assumed, because node 1 is connected to a 5V DC source, that the argument of the square root function is always positive. However, it could be the case that during the nonlinear solution of the full circuit that an unconverged value of node 1 might be negative. Tracking down mistakes such as this can be difficult, as on most platforms B1 will result in a “Not a Number” value for the nodal voltage of node 2, but the program will not crash. This frequently results in inexplicable “Timestep too small” errors.

Although such things can be avoided by protecting the arguments of functions with a limited domain, care must be taken when doing this. One obvious way to protect the example circuit fragment would be to take the absolute value of V(1) before calling the square root (sqrt) function:

```

*...other parts of more complex circuit deleted...
* safer usage of ABM device
Vexample 1 0 5V
d1 1 0 diode_model
B1 2 0 V={sqrt(abs(v(1)))}
r1 2 0 10k
*...other parts of more complex circuit deleted...

```

There are many other ways to protect the square root function from negative arguments, such as by using the maximum of zero and  $V(1)$ . Some alternatives might be more appropriate than others in different contexts.

Note, though, that it would be a mistake to attempt to generate the absolute value as shown here:

```

*...other parts of more complex circuit deleted...
* really bad misuse of ABM device
Vexample 1 0 5V
d1 1 0 diode_model
B2 3 0 V={abs(v(1))} ; watch out!
B1 2 0 V={sqrt(v(3))}; just as bad as first example!
r1 2 0 10k
*...other parts of more complex circuit deleted...

```

There are two things wrong with this example — first, node 3 is floating and this alone could lead to convergence problems. Second, by adding the second ABM device one has merely created an equation whose solution is that node 3 contains the absolute value of the voltage on node 1. However, until convergence is reached there is no guarantee node 3 will be precisely the absolute value of  $V(3)$ , nor is it guaranteed that node 3 will have a positive voltage. To re-iterate, nodes have values that are solutions to the set of equations created by the netlist only at convergence.

### 6.3.3 ABM devices should not be used purely for output postprocessing

Users sometimes use ABM devices to provide output postprocessing. For example, if a user was interested in the absolute value, or the log of an output voltage then that user might create an ABM circuit element to calculate the desired output value.

Using ABM sources in this manner is bad practice though. By creating a circuit element whose only purpose is postprocessing, Xyce is forced to include it and the corresponding nonlinear solve in the circuit, which can cause unnecessary solver problems. If postprocessing is the goal, it is much better to use expressions directly on the `.PRINT` line.

An example of a “bad use” of ABM sources can be found in the following code fragment:

```

* Bad example

```

```

B1 test1 0 V = {(abs(I(VMON)))*1.0e-10}
VIN 1 0 DC 5V
R1 1 2 2K
D1 3 0 DMOD
VMON 2 3 0
.MODEL DMOD D (IS=100FA)
.DC VIN 5 5 1
.PRINT DC I(VMON) V(3) V(test1)

```

Although the source B1 provides a postprocessing output, it doesn't play a functional role in the circuit; **Xyce** would still be forced to include B1 in the problem it is attempting to solve.

A better solution to the previous problem is given here:

```

* Good example
VIN 1 0 DC 5V
R1 1 2 2K
D1 3 0 DMOD
VMON 2 3 0
.MODEL DMOD D (IS=100FA)
.DC VIN 5 5 1
.PRINT DC I(VMON) V(3) {(abs(I(VMON)))*1.0e-10}

```

Section 9.1 and the **Xyce** Reference Guide [3] provide a more detailed explanation of how to use expressions in the .PRINT line.

# 7. Analysis Types

## Chapter Overview

This chapter describes the different analysis types available in **Xyce**. It includes the following sections:

- Section 7.1, *Introduction*
- Section 7.2, *DC Analysis*
- Section 7.3, *Transient Analysis*
- Section 7.4, *STEP Parametric Analysis*
- Section 7.5, *Harmonic Balance Analysis*
- Section 7.6, *AC Analysis*

## 7.1 Introduction

**Xyce** supports several simulation analysis options, including DC bias point (`.DC`, section 7.2), transient (`.TRAN`, section 7.3), AC (`.AC`, section 7.6), and harmonic balance (`.HB`, section 7.5).

Using `.STEP`(section 7.4), **Xyce** can also apply an outer parametric loop to any type of analysis. This allows one (for example) to sweep a model parameter and perform a transient simulation for each parameter value.

There are some analysis types typically found in SPICE-style simulators are still a work in progress for **Xyce**. Operating point analysis (`.OP`, section 7.2.3) is partially supported in **Xyce**.

## 7.2 Steady-State (`.DC`) Analysis

The DC sweep analysis capability in **Xyce** computes the DC bias point of a circuit for a range of values of input sources. DC sweep is supported for a source or device parameter, through a range of specified values. As the sweep proceeds, **Xyce** computes the bias point for each value in the specified range of the sweep.

If the variable to be swept is a voltage or current source, a DC source must be used and its value set in the netlist (see **Xyce** Reference Guide [3]). In simulating the DC response of an analog circuit, **Xyce** eliminates time dependence from the circuit by treating capacitor elements as open circuits and inductor elements as short circuits, while using only the DC values of voltage and current sources.

### 7.2.1 `.DC` Statement

To specify a `.DC` analysis, include a `.DC` line in the netlist. Some examples of typical `.DC` lines are:

**Example:**

```
.DC V1 7m 5m -1m
.DC I1 5u 10u 1u
.DC M1:L 7u 5u -1u
.DC OCT V0 0.125 64 2
.DC DEC R1 100 10000 3
.DC TEMP LIST 10.0 15.0 18.0 27.0 33.0
```

The examples include all four types of sweep — linear, octave, decade, and list, and demonstrates sweeping over voltage and current sources as well as device parameters. The **Xyce** Reference Guide [3] provides a complete description of each.



## 7.2.2 Setting Up and Running a DC Sweep

Following the example given in section 3.2, figure 7.1 shows the diode clipper circuit netlist with a DC sweep analysis specified. Here, the voltage source  $V_{in}$  is swept from -10 to 15 in 1-volt increments, resulting in 26 DC operating point calculations.

NOTE: **Xyce** ignores the default setting for  $V_{in}$  during these calculations. All other source values use the specified values (in this case,  $VCC = 5V$ ).

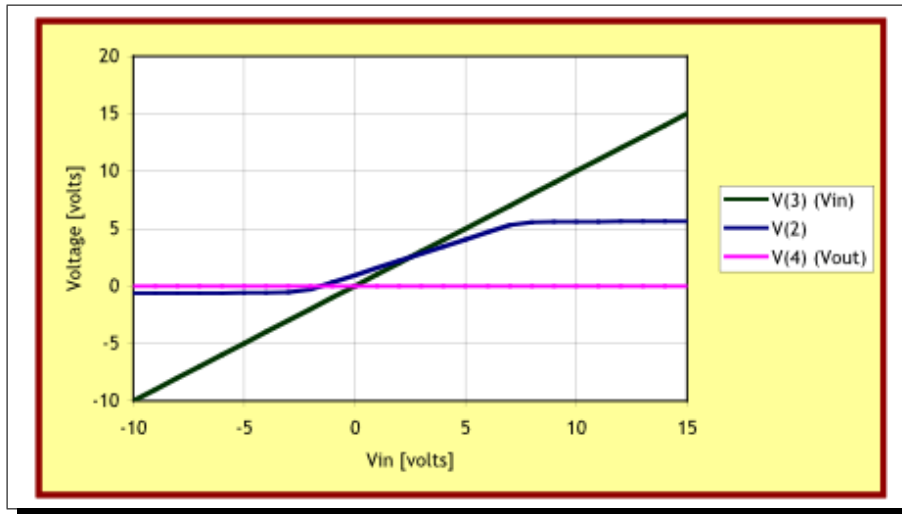
Running **Xyce** on this netlist produces an output results file named `clipper.cir.prn`. Obtaining this file requires specifying the `.PRINT DC` line. Plotting this data produces the graph shown in figure 7.2.

```
Diode Clipper Circuit
** Voltage Sources
VCC 1 0 5V
VIN 3 0 0V
* Analysis Command
.DC VIN -10 15 1
* Output
.PRINT DC V(3) V(2) V(4)
* Diodes
D1 2 1 D1N3940 D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
.MODEL D1N3940 D(
+ IS=4E-10 RS=.105 N=1.48 TT=8E-7
+ CJO=1.95E-11 VJ=.4 M=.38 EG=1.36
+ XTI=-8 KF=0 AF=1 FC=.9
+ BV=600 IBV=1E-4)
.END
```

**Figure 7.1.** Diode clipper circuit netlist for DC sweep analysis.

## 7.2.3 OP Analysis

**Xyce** also supports `.OP` analysis statements. In **Xyce**, consider `.OP` as a shorthand for a single-step DC sweep, in which all the default operating point values are used. One may also consider



**Figure 7.2.** DC sweep voltages at Vin, node 2 and Vout.

.OP analysis to be the operating point calculation that would occur as the initial step to a transient calculation, without the subsequent time steps.

This capability was mainly added to enable the code to handle legacy netlists using this analysis statement type. In most versions of SPICE, using .OP results in extra output not available from a DC sweep. **Xyce** will also output some of this extra information about devices, but the capability is not fully implemented.

## 7.2.4 Output

During analysis a number of output files may be generated. The selection of which files are created depends on a variety of factors, most obvious of which is the .PRINT command. Table 7.1 lists the format options and files created. The column labeled “Additional Columns” lists the additional data that is written, though not specified on the .PRINT line.

## 7.3 Transient Analysis

The transient response analysis simulates the response of the circuit from TIME=0 to a specified time. Throughout a transient analysis, any or all of the independent sources may have time-dependent values.

In **Xyce** (and most other circuit simulators), the transient analysis begins by performing its own bias point calculation at the beginning of the run, using the same method as used for DC sweep. This is required to set the initial conditions for the transient solution as the initial values of the sources may differ from their DC values.

**Table 7.1.** Output generated for DC analysis

Trigger	Files	Additional Columns
.PRINT DC	<i>circuit-file.prn</i>	INDEX TIME
.PRINT DC NOINDEX	<i>circuit-file.prn</i>	TIME
.PRINT DC FORMAT=CSV	<i>circuit-file.csv</i>	TIME
.PRINT DC FORMAT=RAW	<i>circuit-file.raw</i>	TIME
.PRINT DC FORMAT=TECPLOT	<i>circuit-file.dat</i>	TIME
.PRINT DC FORMAT=PROBE	<i>circuit-file.csd</i>	TIME
<i>runxyce -r</i>	<i>circuit-file.raw</i>	All circuit variables printed
<i>runxyce -r -a</i>	<i>circuit-file.raw</i>	All circuit variables printed
.OP	<i>log-file</i>	Operating point information

### 7.3.1 .TRAN Statement

To run a transient simulation, the circuit netlist file must contain a .TRAN command.

**Example:**

```
.TRAN 100us 300ms  
.TRAN 100p 12.05u 9.95u
```

The **Xyce** Reference Guide [3] provides a detailed explanation of the .TRAN statement. The netlist must also contain one of the following:

- Independent, transient source (see table 7.2),
- Initial condition on a reactive element, or
- Time-dependent behavioral modeling source (see chapter 6)

### 7.3.2 Defining a Time-Dependent (transient) Source

#### Overview of Source Elements

Source elements, either voltage or current, are entered in the netlist file as described in the **Xyce** Reference Guide [3]. Table 7.2 lists the time-dependent sources available in **Xyce** for either voltage

**Table 7.2.** Summary of **Xyce**-supported time-dependent sources

Source Element Name	Description
EXP	Exponential Waveform
PULSE	Pulse Waveform
PWL	Piecewise Linear Waveform
SFFM	Frequency-modulated Waveform
SIN	Sinusoidal Waveform

or current. For voltage sources, the name is preceded by *v* while current sources are preceded by *I*.

To use time-dependent or transient sources, place the source element line in the netlist and characterize the transient behavior using the appropriate parameters. Each transient source element has a separate set of parameters dependent on its transient behavior. In this way, the user can create analog sources that produce sine wave, square pulse, exponential pulse, single-frequency FM, and PLWs.

### Defining Transient Sources

To define a transient source, select one of the supported sources: independent voltage or current, choose a transient source type from table 7.2, and provide the transient parameters (refer to the **Xyce** Reference Guide [3] to fully define the source).

The following example of an independent sinusoidal voltage source in a circuit netlist creates a voltage source between nodes 1 and 5 that oscillates sinusoidally between -5V and +5V with a frequency of 50 KHz. The arguments specify an offset of -5V, a 10V amplitude, and a 50KHz frequency, in that order.

**Example:** `Vexample 1 5 SIN(-5V 10V 50K)`

### 7.3.3 Transient Time Steps

During the simulation, **Xyce** uses a calculated time step that is continuously adjusted for accuracy and efficiency (see [7] and [8]). Calculation timestep increases during periods of circuit idleness, and decreases during dynamic portions of the waveform. Users may control maximum internal step size by specifying the step ceiling value in the `.TRAN` command (see the **Xyce** Reference Guide [3]).

The internal calculation time steps used might not be consistent with the user-requested output time steps. By default, **Xyce** outputs solution results at every time step it calculates. If the user selects output timesteps via the `.OPTIONS OUTPUT` statement (see chapter 9), then **Xyce** will output

results at the interval requested, interpolating solution variables to desired output times if necessary.

## 7.3.4 Time Integration Methods

For a transient analysis, several time integration methods can be selected to solve the circuit model's differential algebraic equations. The following algorithms are available:

- Variable order Trapezoidal (combines Trapezoidal and Backward Euler)
- Backward Difference Formula, orders 1-5
- Gear method, orders 1-2.

You can set the `method`, `maxord` and `minord` parameters to select the time integration methods via a `.OPTIONS` line. The following table shows the possible settings for those three parameters. (Note: Consult the Reference Guide for the exact syntax of the `.OPTIONS` line for each time integration method.) The default time integration method in **Xyce** is Trap, which is the same as SPICE, PSPICE and HSPICE.

**Table 7.3.** Summary of **Xyce**-supported time integration methods

Integration Methods	Option Settings	Comments
Backward-Euler	method=trap maxord=1	Backward-Euler only
Trap	method=trap	combines Trapezoidal and Backward Euler (default)
Trap only	method=trap minord=2	Trapezoidal only
Backward Difference Formula	method=bdf	higher order integration
Gear	method=gear	combines Backward Euler and 2nd order Gear
Gear2 only	method=gear minord=2	2nd order Gear only

The Trapezoidal method is often the preferred method because it is accurate and fast. However, this method can exhibit artificial point-to-point ringing, which can be controlled by using tighter tolerances. If a circuit fails to converge with the Trapezoidal method then you can re-run the transient analysis using the Gear or BDF method.

The Gear method and Backward Difference Formula (BDF) method may help convergence for some circuits. The 2nd order Gear method is typically more accurate than Backward-Euler method. However, both of these methods are overly stable methods, and they can damp the actual circuit behavior when simulating high Q resonators such as oscillators. The Backward-Euler method has more damping effect than the 2nd order Gear method. This effect can be alleviated by using

tighter tolerances in the simulations. However, it is suggested to use the pure Trapezoidal method for oscillators.

The Backward Difference Formula (BDF) method can use higher order integration up to order 5. It uses variable time step size and variable order. If the order used is more than 2nd order then the results are interpolated using high order polynomial interpolations.

## 7.3.5 Error Controls

There are two basic time-step error control methods in **Xyce** — Local Truncation Error (LTE) based and non-LTE based.

### Local Truncation Error (LTE) Strategy

All time integration methods use the LTE-based strategy by default. The accuracy of the simulation can be controlled by specifying appropriate relative and absolute error tolerances (RELTOL and ABSTOL).

#### Example:

```
.OPTIONS TIMEINT RELTOL=1e-4 ABSTOL=1e-8
```

The total tolerance of LTE is

$$Tol_{LTE} = abstol + reltol * ref$$

The parameter `ref` is the reference value that the relative error is compared to. It can be controlled by setting `newlte` option.

#### Example:

```
.OPTIONS TIMEINT NEWLTE=1
```

When `newlte` is set to be true, the reference value is the maximum of all the signals at the current time. When `newlte` is set to be false, the reference value is the current value at each node.

The Trapezoid integrator algorithm introduces no numerical dissipation. So, a strong ringing (artificially introduced by the numerical algorithm) will occur when sources or models introduce discontinuities. This can result in a large local truncation error estimate, ultimately leading to a “time-step too small” error. In this case, using the Gear and BDF methods or a non-LTE strategy may help.

### Non-LTE Strategy

The non-LTE strategy used in **Xyce** is based on success of the nonlinear solve, and is enabled by setting `ERROPTION=1`. Since the step-size selection is based only upon nonlinear iteration statistics rather than accuracy, it is highly suggested that `DELMAX` be specified, in a circuit-specific

manner, for all three time integrators. The purpose of DELMAX is to limit the largest time step taken.

The behavior of this setting (ERROPTION=1) is slightly different for the BDF integrator and other integrators. For the BDF integrator, if the nonlinear solver converges, then the step-size is doubled. On the other hand, if the nonlinear solver fails to converge, then the step-size is cut by one eighth.

**Example:**

```
.OPTIONS TIMEINT ERROPTION=1 DELMAX=1.0e-4
```

For the Trapezoid and Gear integrators, the options are slightly more refined. If the number of nonlinear iterations is below NLMIN, then the step size is doubled. If the number of nonlinear iterations is above NLMAX then the step size is cut by one eighth. In between, the step size is not changed. An example using Trap (METHOD=7) is given below.

**Example:**

```
.OPTIONS TIMEINT METHOD=7 ERROPTION=1 NLMIN=3 NLMAX=8 DELMAX=1.0e-4
```

If the number of Newton iterations is bigger than NLmax and TIMESTEPSREVERSAL is not set, then Xyce will cut the next step. If the number of Newton iterations is bigger than NLmax and TIMESTEPSREVERSAL is set, then Xyce will reject the current step and also cut the current step.

**Example:**

```
.OPTIONS TIMEINT METHOD=7 ERROPTION=1 DELMAX=1.0e-4 TIMESTEPSREVERSAL=1
```

## 7.3.6 Checkpointing and Restarting

**Xyce** was designed to simulate large, complex circuits over long simulation runs. Because complex simulations can take many hours (or even days) to complete, it can sometimes be helpful to use “checkpointing.” When checkpointing is used, **Xyce** periodically saves its complete simulation state. The saved state can be used to restart **Xyce** from one of these “checkpoints.” In the event of a computer crash, power outage, or should the simulation need to be interrupted for some other reason, checkpointing allows the user to restart a long simulation in the middle of a run without having to start over.

**Xyce** uses the `.OPTIONS RESTART` netlist command to control all checkpoint output and restarting.

### Checkpointing Command Format

```
■ .OPTIONS RESTART [PACK=<0|1>] JOB=<job name> [INITIAL_INTERVAL=<interval>
  [<t0> <i0> [<t1> <i1>...]]]
```

PACK=<0|1> indicates whether restart data files will contain byte-packed (binary) data(PACK=1,

the default) or unpacked (ASCII)(PACK=0). JOB=<job name> identifies the prefix for restart files. The actual restart files will be the job name appended with the current simulation time (e.g., name1e-05 for JOB=name and simulation time 1e-05 seconds). Furthermore, the INITIAL\_INTERVAL=<interval> identifies the initial interval time used for restart output. The <tx ix> intervals identify times (tx) at which the output interval (ix) will change. This functionality is identical to that described for the .OPTIONS OUTPUT command (section 9.1).

- Example — Generate checkpoints at every time step (default):

```
.OPTIONS RESTART JOB=checkpoint
```

- Example — Generate checkpoints every 0.1  $\mu s$ :

```
.OPTIONS RESTART JOB=checkpoint INITIAL_INTERVAL=0.1us
```

- Example — Generate unpacked checkpoints every 0.1  $\mu s$ :

```
.OPTIONS RESTART PACK=0 JOB=checkpoint INITIAL_INTERVAL=0.1us
```

- Example — Initial interval of 0.1  $\mu s$ , at 1  $\mu s$  in the simulation, change to interval of 0.5  $\mu s$ , and at 10  $\mu s$  change to an interval of 0.1  $\mu s$ :

```
.OPTIONS RESTART JOB=checkpoint INITIAL_INTERVAL=0.1us 1us 0.5us
+ 10us 0.1us
```

## Restarting Command Format

- .OPTIONS RESTART <FILE=<filename> | JOB=<job name> START\_TIME=<time>>  
+ [INITIAL\_INTERVAL=<interval> [<t0> <i0> [<t1> <i1> ...]]]

To restart from an existing restart file, specify the file by using either the FILE=<filename> parameter to explicitly request a file or JOB=<job name> START\_TIME=<time> to specify a file prefix and a specific time. The time must exactly match an output file time for the simulator to correctly load the file.

To continue checkpointing the simulation in a restarted run, append INITIAL\_INTERVAL=<interval> and the following intervals to the command in the same format as previously described. Without these additional parameters, the simulation will restart as requested, but will not generate further checkpoint files.

- Example — Restart from checkpoint file at 0.133  $\mu s$ :

```
.OPTIONS RESTART JOB=checkpoint START_TIME=0.133us
```

- Example — Restart from checkpoint file at 0.133  $\mu s$  :

```
.OPTIONS RESTART FILE=checkpoint0.000000133
```

- Example — Restart from 0.133  $\mu s$  and continue checkpointing at 0.1  $\mu s$  intervals:

```
.OPTIONS RESTART FILE=checkpoint0.000000133 JOB=checkpoint_again
+ INITIAL_INTERVAL=0.1us
```



## 7.3.7 Output

During analysis a number of output files may be generated. The selection of which files are created depends on a variety of factors, most obvious of which is the `.PRINT` command. Table 7.4 lists the format options and files created. The column labeled “Additional Columns” lists the additional data that is written, though not specified on the `.PRINT` line.

**Table 7.4.** Output generated for Transient analysis

Trigger	Files	Additional Columns
<code>.PRINT TRAN</code>	<i>circuit-file.prn</i>	INDEX TIME
<code>.PRINT TRAN NOINDEX</code>	<i>circuit-file.prn</i>	TIME
<code>.PRINT TRAN FORMAT=CSV</code>	<i>circuit-file.csv</i>	TIME
<code>.PRINT TRAN FORMAT=RAW</code>	<i>circuit-file.raw</i>	TIME
<code>.PRINT TRAN FORMAT=TECPLOT</code>	<i>circuit-file.dat</i>	TIME
<code>.PRINT TRAN FORMAT=PROBE</code>	<i>circuit-file.csd</i>	TIME
<code>runxyce -r</code>	<i>circuit-file.raw</i>	All circuit variables printed
<code>runxyce -r -a</code>	<i>circuit-file.raw</i>	All circuit variables printed
<code>.OP</code>	<i>log-file</i>	Operating point information

## 7.4 STEP Parametric Analysis

The `.STEP` command performs a parametric sweep for all the analyses of the circuit. When the `.STEP` command is invoked, typical analyses, such as `.DC`, `.AC`, and `.TRAN` are performed for each value of the stepped parameter.

This capability is very similar, but not identical, to the `STEP` capability in PSPICE [4]. **Xyce** can use `.STEP` to sweep over any device instance or device model parameter, as well as the circuit temperature. It is not legal to sweep parameters defined in `.PARAM` statements, but it is legal to sweep global parameters defined in `.global_param` statements. Section 4.3) discusses of these two distinct parameter definitions.

### 7.4.1 .STEP Statement

A `.STEP` analysis may be specified by simply adding a `.STEP` line to a netlist. Unlike `.DC`, `.STEP` by itself is not an adequate analysis specification, as it merely specifies an outer loop around the normal analysis. A standard analysis line, either specifying `.TRAN`, `.AC` and `.DC` analysis, is still required.

Some examples of typical `.STEP` lines are:

**Example:**

```
.STEP M1:L 7u 5u -1u
.STEP OCT V0 0.125 64 2
.STEP DEC R1 100 10000 3
.STEP TEMP LIST 10.0 15.0 18.0 27.0 33.0
```

`.STEP` has a format similar to that of the `.DC` format specification. In the first example, `M1:L` is the name of the parameter (in this instance, the length parameter of the MOSFET `M1`), `7u` is the initial value of the parameter, `5u` is the final value of the parameter, and `-1u` is the step size. Like `.DC`, `.STEP` in **Xyce** can also handle sweeps by decade, octave, or specified lists of values. Consult the **Xyce** Reference Guide [3] for complete explanations of each sweep type.

### 7.4.2 Sweeping over a Device Instance Parameter

The first example uses `M1:L` as the parameter, but it could have used any model or instance parameter existing in the circuit. Internally, **Xyce** handles the parameters for all device models and device instances in the same way. Users can uniquely identify any parameter by specifying the device instance name, followed by a colon (:), followed by the specific parameter name. For example, all the MOSFET models have an instance parameter for the channel length, `L`. For a MOSFET instance specified in a netlist, named `M1`, then the full name for the `M1` channel length parameter is `M1:L`.

Figure 7.3 provides a simple application of `.STEP` to a device instance. This is the same diode clipper circuit as was used in the transient analysis chapter, except that a single line (in red) has

been added. The .STEP line will cause **Xyce** to sweep the resistance of the resistor, R4, from 3.0 KOhms to 15.0 KOhms, in 2.0-KOhms increments, meaning seven transient simulations will be performed, each one with a different value for R4.

As the circuit is executed multiple times, the resulting output file is a little more sophisticated. The .PRINT statement is still used in much the same way as before. However, the .prn output file contains the concatenated output of each .STEP increment. The end of this section provides details of how .STEP changes output files.

```
Transient Diode Clipper Circuit with Step Analysis
* Voltage Sources
VCC 1 0 5V
VIN 3 0 SIN(0V 10V 1kHz)
* Analysis Command
.TRAN 2ns 2ms
* Output
.PRINT TRAN V(3) V(2) V(4)
* Step statement
.STEP R4:R 3.0K 15.0K 2.0K
* Diodes
D1 2 1 D1N3940
D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
.MODEL D1N3940 D(
+ IS=4E-10 RS=.105 N=1.48 TT=8E-7
+ CJO=1.95E-11 VJ=.4 M=.38 EG=1.36
+ XTI=-8 KF=0 AF=1 FC=.9
+ BV=600 IBV=1E-4)
.END
```

**Figure 7.3.** Diode clipper circuit netlist for step transient analysis

### 7.4.3 Sweeping over a Device Model Parameter

Sweeping a model parameter can be done in an identical manner to an instance parameter. Figure 7.4 contains the same circuit as in figure 7.3, but with additional .STEP line referring to a model parameter, D1N3940: IS.

NOTE: .STEP line syntax differs from .DC line syntax in that multiple parameters require separate

.STEP lines. Each parameter needs a separate line.

```
Transient Diode Clipper Circuit with Step Analysis
* Voltage Sources
VCC 1 0 5V
VIN 3 0 SIN(0V 10V 1kHz)
* Analysis Command
.TRAN 2ns 2ms
* Output
.PRINT TRAN V(3) V(2) V(4)
  * Step statements
  .STEP R4:R 3.0K 15.0K 2.0K
  .STEP D1N3940:IS 2.0e-10 6.0e-10 2.0e-10
* Diodes
D1 2 1 D1N3940
D2 0 2 D1N3940
* Resistors
R1 2 3 1K
R2 1 2 3.3K
R3 2 0 3.3K
R4 4 0 5.6K
* Capacitor
C1 2 4 0.47u
.MODEL D1N3940 D(
+ IS=4E-10 RS=.105 N=1.48 TT=8E-7
+ CJO=1.95E-11 VJ=.4 M=.38 EG=1.36
+ XTI=-8 KF=0 AF=1 FC=.9
+ BV=600 IBV=1E-4)
.END
```

**Figure 7.4.** Diode clipper circuit netlist for 2-step transient analysis

## 7.4.4 Sweeping over Temperature

It is also possible to sweep over temperature. To do so, simply specify `temp` as the parameter name. It will work in the same manner as `.STEP` when applied to model and instance parameters.

## 7.4.5 Special cases: Sweeping Independent Sources, Resistors, Capacitors

For some devices, there is generally only one parameter that one would want to sweep. For example, a linear resistor's only parameter of interest is resistance, `R`. Similarly, for a DC voltage

or current source, one is usually only interested in the magnitude of the source. Finally, linear capacitors generally only have capacitance,  $C$ , as a parameter of interest.

For these simple devices, it is not necessary to specify both the parameter and device on the `.STEP` line: only the device name is strictly required, as these three types of devices have default parameters that are assumed if no parameter name is given explicitly.

Examples of usage are given below. The first two lines are equivalent — in the first line, the resistance parameter of `R4` is named explicitly, and in the second line the resistance parameter is implicit. In the remaining lines, parameter names are all implicit, and the default parameters of the associated devices are used.

**Example:**

```
.STEP R4:R 3.0K 15.0K 2.0K
.STEP R4 3.0K 15.0K 2.0K
.STEP VCC 4.0 6.0 1.0
.STEP ICC 4.0 6.0 1.0
.STEP C1 0.45u 0.50u 0.1u
```

Independent sources require further explanation. Only some of the many different types of independent sources have default parameters. Sources subject to `.DC` sweeps (swept sources) have no default parameter, as this could easily lead to infinite loops should a device be specified in both a `.DC` and `.STEP` line. Table 7.5 defines various independent source default parameters.

Table 7.5: Default parameters for independent sources.

Source Type	Default
Sinusoidal source	V0 (DC value, Offset)
Exponential source	V1 (DC value, Initial value)
Pulsed source	V2 (Pulsed value)
Constant, or DC source	V0 (Constant value)
Piecewise Linear source	No default
SFFM source	No default
Swept source (specified on a <code>.DC</code> line)	No default

## 7.4.6 Output files

Users can think of `.STEP` simulations as several distinct executions of the same circuit netlist. The output data, as specified by a `.PRINT` line, however, goes to a single (`*.prn`) file. For convenience, **Xyce** also creates a second auxiliary file with the `*.res` suffix.

Figure 7.3 shows an example file named `clip.cir`, which when run will produce files `clip.cir.res` and `clip.cir.prn`. `clip.cir.res` contains one line for each step, showing what parameter value was used on that step. `clip.cir.prn` is the familiar output format, but the `INDEX` field recycles to zero each time a new step begins. As the default behavior distinguishes each step's output

only by recycling the INDEX field to zero, it can be beneficial to add the sweep parameters to the .PRINT line. For the default file format (`format=std`), **Xyce** will not automatically include these sweep parameters, so for plotting it is usually best to specify them by hand.

If using the default .prn file format (`format=std`), the resulting .STEP simulation output file will be a simple concatenation of each step's underlying analysis output. If using `format=probe`, the data for each execution of the circuit will be in distinct sections of the file, and it should be easy to plot the results using PROBE. If using `format=tecplot`, the results of each .STEP simulation will be in a distinct tecplot zone. Finally, `format=raw` will place the results for each .STEP simulation in a distinct "plot" region.

## 7.5 Harmonic Balance Analysis

Harmonic balance (HB) is a technique that solves for the steady state solution of nonlinear circuits in the frequency domain. In harmonic balance simulation, voltages and currents in a nonlinear circuit are represented by truncated Fourier series. HB directly computes the frequency spectrum of voltages and currents at the steady state solution. This can be more efficient than transient analysis in applications where transient analysis may take long time to reach the steady state solution. In particular, HB is well suited for simulating analog RF and microwave circuits.

**Xyce** supports single-tone HB for driven circuits in its serial build. That means, harmonic balance analysis can be only applied on a circuit that is excited by a periodic source with one fundamental frequency. HB outputs the real and imaginary components of voltages and currents in frequency domain. **Xyce** also provides time domain responses of a circuit.

For HB simulation, an initial guess of the solution is required. A good initial guess is important for HB to converge. In **Xyce**, a transient analysis is performed to automatically determine the initial guess. The starting time of the transient analysis can be modified by specifying parameter `STARTUPPERIODS` in `.options hbint`. The **Xyce** Reference Guide [3] provides a detailed explanation of the HB options.

### 7.5.1 .HB Statement

To run a HB simulation, the circuit netlist file must contain a `.HB` command.

**Example:**

```
.HB 1e4
```

The parameter following `.HB` is the fundamental frequency and **must** be specified by the user. The **Xyce** Reference Guide [3] provides a detailed explanation of the `.HB` statement.

### 7.5.2 HB Options

Key parameters for `.HB` simulation can be specified by `.options hbint`.

**Example:**

```
.options hbint numfreq=41 STARTUPPERIODS=2
```

As shown in the example, `numfreq` specifies the total number of harmonic frequencies to be calculated, which must be an odd number. For this example, the user will be returned 20 negative and 20 positive harmonics plus the dc component.

`STARTUPPERIODS` specifies the number of time periods that **Xyce** should integrate through using normal transient analysis **before** generating the initial conditions for HB analysis. For this example, **Xyce** will integrate through two periods before computing the initial conditions, which requires an

additional period. Thus, **Xyce** will integrate through three periods to compute the initial conditions for HB analysis.

## Nonlinear Solver Options

The HB analysis uses a different set of default nonlinear solver parameters than that of transient and DC analysis. Nonlinear solver parameters for HB simulation can be specified by using `.options nonlin-hb`.

### Example:

```
.options nonlin-hb abstol=1e-6
```

The **Xyce** Reference Guide [3] provides a detailed explanation of the `.options nonlin-hb` statement.

## Linear Solver Options

The single-tone HB analysis provided by **Xyce** employs direct solvers in the transient analysis used to generate initial conditions. However, during the HB analysis, only matrix-free operators are available, which require the use of iterative solvers. Section 10.3 provides a more detailed discussion of iterative solvers.

Preconditioners have been developed for the iterative solvers used in HB analysis. You can set iterative solver and preconditioner options using the `.options hb-linsol` statement.

### Example:

```
.options linsol-hb type=aztecoo prec_type=block_jacobi AZ_tol=1e-9
```

where, `type` specifies the iterative solver to use in the HB analysis and `AZ_tol` is the relative tolerance for the iterative solver. Any of the iterative solver options in section 10.3 are valid. However, `prec_type` specifies which HB-specific preconditioner to use. The choices for this option are `none` (default) and `block_jacobi`.

## 7.5.3 Output

During analysis a number of output files may be generated. The selection of which files are created depends on a variety of factors, most obvious of which is the `.PRINT HB` command. Table 7.6 lists the format options and files created. The column labeled “Additional Columns” lists the additional data that is written, though not specified on the `.PRINT HB` line.

## 7.5.4 User Guidance

One of the most common errors in HB simulation setup is the use of too few harmonic frequencies (i.e., `numfreq` is too small). One way to determine the optimum number of harmonic frequencies is to first simulate the circuit with a small `numfreq`, then increase the `numfreq` until the solution



**Table 7.6.** Output generated for HB analysis

Trigger	Files	Additional Columns
.PRINT HB	<i>circuit-file</i> .HB.TD.prn <i>circuit-file</i> .HB.FD.prn	INDEX TIME FREQUENCY
.PRINT HB NOINDEX	<i>circuit-file</i> .HB.TD.prn <i>circuit-file</i> .HB.FD.prn	TIME FREQUENCY
.PRINT HB FORMAT=CSV	<i>circuit-file</i> .HB.TD.csv <i>circuit-file</i> .HB.FD.csv	TIME FREQUENCY
.PRINT HB FORMAT=RAW	<i>circuit-file</i> .raw	
.PRINT HB FORMAT=TECPLOT	<i>circuit-file</i> .HB.TD.dat <i>circuit-file</i> .HB.FD.dat	TIME FREQUENCY
<i>runxyce -r</i>	<i>circuit-file</i> .raw	All circuit variables printed
<i>runxyce -r -a</i>	<i>circuit-file</i> .raw	All circuit variables printed
.PRINT HB .options hbint STARTUPPERIODS=n	<i>circuit-file</i> .startup.prn	INDEX TIME
.PRINT HB FORMAT=CSV .options hbint STARTUPPERIODS=n	<i>circuit-file</i> .startup.csv	TIME
.PRINT HB FORMAT=TECPLOT .options hbint STARTUPPERIODS=n	<i>circuit-file</i> .startup.dat	TIME
.PRINT HB .options hbint SAVEICDATA=1	<i>circuit-file</i> .hb_ic.prn	INDEX TIME
.PRINT HB FORMAT=CSV .options hbint SAVEICDATA=1	<i>circuit-file</i> .hb_ic.csv	TIME
.PRINT HB FORMAT=TECPLOT .options hbint SAVEICDATA=1	<i>circuit-file</i> .hb_ic.dat	TIME
.OP	<i>log-file</i>	Operating point information

stops changing within a significant bound. Requesting too many harmonic frequencies is wasteful of memory and simulation time, so it is not practical to just clobber the problem with a very high `numfreq` either.

## 7.6 AC Analysis

The AC small-signal analysis of **Xyce** computes AC output variables as a function of frequency. The program first computes the DC operating point of the circuit and linearizes the circuit. The resultant linear circuit is then analyzed over a user-specified range of frequencies. The desired output of an AC small-signal analysis is usually a transfer function (voltage gain, transimpedance, etc). If the circuit has one AC input, it is convenient to set that input to unity and zero phase so output variables have the same value as the transfer function of the output variable with respect to input.

### 7.6.1 .AC Statement

One may specify .AC analyses by adding a .AC line in the netlist. Some examples of typical .AC lines include:

**Example:**

```
.AC DEC 10 1K 100MEG
.AC DEC 10 1 10K
.AC LIN 100 1 100HZ
```

The examples include some types of sweep (linear and decade). The **Xyce** Reference Guide [3] provides a complete description of all types of sweep.

### 7.6.2 AC Voltage and Current Sources

**Xyce** assumes the AC source to be a cosine waveform at a specified phase angle. Its frequency must be defined in a separate “.AC” command defining the frequency for all the sources in the circuit. The unique information for the individual source is the name (which must start with “V” or “I”), the node numbers, the magnitude of the source, and its phase angle. Some examples are as follows:

**Example:**

```
Vac 4 1 AC 120V 30
Vin 1 0 1.44 ac .1
Iin 1 0 1.44e-5 ac 0.1e-5 sin(0 1 1e+5 0 0)
```

NOTE: The type, AC, must be specified because the default is DC. If not specified, **Xyce** assumes the phase angle to be zero degrees. The units of the phase angle are in degrees.

### 7.6.3 Output

During analysis a number of output files may be generated. The selection of which files are created depends on a variety of factors, most obvious of which is the `.PRINT` command. Table 7.7 lists the format options and files created. The column labeled “Additional Columns” lists the additional data that is written, though not specified on the `.PRINT` line.

**Table 7.7.** Output generated for AC analysis

Trigger	Files	Additional Columns
<code>.PRINT AC</code>	<i>circuit-file</i> .FD.prn <i>circuit-file</i> .prn	INDEX FREQUENCY INDEX TIME
<code>.PRINT AC NOINDEX</code>	<i>circuit-file</i> .FD.prn <i>circuit-file</i> .prn	INDEX FREQUENCY TIME
<code>.PRINT AC FORMAT=CSV</code>	<i>circuit-file</i> .FD.csv <i>circuit-file</i> .csv	FREQUENCY TIME
<code>.PRINT AC FORMAT=RAW</code>	<i>circuit-file</i> .raw	TIME
<code>.PRINT AC FORMAT=TECPLOT</code>	<i>circuit-file</i> .dat	TIME
<code>.PRINT AC FORMAT=PROBE</code>	<i>circuit-file</i> .csd	TIME
<code>runxyce -r</code>	<i>circuit-file</i> .raw	All circuit variables printed
<code>runxyce -r -a</code>	<i>circuit-file</i> .raw	All circuit variables printed
<code>.OPTIONS NONLIN</code> <code>CONTINUATION=&lt;method&gt;...</code>	<i>circuit-</i> <i>file</i> .HOMOTOPY.prn	INDEX TIME
<code>.PRINT AC NOINDEX</code> <code>.OPTIONS NONLIN</code> <code>CONTINUATION=&lt;method&gt;...</code>	<i>circuit-</i> <i>file</i> .HOMOTOPY.prn	INDEX TIME

### 7.6.4 Using the `.PRINT AC` Command

Running **Xyce** on AC analysis produces an output results file named `.cir.FD.prn`. Obtaining this file requires that the `.PRINT AC` line be specified.

**Xyce** supports printing the real and imaginary parts of phasor values (complex numbers) for AC analysis output as voltages or currents. For instance, specify “V(1)” to print the real part and imaginary part of a voltage at nodes 1. Some complete examples are as follows:

**Example:**

```
.print AC v(3)
```

REWRITE!

Support for other formats of AC analysis output, such as magnitude, phase (angle), and options to print each format, is still a work in progress for **Xyce**.

# 8. Using Homotopy Algorithms to Obtain Operating Points

## Chapter Overview

This chapter includes the following sections:

- Section 8.1, *Homotopy Algorithms Overview*
- Section 8.4, *MOSFET Homotopy*
- Section 8.2, *Natural Parameter Homotopy*
- Section 8.3, *Natural Multiparameter Homotopy*
- Section 8.5, *GMIN Stepping Homotopy*
- Section 8.6, *Pseudo Transient*

# 8.1 Homotopy Algorithms Overview

Often, circuit convergence problems are most prominent during the DC operating point calculation. Unlike transient solves, DC operating point analysis cannot rely on a good initial guess from a previous step, and cannot simply reduce the step size when the solver fails. Additionally, operating points often have multiple solutions, with no reliance on intent. Multiple solutions can, even for converged circuit problems, result in a standard Newton solve being unreliable. For example, it has been observed that the operating point solution to a Schmidt trigger circuit changed with the computational platform.

Homotopy methods can often provide solutions to difficult nonlinear problems, including circuit analysis, even when conventional methods (e.g., Newton’s method) fail [9] [10]. This chapter gives an introduction to using homotopy algorithms (sometimes called continuation algorithms) in **Xyce**. The **Xyce** Reference Guide [3] provides a more complete description of solver options.

## 8.1.1 HOMOTOPY Algorithms Available in Xyce

Most of the several types of homotopy **Xyce** are accessed by setting `.options nonlin continuation=1`, which allows the user to sweep existing device parameters (models and instances), as well as a few reserved artificial parameter cases. The most obvious natural parameter to use is the magnitude(s) of independent voltage or current sources, the choice of which is equivalent to “source stepping” in SPICE. Section 8.2 provides a **Xyce** source-stepping example. For some circuits (as in the aforementioned Schmidt trigger), source stepping leads to turning points in the continuation.

A special **Xyce**-only homotopy, an algorithm designed specifically for MOSFET circuits [11], involves two internal MOSFET model parameters — one for the MOSFET gain, and the other for the nonlinearity of the current-voltage relationship. This algorithm is invoked with `.options nonlin continuation=2`, and has proven to be effective in some large MOSFET circuits. Section 8.4 provides a detailed example.

**Xyce** invokes another well-known SPICE method, “GMIN stepping,” with `.options nonlin continuation=3` or `.options nonlin continuation=gmin`, and is a special case where the parameter being swept is artificial. Section 8.5 provides an example of GMIN stepping.

## 8.2 Natural Parameter Homotopy

Figure 8.1 shows a natural parameter homotopy netlist with parameters pertinent to the homotopy algorithm highlighted in red. For this example, the parameter being swept is the DC value of the voltage source `VDDdev`. As a result, this example demonstrates a version of “source stepping” similar to that of SPICE.

### 8.2.1 Explanation of Parameters, Best Practice

Figure 8.1 also illustrates the following “best practice” rules:

```

THIS CIRCUIT IS A MOS LEVEL 1 MODEL CMOS INVERTER
.TRAN 20ns 30us 0 5ns
.PRINT tran v(vout) v(in) v(1)
.options timeint reltol=5e-3 abstol=1e-3
* HOMOTOPY Options

.options nonlin continuation=1
.options loca stepper=0 predictor=0 stepcontrol=1
+ conparam=VDDdev
+ initialvalue=0.0 minvalue=-1.0 maxvalue=5.0
+ initialstepsize=0.2 minstepsize=1.0e-4
+ maxstepsize=5.0 aggressiveness=1.0
+ maxsteps=100 maxnliters=200

VDDdev  VDD 0 5V
RIN IN 1 1K
VIN1 1 0 5V PULSE (5V 0V 1.5us 5ns 5ns 1.5us 3us)
R1  VOUT 0 10K
C2  VOUT 0 0.1p
MN1  VOUT IN 0 0 CD4012_NMOS L=5u W=175u
MP1  VOUT IN VDD VDD CD4012_PMOS L=5u W=270u
.MODEL cd4012_pmos PMOS
.MODEL cd4012_nmos NMOS
.END

```

**Figure 8.1.** Example natural parameter homotopy netlist. NOTE: This usage example of source stepping shows a circuit that does not require homotopy to run. Most circuits complex enough to require homotopy would not fit on a single page.

- `.options nonlin continuation=1`. Sets the algorithm to use natural parameter homotopy.
- `.options loca conparam=VDDdev`. If using natural parameter homotopy, it is necessary include a setting for `conparam`. It sets which input parameter to perform continuation. The parameter name is subject to the same rules as parameter used by the `.STEP` capability (section 7.4.2). In this case, the parameter is the magnitude of the DC voltage source, `VD-Ddev`. For this type of voltage source, it was possible to use the default device parameter (section 7.4.5)
- `.options loca initialvalue=0.0`. This is required.
- `.options loca maxvalue=5.0`. This is required.
- `.options loca stepcontrol=1` or `.options loca stepcontrol=adaptive`. This specifies homotopy steps to be adaptive, rather than constant. This is recommended.
- `.options loca maxsteps=100`. This sets the maximum number of continuation steps for each parameter.
- `.options loca maxnliters=200`. This is the maximum number of nonlinear iterations, and has precedence over the similar number that can be set on the `.options nonlin` line.
- `.options loca aggressiveness=1.0`. This refers to the step size control algorithm, and the value of this parameter can be anything from 0.0 to 1.0. 1.0 is the most aggressive. In practice, try starting with this set to 1.0. If the solver fails, then reset to a smaller number.

NOTE: Although using the magnitudes of independent voltage and current sources is a fairly obvious approach, it does not seem to work very well in practice.

## 8.3 Natural Multiparameter Homotopy

It is possible to use the natural parameter homotopy specification to have **Xyce** sweep multiple parameters in sequential order. This requires specifying many of the parameters in the `.options loca` statement as vectors, delineated by commas, rather than as single parameters.

NOTE: This is a usage example — the circuit itself does not require homotopy to run. Most circuits complex enough to require homotopy would not fit on a single page.

### 8.3.1 Explanation of Parameters, Best Practice

The solver parameters set in figure 8.2 are the same as those from figure 8.1, but many of them are in vector form. Specify any parameters specific to the continuation variable as a vector, including `conparam`, `initialvalue`, `minvalue`, `maxvalue`, `initialstepsize`, `minstepsize`, `maxstepsize`, and `aggressiveness`. Otherwise, the specification is identical.



```

THIS CIRCUIT IS A MOS LEVEL 1 MODEL CMOS INVERTER
.TRAN 20ns 30us 0 5ns
.PRINT tran v(vout) v(in) v(1)
.options timeint reltol=5e-3 abstol=1e-3
* HOMOTOPY Options

.options nonlin continuation=1
.options loca stepper=0 predictor=0 stepcontrol=adaptive
+ conparam=mosfet:gainscale,mosfet:nltermscale
+ initialvalue=0.0,0.0
+ minvalue=-1.0,-1.0
+ maxvalue=1.0,1.0
+ initialstepsize=0.2,0.2
+ minstepsize=1.0e-4,1.0e-4
+ maxstepsize=5.0,5.0
+ aggressiveness=1.0,1.0

VDDdev VDD 0 5V
RIN IN 1 1K
VIN1 1 0 5V PULSE (5V 0V 1.5us 5ns 5ns 1.5us 3us)
R1 VOUT 0 10K
C2 VOUT 0 0.1p
MN1 VOUT IN 0 0 CD4012_NMOS L=5u W=175u
MP1 VOUT IN VDD VDD CD4012_PMOS L=5u W=270u
.MODEL cd4012_pmos PMOS
.MODEL cd4012_nmos NMOS
.END

```

**Figure 8.2.** Example multiparameter homotopy netlist.  
NOTE: This netlist reproduces MOSFET homotopy with a manual specification.

## 8.4 MOSFET Homotopy

Figure 8.3 contains a MOSFET homotopy example netlist, and is the same circuit as was used in figure 8.3, except some of the parameters are different. As before, the lines pertinent to the homotopy algorithm are highlighted in red.

```
THIS CIRCUIT IS A MOS LEVEL 1 MODEL CMOS INVERTER
.TRAN 20ns 30us 0 5ns
.PRINT tran v(vout) v(in) v(1)
.options timeint reltol=5e-3 abstol=1e-3

* HOMOTOPY Options
.options nonlin continuation=mos

VDDdev VDD 0 5V
RIN IN 1 1K
VIN1 1 0 5V PULSE (5V 0V 1.5us 5ns 5ns 1.5us 3us)
R1 VOUT 0 10K
C2 VOUT 0 0.1p
MN1 VOUT IN 0 0 CD4012_NMOS L=5u W=175u
MP1 VOUT IN VDD VDD CD4012_PMOS L=5u W=270u
.MODEL cd4012_pmos PMOS
.MODEL cd4012_nmos NMOS
.END
```

**Figure 8.3.** MOSFET homotopy netlist example. NOTE: This is a usage example — the circuit itself does not require homotopy to run. Most circuits complex enough to require homotopy would not fit on a single page.

### 8.4.1 Explanation of Parameters, Best Practice

There are a few differences between the netlist in figures 8.1 and 8.3. This example shows one set of options, but there are numerous options of working combinations.

MOSFET homotopy requires only `.options nonlin continuation=2` or `.options nonlin continuation=mos` parameters, which specifies use of the special MOSFET homotopy. This is a two-pass homotopy, in which first a parameter concerning gain is swept from 0 to 1, and then a parameter relating to the nonlinearity of the transfer curve is swept from 0 to 1. The default parameters will work for a variety of MOSFET circuits, so it often will be unnecessary to override them using an `.options loca` line. However, it is possible to override the default parameters using the same `.options loca` parameters described in section 8.2.1.

## 8.5 GMIN Stepping

GMIN stepping is a type of homotopy commonly available in circuit simulators. Although SPICE automatically attempts GMIN stepping if the initial operating point fails, **Xyce** requires it to be manually specified by setting `continuation=3` or `continuation=gmin`. Figure 8.4 provides a netlist example of GMIN stepping.

```
THIS CIRCUIT IS A GMIN STEPPING EXAMPLE.
.TRAN 20ns 30us 0 5ns
.PRINT tran v(vout) v(in) v(1)
.options timeint reltol=5e-3 abstol=1e-3

* HOMOTOPY Options
.options nonlin continuation=gmin

VDDdev VDD 0 5V
RIN IN 1 1K
VIN1 1 0 5V PULSE (5V 0V 1.5us 5ns 5ns 1.5us 3us)
R1 VOUT 0 10K
C2 VOUT 0 0.1p
MN1 VOUT IN 0 0 CD4012_NMOS L=5u W=175u
MP1 VOUT IN VDD VDD CD4012_PMOS L=5u W=270u
.MODEL cd4012_pmos PMOS
.MODEL cd4012_nmos NMOS
.END
```

**Figure 8.4.** Example GMIN stepping netlist. NOTE: The continuation parameter is `gmin`. It can also be specified using `continuation=3`.

The name "GMIN stepping" can be somewhat confusing, as "GMIN" is also a user-specified device package parameter (unrelated to this algorithm) that one may set. In the device context, "GMIN" refers to a minimum conductance applied to many device models to enhance convergence. In the homotopy context, it refers to the conductance of resistors attached from every circuit node to ground.

The conductance, which is the continuation parameter, is initially very large, and is iteratively reduced until the artificial resistors have a very high resistance. At the end of the continuation, the resistors are removed from the problem. At this point, assuming the continuation has been successful, the original user-specified problem has been solved.

## 8.5.1 Explanation of Parameters, Best Practice

In general, GMIN stepping can be very useful. It should be considered the first option whenever a circuit fails to obtain an operating point. One advantage is that it has the potential to be successful for any circuit type. Unlike MOSFET homotopy, it doesn't require specific device models to be present to run.

## 8.6 Pseudo Transient

Pseudo transient continuation is very similar to GMIN stepping, in that both algorithms involve placing large artificial terms on the Jacobian matrix diagonal, and progressively making these terms smaller until the original circuit problem is recovered. One difference is, rather than doing a series on Newton solves, Pseudo transient does a single nonlinear solve while progressively modifying the pseudo transient parameter. Figure 8.5 provides an example of pseudo transient homotopy options.

```
* HOMOTOPY Options
.options nonlin continuation=9

.options loca
+ stepper=natural
+ predictor=constant
+ stepcontrol=adaptive
+ initialvalue=0.0
+ minvalue=0.0
+ maxvalue=1.0e12
+ initialstepsize=1.0e-6
+ minstepsize=1.0e-6
+ maxstepsize=1.0e6
+ aggressiveness=0.1
+ maxsteps=200
+ maxnliters=200
+ voltagescalefactor=1.0
```

**Figure 8.5.** Pseudo transient solver options example. NOTE:  
The continuation parameter is set to 9.

### 8.6.1 Explanation of Parameters, Best Practice

Pseudo transient has not been observed to be as successful as MOSFET-homotopy for large MOSFET circuits. It may, however, be a good candidate for difficult non-MOSFET circuits as it tends to be faster because the total number of matrix solves is smaller.

y

# 9. Results Output and Evaluation Options

## Chapter Overview

This chapter illustrates how to output simulation results to data or output files and includes the following sections:

- Section 9.1, *Control of Results Output*
- Section 9.2, *Additional Output Options*
- Section 9.3, *Output Analysis*
- Section 9.4, *Graphical Display of Solution Results*

# 9.1 Control of Results Output

**Xyce** supports one solution output command, `.PRINT`, which is quite flexible, and supports several output formats.

## 9.1.1 `.PRINT` Command

The `.PRINT` command sends the analysis results to an output file. **Xyce** supports several options on the `.PRINT` line of netlists that control the format of the output. The syntax for the command is as follows:

■ `.PRINT <analysis type> [options] <output variable> [<output variable>]*`

Table 9.1 gives the various options currently available to the `.PRINT` command.

**Table 9.1.** `.PRINT` command options.

Option...	Action...
FORMAT= <STD NOINDEX PROBE TECPLOT RAW CSV>	Controls the output format. See Table 9.2. The <i>default</i> is STD.
FILE=<filename>	Output filename. The <i>default</i> is the netlist filename with “.prn” appended. <code>foo.cir.prn</code> , where <code>foo.cir</code> is the input netlist filename.
WIDTH=<field-width>	Column width for the output data
PRECISION=<floating-point-precision>	Number of significant digits past the decimal point
FILTER=<floor-value>	Absolute value below which output variables will be printed as 0.0
DELIMITER=<TAB COMMA>	Alternate delimiter between columns of output in the STD output format.

Table 9.2 gives the various output formats currently available to the `.PRINT` command.



**Table 9.2.** .PRINT FORMAT options.

Format...	Action...
STD	Outputs data in standard columns
NOINDEX	Outputs the same as the STD except the index column is omitted.
PROBE	Output is formatted to be compatible with the PSpice Probe plotting utility.
RAW	Output conforms to the Spice binary rawfile. Use the <b>-a</b> command line option to produce an ascii rawfile.
TECPLOT	Output for use in the TecPlot graphics package.
CSV	Produces a comma separated value format.

The <output variable> parameter can be nodal voltages or device currents, as given by

- V(<node name>)
- V(<node name>, <node name>) (the voltage difference between the first and second nodes)
- I(<two-terminal device>)
- Ik(<three-or-more-terminal device>) (the k indicates the device node from which to acquire the value, which is device specific; see the **Xyce** Reference Guide [3] for details)

Voltage variables specified in the frequency domain have special processing to handle complex results. For file formats which have a complex output capability, the complex value is written. However, for file formats, such as STD and CSV, the complex value is written as two columns of data, the real part followed by the imaginary part. Pseudo names may also be used to compute scalar values from a complex voltage variable. These are given in Table 9.3.

**Table 9.3.** Pseudo Variables for Complex Output

Variable	Definitions
VR(node)	Voltage Real Component
VI(node)	Voltage Imaginary Component
VM(node)	Voltage Magnitude
VP(node)	Voltage Phase, Radians
VDB(node)	Voltage Magnitude, Decibels

In addition to the above, internal device variables can be specified as an <output variable>. These take the form, N(device variable). The format of the device variable called by N is device-specific, and exact forms can be found in the **Xyce** Reference Guide [3].

Finally, a parameter or expression may also be specified as an <output variable>. To do so, enclose the parameter or expression within curly braces ({}). See Section 4.3 for a description of parameters and expressions.

**Example:**

```
.PRINT TRAN FILE=Output.prn V(3) I(R3) ID(M5) V(4)
.PRINT DC FORMAT=TECPLOT FILE=Output.dat V(2) {I(C3)+abs(V(4))*5.0}
.print AC v(3)
```

## 9.2 Additional Output Options

### 9.2.1 .OPTIONS OUTPUT Command

The main purpose of the .OPTIONS OUTPUT command is to provide control of the interval at which data is written to files specified by .PRINT TRAN commands. This can be especially useful in controlling the size of the results file for simulations that require a large number of time steps. Also, reducing the output frequency from the default, which outputs results at every time-step, provides an additional benefit of improved performance.

The format for controlling the output frequency is:

```
■ .OPTIONS OUTPUT INITIAL_INTERVAL=<interval> [<t0> <i0> [<t1> <i1> ...]]
```

where INITIAL\_INTERVAL=<interval> specifies the starting interval time for output and <tx ix> specifies later simulation times (tx) where the output interval will change to (ix).

The following example shows the output being requested (via the netlist .OPTIONS OUTPUT command) every  $.1\mu s$  for the first  $10\mu s$ , every  $1\mu s$  for the next  $10\mu s$ , and every  $5\mu s$  for the remainder of the simulation:

**Example:**            .OPTIONS OUTPUT INITIAL\_INTERVAL=.1us 10us 1us 20us 5us

## 9.3 Output Analysis

### 9.3.1 .MEASURE

**Xyce** supports analysis of the data from a simulation through the .MEASURE command. Using .MEASURE one can locate extrema in a voltage or current node, calculate integrals, derivatives,

Fourier transforms, and locate transient events. The general syntax is:

```
■ .MEASURE <analysis type> <measure name> <measure type>
   <simulation variable> [qualifiers]
```

where <analysis type> is the analysis under which the measure should be calculated. Currently only transient analysis (.TRAN) is supported. The <measure name> is the name by which this measure is referred. This name is used in the summary output at the end of the simulation to report the value of this measure. The <measure type> is the type of calculation which be done. Currently supported measure types are:

- **AVG**: Computes the arithmetic mean.
- **DERIV**: Computes the derivative of a simulation variable.
- **DUTY**: Fraction of time that a given simulation variable is greater than ON and does not fall below OFF (ON and OFF are defined later in this section).
- **FOUR**: Calculates the Fourier transform of the solution variable for the .TRAN analysis type using the fundamental frequency AT. By default, the DC component and first nine harmonics are computed; more can be reported by setting NUMFREQ to the desired value. More interpolation points can be used in the Fourier analysis by setting GRIDSIZE, which is 200 by default.
- **FREQ**: An estimate of the frequency of a solution variable found by cycle counting during the simulation. Thresholds are defined through the values of ON and OFF.
- **INTEG**: Calculates the integral of a solution variable through second order numerical integration.
- **MAX**: Returns the maximum value of a solution variable.
- **MIN**: Returns the minimum value of a solution variable.
- **OFF\_TIME**: Returns the time that a solution variable is below OFF, and not greater than ON for the simulation.
- **ON\_TIME**: Returns the time that a solution variable is above ON, and not less than OFF for the simulation.
- **PP**: Returns the difference between the maximum value and the minimum value of a solution variable during the simulation.
- **RMS**: Computes the root-mean-squared value of a solution variable.
- **WHEN**: Returns the time when a solution variable reaches a specified fixed value or is equal to another solution variable.

The <simulation variable> specifies a voltage or current node that will be used in this measure, such as V(a). The measure WHEN is different from the other measures in that it can take one or two

solution variables. For example, `WHEN v(a)=5` returns the time when `v(a)` equals 5. Or, if `WHEN V(a) = V(b)` is specified, the time when `V(a)` equals `V(b)` is returned.

The `.MEASURE` command can also take optional [qualifiers] that limit the time window when `.MEASURE` is applied. The [qualifiers] also place numeric limits on what state a value is considered to be in (e.g., ON and OFF), and provide numeric qualification on comparisons of values (e.g., MINVAL). The supported qualifiers are:

- `TD=value` A time delay before which the measurement should be taken or checked.
- `RISE=r|LAST` The number of rises after which the measurement should be checked. If `LAST` is specified, then the last rise found in the simulation will be used.
- `FALL=f|LAST` The number of falls after which the measurement should be checked. If `LAST` is specified, then the last fall found in the simulation will be used.
- `CROSS=c|LAST` The number of zero crossings after which the measurement should be checked. If `LAST` is specified, then the last zero crossing found in the simulation will be used.
- `MINVALUE=value` An allowed absolute difference between the simulation variable and the variable to which it is being compared. This has a default value of 1.0e-12. One may need to specify a larger value to avoid missing the test condition in a transient run.
- `ON=value` The value at which a signal is considered to be on for frequency, duty and on time calculations
- `OFF=value` The value at which a signal is considered to be off for frequency, duty and off time calculations.

An example of using `.measure` is shown in the following netlist:

```
VS 1 0 SIN(0 1.0 1KHZ 0 0)
VP 2 0 PULSE( 0 1 0.2ms 0.2ms 0.2ms 1ms 2ms )

R1 1 0 100
R2 2 0 100

.TRAN 0 10ms
.PRINT TRAN FORMAT=NOINDEX V(1) V(2)

.MEASURE TRAN avg1 AVG V(1)
.MEASURE TRAN avg2 AVG V(2)

.MEASURE TRAN duty1 DUTY V(1) ON=0.75 OFF=0.25
```

The measure `avg1` returns the average of `v(1)`, and `avg2` returns the average of `v(2)`. Additionally, `duty1` computes the fraction of time that `v(1)` is above 0.75 V, without falling below 0.25 V.

The next netlist provides an example of using the `when` measure:

```
VS 1 0 SIN(0 1.0 1KHZ 0 0)
VP 2 0 PULSE( 0 100 0.2ms 0.2ms 0.2ms 1ms 2ms )

R1 1 0 100
R2 2 0 100

.TRAN 0 10ms 0 1.0e-5
.PRINT TRAN FORMAT=NOINDEX V(1) V(2)

.MEASURE TRAN hit1_75 WHEN V(1)=0.75 MINVAL=0.02
.MEASURE TRAN hit2_75 WHEN V(1)=0.75 MINVAL=0.08 RISE=2
```

In the above netlist, the measure called `hit1_75` will return the simulation time where `v(1)` reaches a value of 0.75, while `hit2_75` returns the second time that `v(1)` reaches a value of 0.75. The `MINVAL` option acts at an absolute tolerance in this case. So, the above measure statements are more exactly interpreted as `hit1_75` is the simulation time when `v(1)` reaches a value of  $0.75 \pm 0.02$  and `hit2_75` is the simulation time when `v(1)` reaches a value of  $0.75 \pm 0.08$  on its second rise.

## 9.3.2 .FOUR

Fourier analysis can be performed as a part of the transient analysis using the `.FOUR` command. The general syntax is:

- `.FOUR freq ov1 <ovn>*`

where `freq` is the fundamental frequency used for Fourier analysis. The `ov1` parameter is the desired solution variable to be analyzed, specifically

- `V(<node name>)`
- `V(<node name>, <node name>)` (the voltage difference between the first and second nodes)
- `I(<two-terminal device>)`
- `Ik(<three-or-more-terminal device>)` (see the `.PRINT` section, 9.1.1, for more detail)
- `N(device variable)` (see the `.PRINT` section, 9.1.1, for more detail)
- The pseudo-variables given in Table 9.3 for complex output handling

At least one solution variable must be specified, but Fourier analysis can be performed on several solution variables for each fundamental frequency, `freq`. Multiple `.FOUR` lines may be used in a

netlist. All results from Fourier analysis will be returned to the user in a file with the same name as the netlist file suffixed with a `.four`.

Fourier analysis is performed over the last period ( $1/\text{freq}$ ) of the transient simulation. The dc component and the first nine harmonics are calculated. The number of harmonics computed by `.FOUR` is static. This is the main difference between `.FOUR` and the Fourier analysis in `.MEASURE`, where the later will allow the user to select the number of harmonics. The default options for the Fourier analysis in `.MEASURE` is the same as `.FOUR`. For instance, these two lines will result in the same Fourier analysis:

```
.FOUR 20MEG V(2)
.MEASURE TRAN FOURV2 FOUR V(2) AT=20MEG
```

The Fourier analysis in `.MEASURE` will allow for more harmonics to be computed using the `NUMFREQ` option and more interpolation points to be used in the Fourier analysis with `GRIDSIZE`. For instance, to compute twenty harmonics (including the dc component), the previous `.MEASURE` line can be amended to:

```
.MEASURE TRAN FOURV2 FOUR V(2) AT=20MEG NUMFREQ=20
```

To increase the number of interpolation points from 200, which is the default, to 500, the line can be amended to:

```
.MEASURE TRAN FOURV2 FOUR V(2) AT=20MEG NUMFREQ=20 GRIDSIZE=500
```

For maximum accuracy of the Fourier analysis, it is recommended that the time integration option `DELMAX` should be set to `period/100`. This is the preferred approach to improving the accuracy of the Fourier analysis over increasing the number of interpolation points.

### 9.3.3 `.SENS`

The `.SENS` command instructs **Xyce** to calculate the steady-state (DC) sensitivities of an output expression with respect to a specified list of circuit parameters. The syntax for the command is as follows:

- `.SENS objfunc=<output expression> param=<circuit parameter(s)>`
- `.options SENSITIVITY [direct=<1 or 0>] [adjoint=<1 or 0>]`

The parameter objective function parameter, `objfunc`, is required. The list of circuit parameters must have at least one entry as well. **Xyce** can compute a direct sensitivity, an adjoint sensitivity, or both. An example of using `.SENS` is shown in the following netlist:

```

R1 A B 10.0
R2 B 0 10.0

* input nodes:
Va A 0 5

.dc Va 5 5 1
.print dc v(A) v(B)

.SENS objfunc={0.5*(V(B)-3.0)**2.0} param=R1:R,R2:R
.options SENSITIVITY direct=1 adjoint=1

.END

```

The output for this particular example is:

```

Direct Sensitivities:
R1:R d0dp = 6.2500e-02
R2:R d0dp = -6.2500e-02

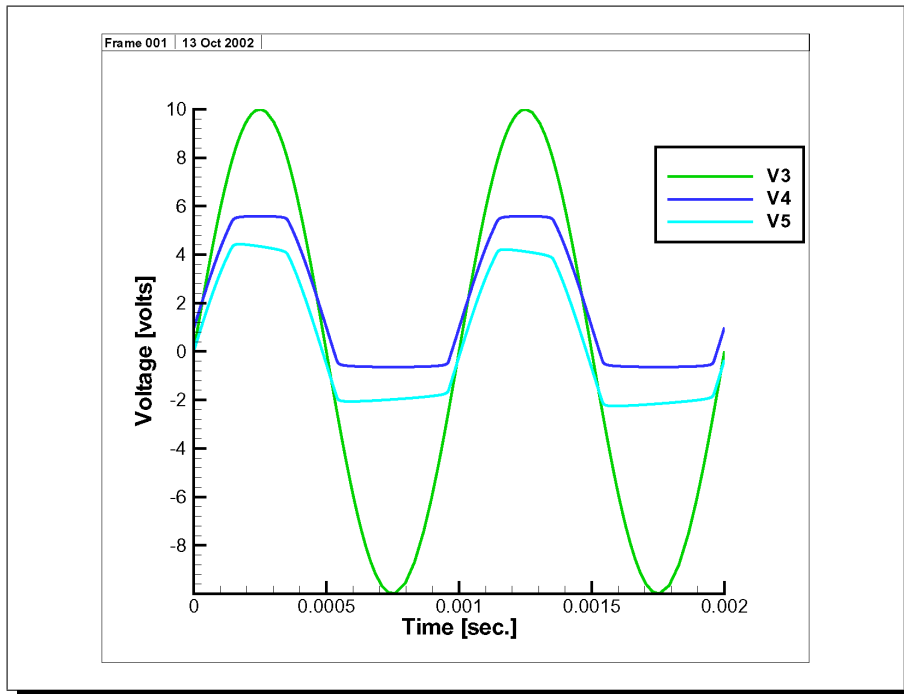
Adjoint Sensitivities:
R1:R d0dp = 6.2500e-02
R2:R d0dp = -6.2500e-02

```

The `.SENS` capability can only be used for DC calculations. If performing a sweep, it computes the sensitivities for the final sweep step.

## 9.4 Graphical Display of Solution Results

Although **Xyce** does not provide integrated graphical display options, it produces output in a form that may readily be used with commonly available graphical tools, including TecPlot, gnuplot, and MS Excel (see figure 9.1 for an example plot using TecPlot, <http://www.amtec.com>). The standard **Xyce** print format (`FORMAT=STD` or `FORMAT=NOINDEX`) is well suited for use with gnuplot. Comma separated variable (`FORMAT=CSV`) is the best choice for import into Excel. `FORMAT=TECPLOT` produces output specifically targeted at the TecPlot tool. And by using the `FORMAT=PROBE` option to the `.PRINT` command, **Xyce** is able to output `.csd` files that can be read by the PSpice Probe utility to view the results. See the PSpice Users Guide [4] for instructions on using the Probe tool, and the **Xyce** Reference Guide [3] for details on the `.PRINT` command options.



**Figure 9.1.** TecPlot plot of diode clipper circuit transient response from Xyce .prn file.



# 10. Guidance for Running **Xyce** in Parallel

## Chapter Overview

This chapter provides guidance for running a parallel version of **Xyce**, and includes the following sections:

- Section 10.1, *Introduction*
- Section 10.2, *Problem Size*
- Section 10.3, *Linear Solver Options*
- Section 10.4, *Transformation Options*

## 10.1 Introduction

**Xyce** is designed from the ground up to be distributed-memory parallel, supported by the message-passing interface (MPI) standard. Although many of the issues pertinent to running in parallel are still being researched, **Xyce** is mature enough that some general principles have emerged for efficiently running problems in a parallel environment. In addition to the information in this chapter, reference [12] provides supplemental information about **Xyce** parallel performance.

Parallel simulations must be run from the command line. Section 2.2.1 provides information about the parallel execution syntax for **Xyce**.

## 10.2 Problem Size

Running **Xyce** in parallel is often useful for circuits with thousands of devices or more. However, due to the overhead of interprocessor communication, there is an optimal number of processors that will achieve the best performance. This number is dependent upon many factors, including the number and type of devices, topology of the circuit, and the characteristics of the computing architecture. It is difficult to know a priori what this optimal number of processors is. However, it is apparent when that optimal number is exceeded because, as the number of processors is increased, the total simulation time will also increase. This is due to the increasing amount of required communication and decreasing amount of work per processor. In other words, the benefit of distributing the problem is outweighed by the communication overhead, so increasing the processor count beyond this optimal point is counterproductive.

### 10.2.1 Ideal Problem Size

In general, a circuit needs to be relatively large to take full advantage of the parallel capability of **Xyce**. However, parallelism is achieved in two distinct phases of the code: the device evaluation and the linear solve. The device evaluation is, as the name implies, the evaluation of all the device equations in order to compute the residual vector and Jacobian entries for Newton's method. Xyce distributes the number of devices over the number of processors in parallel, so their evaluation enables speedups in the total simulation time even for thousands of devices.

The linear solve phase is more computationally complex. The Jacobian matrix generated by most circuits is sparse and has heterogeneous structure, in that there is not a regular sparsity pattern in the matrix nonzeros. Sparse, direct linear solvers have proven to be efficient on these types of linear systems up into the tens to hundreds of thousands of unknowns. They become less efficient for linear systems in the hundreds of thousands of unknowns. This is where iterative linear solvers can provide scalable performance because of their inherent parallelism. Unfortunately, the effectiveness of iterative linear solvers is dependent upon preconditioning the linear system (see Section 10.3.5). The benefit of direct over iterative linear solvers is that they rarely fail to compute a solution, so direct linear solvers are the more robust option for enabling simulations to complete.

In general, there are three modes in which **Xyce** can be executed: "Serial load, serial solve", "Parallel load, serial solve", and "Parallel load, parallel solve". Each of these modes optimizes the

amount of available parallelism for a given linear system size, see Table 10.1 for a summary. The “load” refers to the device evaluation phase combined with the assembly of the Jacobian matrix and residual vector, the “solve” refers to the linear solve phase. “Serial load, serial solve” is the only mode of computation that a serial version of **Xyce** will perform, but it can also be obtained in a parallel version of Xyce by using only one MPI processor. Both the “Parallel load” simulation modes require a parallel build of **Xyce**, where the linear solver method can be a direct method (“serial solve”) or iterative method (“parallel solve”) using the options discussed in Section 10.3. Hybrid linear solvers, which combine the best attributes of both direct and iterative methods, provide both a robust and scalable option. They are not reflected in Table 10.1, but more information about these types of linear solvers will be discussed in Section 10.3.6.

**Table 10.1.** Xyce simulation modes.

Mode	Linear System Size	Reason
“Serial load, serial solve”	$10^0 - 10^2$	MPI overhead cannot speed up device evaluation or linear solve.
“Parallel load, serial solve”	$10^3 - 10^4$	Distributed device evaluations can speed up the simulation, but iterative linear solvers are not more efficient than direct methods.
“Parallel load, parallel solve”	$10^5$ or more	Distributed device evaluations can speed up the simulation and so can iterative linear solvers, if an efficient preconditioner is available.

## 10.2.2 Smallest Possible Problem Size

Circuits consist of a discrete set of components (voltage nodes, devices, etc.). For parallel simulation, it is preferable that **Xyce** be able to put at least one discrete component of the problem on each processor. In practice, this means the circuit should be distributed across fewer processors than the number of nodes and devices it contains.

## 10.3 Linear Solver Options

The different linear solvers available in **Xyce** are:

- KLU
- SuperLU and SuperLU DIST (optional)
- The AztecOO iterative solver library
- The Belos iterative solver library

■ The ShyLU hybrid solver library (optional)

AztecOO and Belos are the parallel iterative solvers and KLU and SuperLU (optional) are the serial direct solvers that are available for both serial and parallel builds of Xyce. If KLU or SuperLU is used with a parallel version of **Xyce**, the devices are evaluated and linear problem is assembled in parallel, but the linear system is solved in serial on processor 0. This can be quite effective for circuits with tens of thousands of devices or fewer (see Table 10.1). The ShyLU hybrid linear solver, which combines the robustness of a direct solver with the scalability of an iterative solver, will be discussed in Section 10.3.6.

The user can specify the solver through the `.OPTIONS LINSOL` control line in the netlist. The default linear solver used by **Xyce** is described in Table 10.2. By default, a parallel version of **Xyce** uses AztecOO as the linear solver when the linear system is larger than a thousand unknowns. For any linear system smaller than a thousand unknowns, **Xyce** uses KLU as the linear solver. A serial version of **Xyce** uses KLU as its default linear solver. To use a solver other than the default the user needs to add the option “`TYPE=<solver>`” to the `.OPTIONS LINSOL` control line in the netlist, where `<solver>` is ‘KLU,’ ‘SUPERLU,’ ‘SUPERLUDIST,’ ‘AZTECOO,’ ‘BELOS,’ or ‘SHYLU.’

**Table 10.2.** Xyce default linear solver.

Solver	Version	Linear System Size
KLU	Serial	<i>all</i>
KLU	Parallel	1 – 1000 unknowns
AztecOO	Parallel	1001+ unknowns

### 10.3.1 KLU

KLU is a serial, sparse direct solver native to the Amesos package in Trilinos [13] and is the default solver for serial builds of **Xyce**. KLU is the default solver for small circuits in parallel builds of **Xyce** as well, but this requires the linear system to be solved on one processor and the solution communicated back to all processors. As long as the linear system can fit on one processor, KLU is often a superior approach to using an iterative linear solver.

Some of the solver parameters for KLU can be altered through the ‘`.OPTIONS LINSOL`’ control line in the netlist. Table 10.3 lists solver parameters and their default values for KLU.

### 10.3.2 SuperLU and SuperLU DIST

SuperLU is a serial, sparse direct solver and SuperLU DIST is a parallel, sparse direct solver with an interface in the Amesos package. SuperLU and SuperLU DIST support are *optionally* built in **Xyce**, so they are not available by default in any Xyce build or provided binary. Furthermore, to enable SuperLU and SuperLU DIST support in **Xyce**, it is necessary to build SuperLU and SuperLU DIST support in Amesos/Trilinos. Similar to KLU, SuperLU can be used in a parallel

**Table 10.3.** KLU linear solver options.

Option	Description	Default Value
KLU_REPIVOT	Recompute pivot order each solve	1 (true)
OUTPUT_LS	Write out linear systems solved by KLU to file every # solves	0 (false)
OUTPUT_BASE_LS	Write out linear systems before any transformations to file every # solves	0 (false)
OUTPUT_FAILED_LS	Write out linear systems KLU failed to solve to file	0 (false)

version of **Xyce**, but the linear system is solved on one processor. SuperLU DIST can only be used in a parallel version of Xyce, the Amesos interface handles the redistribution of the matrix into the format required by SuperLU DIST. **Xyce** does not allow modifications to SuperLU and SuperLU DIST solver parameters.

### 10.3.3 AztecOO

AztecOO is a package in Trilinos [13] that offers an assortment of iterative linear solver algorithms. **Xyce** uses the Generalized Minimal Residual (GMRES) method [14] from this suite of iterative solvers. Some of the solver parameters for GMRES can be altered through the `.OPTIONS LINSOL` control line in the netlist. Table 10.4 provides a list of solver parameters for AztecOO and their default values.

**Table 10.4.** AztecOO linear solver options.

Option	Description	Default Value
AZ_max_iter	Maximum allowed iterations	500
AZ_tol	Iterative solver (relative residual) tolerance	1.0e-12
AZ_kspace	Krylov subspace size	500
OUTPUT_LS	Write out linear systems solved by AztecOO to file every # solves	0 (false)
OUTPUT_BASE_LS	Write out linear systems before any transformations to file every # solves	0 (false)

#### Common AztecOO Warnings

If **Xyce** is built with the verbosity enabled for the linear algebra package, it is not uncommon to see warnings from AztecOO usually indicating the solver returned unconverged due to a numerical issue.

**NOTE:** AztecOO warnings *do not* indicate the entire simulation has failed, **Xyce** uses a hierarchy of solvers so if the iterative linear solver fails, the nonlinear solver or time integrator will usually make adjustments and attempt the step again; so the warnings can often be ignored. If the entire simulation eventually fails (i.e., gets a “time-step-too-small” error), then the AztecOO warnings might contain clues as to what went wrong.

The simplest reason for AztecOO to return unconverged would be when the maximum number of iterations is reached, resulting in the following warning:

```
*****  
Warning: maximum number of iterations exceeded without convergence  
*****
```

Another reason AztecOO may return unconverged is when the GMRES Hessenberg matrix is ill-conditioned, which is usually a sign that the matrix and/or preconditioner is nearly singular, resulting in the following warning:

```
*****  
Warning: the GMRES Hessenberg matrix is ill-conditioned. This may  
indicate that the application matrix is singular. In this case, GMRES  
may have a least-squares solution.  
*****
```

It is also common to lose accuracy when either the matrix or preconditioner, or both, are nearly singular. GMRES relies on an estimate of the residual norm, called the recursive residual, to determine convergence. **Xyce** uses the recursive residual instead of the actual residual for computational efficiency. However, numerical issues can cause the recursive residual to differ from the actual residual. When AztecOO detects but cannot rectify this situation, it outputs the following warning:

```
*****  
Warning: recursive residual indicates convergence  
though the true residual is too large.  
*****
```

Sometimes this occurs when storage is overwritten (e.g. the solution vector was not dimensioned large enough to hold external variables). Other times, this is due to roundoff. In this case, the solution has either converged to the accuracy of the machine or intermediate roundoff errors occurred preventing full convergence. In the latter case, try solving again using the new solution as an initial guess.

```
*****
```

## 10.3.4 Belos

Belos is a package in Trilinos [13] that offers an assortment of iterative linear solver algorithms. Many of the algorithms available in Belos can also be found in AztecOO. However, Belos offers a few computational advantages because its solvers are implemented using templated C++. In particular, AztecOO can solve linear systems only in double-precision arithmetic, while Belos can solve linear systems that are complex-valued or in extended-precision arithmetic. At this time, **Xyce** is using a subset of Belos capabilities, the default method is GMRES, and the interface to Belos will recognize most of the AztecOO linear solver options, as shown in Table 10.5.

**Table 10.5.** Belos linear solver options.

Option	Description	Default Value
AZ_max_iter	Maximum allowed iterations	500
AZ_tol	Iterative solver (relative residual) tolerance	1.0e-12
AZ_kspace	Krylov subspace size	500
OUTPUT_LS	Write out linear systems solved by Belos to file every # solves	0 (false)
OUTPUT_BASE_LS	Write out linear systems before any transformations to file every # solves	0 (false)

## 10.3.5 Preconditioning Options

Iterative linear solvers often require the assistance of a preconditioner to efficiently compute a solution of the linear system

$$Ax = b \tag{10.1}$$

to the requested accuracy. A preconditioner,  $M$ , is an approximation to the original matrix  $A$  that is inexpensive to solve. Then (10.1) can be rewritten to include this (right) preconditioner as

$$AM^{-1}y = b, \tag{10.2}$$

where  $x = M^{-1}y$  is the solution to the original linear system. If  $M = A$ , then the solution to the linear system is found in one iteration. In practice,  $M$  is a good approximation to  $A$ , then it will take few iterations to compute the solution of the linear system to the requested accuracy. By default, **Xyce** uses a non-overlapped additive Schwartz preconditioner with an incomplete LU factorization on each subdomain [15]. The parameters of the incomplete LU factorization are found in Table 10.6. This is a simple preconditioner that always works, but is not always the most effective, so other preconditioning options will be presented in this section.

**Xyce** provides access to preconditioning packages in Trilinos [13], such as Itpack and ML (optionally), through an expanded preconditioning interface. If modifications to the preconditioner are

necessary, the user may specify the preconditioner through the ‘.OPTIONS LINSOL’ control line in the netlist. Table 10.6 provides a list of preconditioner parameters and their default values.

**Table 10.6.** Preconditioner options.

Option	Description	Default Value
prec_type	Preconditioner	lfpack
AZ_ilut_fill	ILU fill level	2.0
AZ_drop	ILU drop tolerance	1.0e-3
AZ_overlap	ILU subdomain overlap	0
AZ_athresh	ILU absolute threshold	0.0001
AZ_rthresh	ILU relative threshold	1.0001
ML_MAX_LEVEL	ML maximum allowable levels	5
USE_IFPACK_FACTORY	Additive Schwarz w/ KLU subdomain solve	0 (false)
USE_AZTEC_PRECOND	Use native ILU from AztecOO package	0 (false)

In practice, the choice of an effective preconditioner is highly problem dependent. By default, **Xyce** provides a preconditioner that works for most circuits, but is not the best preconditioner for all circuits. One simple modification to the default preconditioner that often makes it more effective is the use of a sparse direct solver on each subdomain, instead of an inexact factorization:

```
.OPTIONS LINSOL USE_IFPACK_FACTORY=1
```

This preconditioner will fail if there is a singular subdomain matrix because the KLU solver on that subdomain will fail. If numerical difficulties are not encountered during the simulation, this preconditioner is superior to inexact factorizations. A more advanced preconditioner that has been effective for certain types of circuits uses the block triangular form (BTF) permutation of the original matrix before generating the additive Schwarz preconditioner. This preconditioner, which is published in [16], will be presented in Section 10.4.4.

### 10.3.6 ShyLU

ShyLU is a package in Trilinos [13] that provides a hybrid linear solver designed to be a black-box algebraic solver [17]. ShyLU support is *optionally* built in **Xyce**, so it is not available by default in any Xyce build or provided binary. Furthermore, to enable ShyLU support in **Xyce**, it is necessary to build the ShyLU package in Trilinos.

ShyLU is hybrid in both the parallel programming sense - using MPI and threads - and in the mathematical sense - using features from direct and iterative methods. **Xyce** uses ShyLU as a global Schur complement solver [15]. This solver can be expensive, but also has proven to be a robust and scalable approach for circuit matrices [18].

ShyLU is under active development and testing in Xyce, so a minimum number of options are provided to the user for controlling this flexible solver. For instance, the diagonal blocks of the partitioned matrix are solved using KLU, while the Schur complement is solved using an iterative method (AztecOO’s GMRES specifically). The matrix partitioning is generated using a wide



separator, which is a conventional vertex separator where all the vertices that are adjacent to the separator in one of the subgraphs are added in. This solution approach is static, the only options that can be modified are shown in Table 10.7. This includes the maximum number of iterations and solver tolerance used by GMRES and the dropping threshold that ShyLU uses to generate a preconditioner for GMRES.

**Table 10.7.** ShyLU linear solver options.

Option	Description	Default Value
AZ_max_iter	Maximum allowed iterations	30
AZ_tol	Iterative solver (relative residual) tolerance	1.0e-12
ShyLU_rthresh	Relative dropping threshold for Schur complement preconditioner	1.0e-3
OUTPUT_LS	Write out linear systems solved by ShyLU to file every # solves	0 (false)
OUTPUT_BASE_LS	Write out linear systems before any transformations to file every # solves	0 (false)

## 10.4 Transformation Options

Transformations are often used to permute the original linear system to one that is easier or more efficient for direct or iterative linear solvers. **Xyce** has many different permutations that can be applied to remove dense rows and columns from a matrix, reduce fill-in, find a block triangular form, or partition the linear system for improved parallel performance.

### 10.4.1 Removing Dense Rows and Columns

The transformation that reduces the linear system through removal of all rows and columns with single non-zero entries in the matrix is called singleton filtering. The values associated with these removed entries can be resolved in a pre- or post-processing phase with the linear solve. A by-product of this transformation is a more tractable and sparse linear system for the load balancing and linear solver algorithms. This functionality can be turned on by adding 'TR\_SINGLETON\_FILTER=1' to the '.OPTIONS LINSOL' control line in the netlist. This option is enabled by default whenever iterative solvers are used in **Xyce**.

### 10.4.2 Reordering the Linear System

Approximate Minimum Degree (AMD) ordering is a symmetric permutation that reduces the fill-in for direct factorizations. If given a nonsymmetric matrix  $A$ , the transformation computes the AMD ordering of  $A + A^T$ . This functionality may be turned on by adding 'TR\_AMD=1' to the '.OPTIONS LINSOL' control line in the netlist. For parallel builds of **Xyce**, AMD ordering is enabled by default whenever iterative solvers are used. In parallel, the AMD ordering is performed only on the local

graph for each processor, not the global graph. This is to reduce the fill-in for the incomplete LU factorization used by the additive Schwartz preconditioner, see Section 10.3.5.

### 10.4.3 Partitioning the Linear System

Partitioning subdivides the linear system and then distributes it to the available processors. A good partition can have a dramatic effect on the parallel performance of a circuit simulation tool. There are two key components to a good partition:

- Effective load balance
- Minimizing communication overhead.

An effective load balance ensures the computational load of the calculation is equally distributed among available processors. Minimizing communication overhead seeks to distribute the problem in a way to reduce impacts of underlying message passing during the simulation run. For runs with a small number of devices per processor the communication overhead becomes the critical issue, while for runs with larger numbers of devices per processor the load balancing becomes more important.

**Xyce** provides for graph and hypergraph partitioning via the **Zoltan** library of parallel partitioning heuristics integrated into **Xyce**. The Isorropia package in Trilinos provides access to **Zoltan** and can be controlled through the `‘.OPTIONS LINSOL’` control line in the netlist. Table 10.8 provides the partitioning options and their default parameters. For parallel builds of **Xyce**, when iterative solvers are used, **Isorropia** is enabled by default to use graph partitioning via ParMETIS. The linear system is statically load balanced at the beginning of the simulation based on the graph of the Jacobian matrix.

**Table 10.8.** Partitioning options.

Option	Description	Default Value
TR_PARTITION	Partitioning package	0 (none), serial, 1 (Isorropia), parallel
TR_PARTITION_TYPE	Isorropia partitioner type	GRAPH

**Xyce** includes an expanded partitioning interface to allow the user to access multiple partitioners through Isorropia. Users may change the partitioner provided by adding `‘TR_PARTITION_TYPE’` to the `‘.OPTIONS LINSOL’` control line in the netlist. There are two options for partitioning: graph (`‘TR_PARTITION_TYPE=GRAPH’`) and hypergraph (`‘TR_PARTITION_TYPE=HYPERGRAPH’`). Occasionally it is desirable to turn off the partitioning option, even for parallel simulations. To do so, users can add the `‘TR_PARTITION=0’` to the `‘.OPTIONS LINSOL’` control line.

These techniques can be very effective for improving the efficiency of the iterative linear solvers. See the **Zoltan User Guide** [19] for more details.

## 10.4.4 Permuting the Linear System to Block Triangular Form

The block triangular form (BTF) permutation is often useful for direct and iterative solvers, enabling a more efficient computation of the linear system solution. In particular, the BTF permutation has shown promise when it is combined with an additive Schwartz preconditioner (see Section 10.3.5) in the simulation of circuits with unidirectional flow.

The global BTF transformation computes the permutation of the linear system to block triangular form, and uses the block structure to partition the linear system. The partitioning can be a simple linear distribution of block rows, 'TR\_GLOBAL\_BTF=1', or a hypergraph partitioning of block rows, 'TR\_GLOBAL\_BTF=2.' As the global BTF transformation includes elements of other transformations, it is imperative to turn off other linear solver options. To use the global BTF, the linear solver control line in the netlist should contain:

```
.OPTIONS LINSOL TR_GLOBAL_BTF=<1,2> TR_SINGLETON_FILTER=1  
+ TR_AMD=0 TR_PARTITION=0
```

This transformation is only useful in parallel when using a preconditioned iterative solver. It is often more effective when combined with the exact factorization of each subdomain, given by the 'USE\_IFPACK\_FACTORY=1' option. In practice, the structure that this transformation takes advantage of is found in CMOS memory circuits [16].

# 11. Handling Power Node Parasitics

## Chapter Overview

This chapter includes the following sections:

- Section 11.1, *Power Node Parasitics*
- Section 11.2, *Two Level Algorithms Overview*
- Section 11.3, *Examples*
- Section 11.4, *Restart*

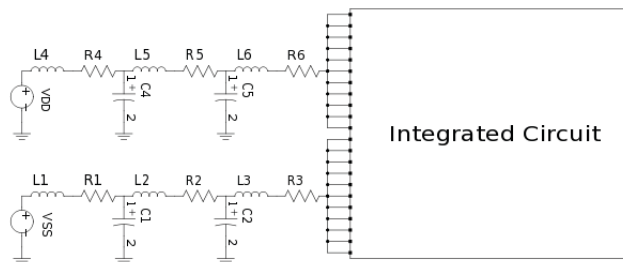
# 11.1 Power Node Parasitics

Parasitic elements (R, L, C) are frequently required for circuit simulations to capture important circuit behavior. Most parasitic elements (interconnect, etc.) can be added to netlists without causing any difficulties for the **Xyce** solvers. Small circuits in particular are very robust to the addition of parasitic elements. Larger circuits, however, that must be simulated in parallel will in general tend to have more solver difficulties with the addition of parasitic devices. Of particular note are parasitic elements attached to the power and/or ground nodes of large digital circuits. An example of this is shown in figure 11.1. As these nodes tend to be highly connected, they can potentially have very high impact on solver difficulties.

One of the parallel algorithms used by **Xyce** is called *singleton removal* [16], which is applied at the linear solver level and is crucial for getting many large circuits to run in parallel. This algorithm takes advantage of the fact that, in circuit simulation, some solution values are available explicitly, rather than being a quantity that needs to be calculated as the solution to a particular equation. In circuit simulation, such quantities are usually the values of independent sources. For instance, the presence of an independent voltage source at a particular node in a circuit fixes the voltage at that node to be the value of the independent source; therefore, equations reflecting the value of the voltage at that particular node do not have to be added to the set of linear equations used (in part) to determine the voltages at all the nodes in the circuit. The technique of fixing such node voltages without including them in the rest of the linear solve can be handled in a preprocessing phase referred to as the singleton removal phase.

When simulating in parallel, singleton removal is crucial as some voltage sources (especially power supplies in digital circuits) are connected to hundreds or thousands of circuit nodes. This presents a big problem in parallel because having numerous connections can often mean a communication bottleneck during the linear solve. Using singleton removal eliminates that bottleneck.

While singleton removal can result in a great improvement for circuits with ideal power supplies, for circuits with nonideal power supplies, the communication bottleneck remains. Once parasitic elements are placed between the power supply and the rest of the circuit, it is only the voltage at the circuit node directly connected to the independent source that can be removed via singleton removal. Other nodes connected to this independent source through parasitic elements have



**Figure 11.1.** Power node parasitics example. NOTE: An RLC network sits between the VDD, VSS sources and the main circuit, so these highly connected nodes cannot be removed with a singleton filter.

voltages that must now be solved for directly.

## 11.2 Two Level Algorithms Overview

Fortunately, **Xyce** [12] provides a workaround that allows power node parasitics to be included in large circuits without breaking singleton removal. The workaround requires the use of a two-level Newton solve, in which the problem is divided into two very separate pieces, each for the most part treated as an entirely separate circuit with minimal coupling terms linking the pieces together.

For power-node problems, two-level users will typically split the netlist into "top" and "inner" netlists. The top netlist contains the power node parasitics and the ideal voltage sources, and very little else. The inner circuit should contain the rest of the circuit. **Xyce** couples the two circuits through an "EXT" (external) device in the top circuit, and two or more independent voltage sources on the inner circuit. The values on the inner voltages are imposed from the top circuit, and the currents and conductances of the EXT device come from the inner circuit.

**Xyce** will construct a different linear system for each circuit. As such, the inner circuit will appear to have independent sources, allowing the singleton removal algorithm to work.

Since at least the 1980s, literature has included the two-level Newton algorithm, although mostly as it applied to circuit-device simulation. [20] and [21] provide a mathematical description, while [12] provides more information about the **Xyce** implementation.

## 11.3 Examples

### 11.3.1 Explanation and Guidance

Figures 11.2 and 11.3 provide an example of a circuit that uses the two level algorithm. The top circuit (compTop.cir) (figure 11.2) invokes the inner circuit (complInner.cir) with the extern device, y1. To run this circuit, the user will only specify the top circuit on the command line:

```
Xyce compTop.cir <return>
```

The extern device (YEXT y1 sits between the contents of compTop.cir and complInner.cir and is connected to two nodes in the top-level circuit, DD1 and SS1. From the perspective of compTop.cir, the YEXT y1 device looks like a nonlinear two-terminal resistor, which is the equivalent of the entire inner circuit.

In the inner circuit, **Xyce** applies nodes DD1 and SS1 through the independent sources Vconnect0000 and Vconnect0001. By convention, the inner circuit must contain an independent voltage source for each node to which the EXT device is connected. The default naming convention requires that these sources be named vconnectxxxx, with xxxx being a four-digit integer starting at 0000.

NOTE: The .tran statement on the inner circuit must match the .tran statement on the top circuit. The same is true for .DC analysis. Also, as both circuit files have their own .print statements,

```

THIS CIRCUIT IS THE TOP PART OF A TWO LEVEL EXAMPLE.
* compTop.cir - BSIM3 Transient Analysis

YEXT y1 DD1 SS1 externcode=xyce netlist=compInner.cir
Vdd DDorig 0 5.0
Vss SSorig 0 0.0

.options linsol type=klu
.options timeint abstol=1.0e-6 reltol=1.0e-3

* PARASITICS
l_Lwirevdd    DDorig Ny    .50n
l_Lwirevss    SSorig Nx    .50n
R_Rbw        Ny    DD1    50m
R_Rwi        Nx    SS1    50m

.tran 0.01ns 60ns
.print tran v(DD1) v(SS1) i(Vdd)

.END

```

**Figure 11.2.** Two-level top netlist example.

both will produce \*.prn output files.

The coupling between the top and inner layers requires extra linear solves, so when using this algorithm the code will run more slowly. In general, one can expect a factor-of-two slowdown, for circuits that can be run either as conventional or two-level simulations. So, in practice this algorithm should only be applied when it is really needed (i.e., when conventional simulations fail).

Finally, when using this method, one must take particular care with file names. In practice, a **Xyce** user may frequently change netlist file names to reflect new details about the run. When this happens, the name of the netlist invoked on the YEXT y1 line must be changed. Failure to do so may result in using the wrong file for the inner simulation.

## 11.4 Restart

Restart works with the two-level algorithm. However, as the two-level algorithm involves two separate netlist input files, a two-level restart requires a separate restart file for each phase of the problem. So, the two files (e.g., compTop.cir and compInner.cir) require .options restart statements, and the statements in the two files must be consistent with each other.

Currently, the user must enforce this because the code does *not* make any attempt to check consistency between the top and inner file ".options restart" statements.

THIS CIRCUIT IS THE INNER PART OF A TWO LEVEL EXAMPLE.

```
* compInner.cir - BSIM3 Transient Analysis
M1 Anot    A      DD1 DD1  PMOS w=3.6u l=1.2u
M2 Anot    A      SS1 SS1  NMOS w=1.8u l=1.2u
M3 Bnot    B      DD1 DD1  PMOS w=3.6u l=1.2u
M4 Bnot    B      SS1 SS1  NMOS w=1.8u l=1.2u
M5 AorBnot SS1    DD1 DD1  PMOS w=1.8u l=3.6u
M6 AorBnot B      1     SS1  NMOS w=1.8u l=1.2u
M7 1       Anot   SS1 SS1  NMOS w=1.8u l=1.2u
M8 Lnot    SS1    DD1 DD1  PMOS w=1.8u l=3.6u
M9 Lnot    Bnot   2     SS1  NMOS w=1.8u l=1.2u
M10 2      A      SS1 SS1  NMOS w=1.8u l=1.2u
M11 Qnot   SS1    DD1 DD1  PMOS w=3.6u l=3.6u
M12 Qnot   AorBnot 3     SS1  NMOS w=1.8u l=1.2u
M13 3      Lnot   SS1 SS1  NMOS w=1.8u l=1.2u
MQL0 8     Qnot   DD1 DD1  PMOS w=3.6u l=1.2u
MQL1 8     Qnot   SS1 SS1  NMOS w=1.8u l=1.2u
MLT0 9     Lnot   DD1 DD1  PMOS w=3.6u l=1.2u
MLT1 9     Lnot   SS1 SS1  NMOS w=1.8u l=1.2u
CQ Qnot 0 30f
CL Lnot 0 10f

Vconnect0000 DD1 0 0
Vconnect0001 SS1 0 0

Va A 0 pulse(0 5 10ns .1ns .1ns 15ns 30ns)
Vb B 0 0

.model nmos nmos (level=9)
.model pmos pmos (level=9)
.options linsol type=klu
.options timeint abstol=1.0e-6 reltol=1.0e-3
.tran 0.01ns 60ns
.print tran v(a) v(b) 1.0+v(9) 1.0+v(8)

.END
```

**Figure 11.3.** Two-level inner netlist example.



# 12. Specifying Initial Conditions

## Chapter Overview

This chapter includes the following sections:

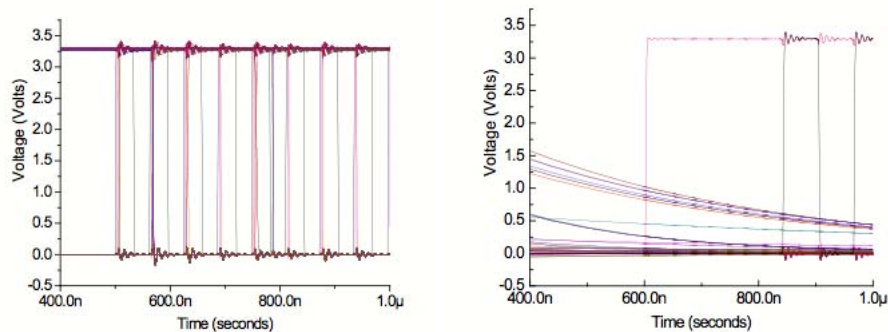
- Section 12.1, *Initial Conditions Overview*
- Section 12.2, *Device Level IC= Specification*
- Section 12.3, *.IC and .DCVOLT Initial Condition Statements*
- Section 12.4, *.SAVE Statements*
- Section 12.5, *DCOP Restart*
- Section 12.6, *UIC and NOOP*

## 12.1 Initial Conditions Overview

**Xyce** provides several different options for users to set an initial condition. Reasons for setting initial conditions include, but are not limited to:

- Improving the robustness of the DCOP solution
- Optimizing performance by reusing DCOP solution of a previous run to start new transient runs
- Setting an initial state for a digital circuit
- Initiating an oscillator circuit.

As noted, setting initial conditions can be particularly useful for multistate digital circuits. Figure 12.1 provides an example result demonstrating how initial conditions can be used to set the state of a digital circuit. In this case, obtaining the state purely through transient simulation can be time-consuming and often is not practical..



**Figure 12.1.** Example result with (left) and without (right) IC= preset. NOTE: The preset example starts in the initial state directly out of the DCOP calculation, while the nonpreset example requires a long transient to equilibrate.

## 12.2 Device Level IC= Specification

Many devices in **Xyce** support setting initial junction voltage conditions on the device instance line with the IC= keyword. This is frequently used to set the state of digital circuits. Figure 12.2 presents a simple inverter example demonstrating the use of IC= on a BSIMSOI device.

While many circuit simulators have a similar IC= capability, **Xyce** implementation differs in some important respects. For any device with an IC= statement, **Xyce** enforces the junction drop in parallel with the device junction as a voltage source in parallel with the device. **Xyce** then applies the parallel voltage source through the DCOP calculation, and then removes it prior to the beginning of the transient. This strongly enforces the requested junction drop, meaning that if the DCOP converges, the requested voltage drop will in the solution. In many other circuit codes, **Xyce** applies IC= as a weaker constraint, with the intent of improving DCOP calculation robustness.

IC= can be applied to the following devices: BSIM3, BSIM4, BSIMSOI, Capacitor, and Inductor.

```
MOS LEVEL=10 INVERTER WITH IC=  
  
.subckt INV IN OUT VDD GND  
MN1 OUT IN GND GND GND NMOS w=4u l=0.15u IC=2,0  
MP1 OUT IN VDD GND VDD PMOS w=10u l=0.15u  
.ends  
  
.tran 20ns 30us  
.print tran v(vout) v(in)+1.0 v(1)  
  
VDDdev VDD 0 2V  
RIN IN 1 1K  
VIN1 1 0 2V PULSE (2V 0V 1.5us 5ns 5ns 1.5us 3.01us)  
R1 VOUT 0 10K  
C2 VOUT 0 0.1p  
XINV1 IN VOUT VDD 0 INV  
.MODEL NMOS NMOS ( LEVEL = 10 )  
.MODEL PMOS PMOS ( LEVEL = 10 )  
  
.END
```

**Figure 12.2.** Example netlist with device-level IC=.

## 12.3 .IC and .DCVOLT Initial Condition Statements

.IC and .DCVOLT are equivalent methods for specifying initial conditions. How **Xyce** applies them, however, depends on whether the UIC parameter is present on the .TRAN line. If UIC is not specified, then **Xyce** applies the conditions specified by a .IC and .DCVOLT statements throughout the DCOP phase, ensuring the specified values will be the solved values at the end of the DCOP calculation. **Xyce** allows unspecified variables to find their computed values, consistent with the imposed voltages.

```
RC circuit
.ic v(1)=1.0
c1 1 0 1uF
R1 1 2 1K
v1 2 0 0V
.print tran v(1)
.tran 0 5ms
.options timeint reltol=1e-6 abstol=1e-6
.end
```

**Figure 12.3.** Example netlist with .IC. NOTE: Without the .IC statement, the capacitor is not given an initial charge, and the transient signals are flat. With the .IC statement, it has an initial charge, which then decays in transient. Without the .IC statement, the capacitor is not given an initial charge, and the signals in transient are all flat. With the .IC statement, it has an initial charge which then decays in transient.

If UIC is specified on the .TRAN line, then **Xyce** skips the DCOP calculation altogether, and uses the values specified on .IC and .DCVOLT lines as the initial values for the transient calculation. Unspecified values are set to zero.

For the UIC and non-UIC cases, **Xyce** ignores specified values that do not correspond to existing circuit variables. Also, the .IC capability can only set voltage values, not current values.

### 12.3.1 Syntax

```
.IC V(node1) = val1 <V(node2) = val2> ...
.DCVOLT V(node1) = val1 <V(node2) = val2> ...
```

where: *val1*, *val2*, ... specify nodal voltages and *node1*, *node2*, ... specify node numbers.

## 12.3.2 Example

```
.IC V(1) = 2.0 V(A) = 4.5  
.DCVOLT 1 2.0 A 4.5
```

Fig. 12.3 provides a more complete example (showing a full netlist).

## 12.4 .SAVE Statements

**Xyce** stores operating point information using `.SAVE` statements, and then reuses it to start subsequent transient simulations. Using `.SAVE` results in solution data being stored in a text file, comprised of `.NODESET` or `.IC` statements. This file can be applied to other simulations using `.INCLUDE`.

The form of `.SAVE` is as follows:

```
.SAVE <TYPE=type_keyword> <FILE=save_file> <LEVEL=level_keyword> <TIME=save_time>
```

where:

`type_keyword` can be set to “NODESET” or “IC”. By default, it will be “IC”.

`save_file` is the user-specified output file name for the \*.ic file. If this is not specified, **Xyce** uses *netlist.cir.ic*.

`level_keyword` is an Hspice compatibility parameter. **Xyce** supports “ALL” and “NONE.”

`save_time` is an Hspice compatibility parameter. Currently unsupported, **Xyce** outputs the \*.ic file at `time=0.0`.

## 12.5 DCOP Restart

DCOP restart is a capability similar to `.NODESET` and `.SAVE` used in combination. Similar to `.NODESET`, starting a simulation with DCOP restart will result in **Xyce** performing two nonlinear solves. The first solve strictly enforces the previous answer, and the second solve allows all the values to float and obtain their unconstrained solution. The second solve relies on the results of the first solve as an initial guess.

If the `UIC` keyword appears on the `.TRAN` line, **Xyce** applies the contents of the DCOP restart file as the initial condition and skips the DCOP calculation altogether. This is, the same as for `.IC` and `.NODESET`.

While `.NODESET` and DCOP restart are similar, there are a few differences. The biggest difference is the handling of voltage source voltages and currents. DCOP restart will attempt to restart from all the variables of the simulation, including voltage source variables. `.NODESET`, on the other hand, will ignore specified variables associated with voltage sources, and explicitly does not allow currents to be set. In general, voltage sources are constraints in and of themselves, so reconstraining them can cause singular matrices. To avoid this issue, DCOP restart makes changes to the linear system to prevent matrices from being singular.

### 12.5.1 Saving a DCOP restart file

To create a DCOP restart file, add a `.DCOP output=filename` line to the netlist:

```
.dcop output=saved.op
```

This will result in **Xyce** producing the file “saved.op” immediately after the operating point calculation. The produced file is similar to a `*.ic` file that can be produced by `.SAVE`, but with different format. Both file types are two-column text files. One column has the variable name, the other column the value of that variable.

### 12.5.2 Loading a DCOP restart file

To use a DCOP restart file, add a `.DCOP input=filename` line to the netlist:

```
.dcop input=saved.op
```

If the specified file does not exist in the local directory, **Xyce** will simply ignore the `.DCOP` statement and run normally.

## 12.6 UIC and NOOP

As noted earlier, the UIC key word on the TRAN line will disable the DCOP calculation, and result in **Xyce** immediately going to transient. If the user specifies .IC, .NODESET, or .DCOP input, then the transient calculation will use the specified initial values as the initial starting point. The NOOP keyword works exactly the same way as UIC.

```
pierce oscillator
c1 1 0 100e-12
c2 3 0 100e-12
c3 2 3 99.5e-15
c4 1 3 25e-12
l1 2 4 2.55e-3
r1 1 3 1e5
r2 3 5 2.2e3
r3 1 4 6.4
v1 5 0 12
Q1 3 1 0 NBJT
.MODEL NBJT NPN (BF=100)
.print tran v(2) v(3)

.tran 1ns 1us UIC
.ic v(2)=-10000.0 v(5)=12.0
```

**Figure 12.4.** Example netlist with UIC.

NOTE: This circuit is a pierce oscillator, which only oscillates if the operating point is skipped. If the .IC statement is not included, the oscillator will take a long time to achieve its steady-state amplitude. By including the .IC statement, the amplitude of node 2 is preset to a value close to its final steady-state amplitude. The transient in this example only runs for 10 cycles as a demonstration. In general, the time scales for this oscillator are much longer and require millions of cycles.

### 12.6.1 Example

```
.tran 1ns 1us UIC
.tran 1ns 1us NOOP
```

Some circuits, particularly oscillator circuits, will only function properly if the operating point is skipped, as they need an inconsistent initial state to oscillate. Figure 12.4 presents a Pierce oscillator example.



# 13. Working with .PREPROCESS Commands

## Chapter Overview

This chapter includes the following sections:

- Section 13.1, *Introduction*
- Section 13.2, *Ground Synonym Replacement*
- Section 13.3, *Removal of Unused Components*
- Section 13.4, *Adding Resistors to Dangling Nodes*

## 13.1 Introduction

In an effort to make **Xyce** more compatible with other commercial circuit simulators (e.g., HSPICE), some optional tools have been added to increase the netlist processing capabilities of **Xyce**. These options, which occur toward the beginning of a simulation, have been incorporated not only to make **Xyce** more compatible with different (i.e. non-**Xyce**) netlist syntax, but also to help detect and remove certain singular netlist configurations that can often cause a **Xyce** simulation to fail. Because all of the commands described in this section occur as a precursory step to setting up a **Xyce** simulation, they are all invoked in a netlist file via the keyword `.PREPROCESS`. This chapter describes each of the different functionalities that can be invoked via a `.PREPROCESS` statement in detail and provides examples to illustrate its use.

## 13.2 Ground Synonym Replacement

In certain versions of SPICE, keywords such as `GROUND`, `GND`, and `GND!` can be used as node names in a netlist file to represent the ground node of a circuit. **Xyce**, however, only recognizes node 0 as an official name for ground. Hence, if any of the prior node names is encountered in a netlist file, **Xyce** will treat these as different nodes from ground. To illustrate this point, consider the netlist of figure 13.1. When the node `Gnd` is encountered in the definition of resistor `R3`, **Xyce** instantiates this as a new node. The schematic diagram corresponding to this netlist (figure reffig:gndreplace2) shows that the resistor `R3` is “floating” between node 2 and a node with only a single device connection, node `Gnd`. When **Xyce** executes the netlist of figure 13.1, the voltage `V(2)` will evaluate to 0.5V.

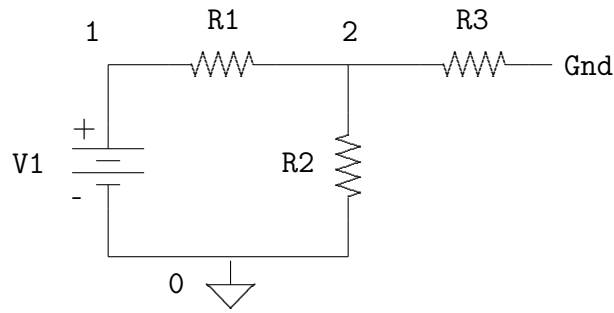
```
Circuit with "floating" resistor R3

V1 1 0 1
R1 1 2 1
R2 2 0 1
R3 2 Gnd 1

.DC V1 1 1 0.1
.PRINT DC V(2)
.END
```

**Figure 13.1.** Example netlist where `Gnd` is treated as being *different* from node 0.

If one would rather treat `Gnd` the same as node 0 in the above example, use the figure 13.3 netlist instead. When the statement `.PREPROCESS REPLACEGROUND TRUE` is present in a netlist, **Xyce** will treat any nodes named `GND`, `GND!`, `GROUND`, or any capital/lowercase variant of these keywords (e.g., `gROunD`) as synonyms for node 0. Hence, according to **Xyce**, the figure 13.3 netlist corresponds to figure 13.4 schematic diagram, and the voltage `V(2)` will evaluate to 0.33V.



**Figure 13.2.** Circuit diagram corresponding to the netlist of figure 13.1 where node Gnd is treated as being *different* from node 0.

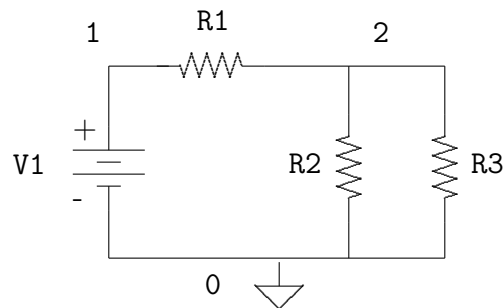
Circuit where resistor R3 does *\*not\** float

```
V1 1 0 1
R1 1 2 1
R2 2 0 1
R3 2 Gnd 1

.PREPROCESS REPLACEGROUND TRUE

.DC V1 1 1 0.1
.PRINT DC V(2)
.END
```

**Figure 13.3.** Example netlist where Gnd is treated as a synonym for node 0.



**Figure 13.4.** Circuit diagram corresponding to figure 13.3 where node Gnd is treated as a synonym for node 0.

NOTE: Only one `.PREPROCESS REPLACEGROUND` statement is allowed per netlist file (this is to prevent the user from setting `REPLACEGROUND` to `TRUE` on one line and then to `FALSE` on another). There is no way to differentiate between different keywords (i.e., it is not possible to treat `GROUND` as a synonym for node 0 while allowing `GND` to represent an independent node). If `REPLACEGROUND` is set to `TRUE`, **Xyce** will treat *both* of these keywords as node 0 if present in a netlist file.

## 13.3 Removal of Unused Components

Consider a slight variant of the circuit in figure 13.3 with the netlist given in figure 13.5. Here, the resistor `R3` is connected in a peculiar configuration: both terminals of the resistor are tied to the same circuit node, as is illustrated in figure 13.6. Clearly, the presence of this resistor has no effect on the other voltages and currents in the circuit since, by the very nature of its configuration, it has no voltage across it and, hence, does not draw any current. Therefore, in some sense, the component can be considered as “unused.” The presence of a resistor such as `R3` is rarely or never introduced by design, rather the presence of such components is the result of either human or automated error.

```
Circuit with an unused resistor R3

V1 1 0 1
R1 1 2 1
R2 2 0 1
R3 2 2 1

.DC V1 1 1 0.1
.PRINT DC V(2)
.END
```

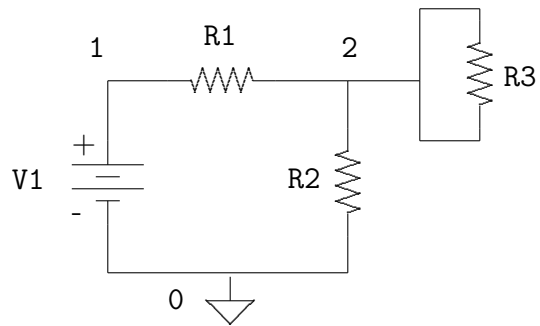
**Figure 13.5.** Netlist with a resistor `R3` whose device terminals are both the same node (node 2).

While the presence of the resistor `R3` in figure 13.3 does not change the behavior of the circuit, it adds an additional component to the netlist **Xyce** must include when solving for the voltages and currents in the circuit. If the number of such components in a given netlist is large, it is potentially desirable to remove them from the netlist to ease the burden on **Xyce**'s solver engines. This, in turn, can help to avoid possible convergence issues. For example, even though the netlist in figure 13.5 will run properly in **Xyce**, the netlist of figure 13.7 will abort. The voltage source `V2` attempts to place a 1V difference between its two device terminals; however, as both nodes of the voltage source are the same, the voltage source is effectively shorted.

**Xyce** includes the following command to prevent similar situations:

```
.PREPROCESS REMOVEUNUSED <component list>
```

where `<component list>` is a list of device types separated by commas. For each device type



**Figure 13.6.** Circuit of figure 13.5 containing a resistor R3 whose terminals are tied to the same node (node 2).

Circuit with improperly connected voltage source V2

V1 1 0 1

R1 1 2 1

R2 2 0 1

V2 2 2 1

.DC V1 1 1 0.1

.PRINT DC V(2)

.END

**Figure 13.7.** Circuit with an improperly connected voltage source V2.

specified in the list, **Xyce** checks for instances of that device type for which all of the device terminals are connected to the same node. If such a device is found, **Xyce** removes that device from the netlist. For instance, if executing the netlist of figure 13.8, **Xyce** will seek out such devices and remove them from the netlist. This causes the resistor R3 to be removed from the netlist. Figure 13.9 presents the schematic of the resulting **Xyce**-simulated circuit. NOTE: The presence of “C” in the REMOVEUNUSED statement does not cause **Xyce** to abort even though there are no capacitors in the netlist. Also, as in the case of a REPLACEGROUND statement, only one .PREPROCESS REMOVEUNUSED line may be present per netlist, or **Xyce** will abort.

Table 13.1 lists devices that can be removed via a REMOVEUNUSED statement. In the case of MOSFETs and BJTs, three device terminals must be the same (the gate, source, and drain in the case of a MOSFET; the base, collector, and emitter in the case of a BJT) to remove either device from the netlist.

```

Circuit with improperly connected voltage source V2

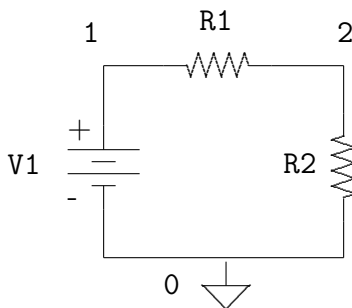
V1 1 0 1
R1 1 2 1
R2 2 0 1
R3 2 2 1

.PREPROCESS REMOVEUNUSED R,C

.DC V1 1 1 0.1
.PRINT DC V(2)
.END

```

**Figure 13.8.** Circuit with an “unused” resistor R3 removed from the netlist.



**Figure 13.9.** Circuit of figure 13.8 where resistor R3 has been removed via the .PREPROCESS REMOVEUNUSED statement.

Table 13.1: List of keywords and device types which can be used in a `.PREPROCESS REMOVEUNUSED` statement.

Keyword	Device Type
C	Capacitor
D	Diode
I	Independent Current Source
L	Inductor
M	MOSFET
Q	BJT
R	Resistor
V	Independent Voltage Source

## 13.4 Adding Resistors to Dangling Nodes

Consider the netlist of figure 13.10 and the corresponding schematic of figure 13.11. Nodes 3 and 4 of the netlist are what we will henceforth refer to as *dangling nodes*. We say that node 4 dangles because it is only connected to the terminal of a single device, while we say that node 3 dangles because it has no DC path to ground. The first of these situations—connection to a single device terminal only—can arise, for example, in a netlist which contains nodes representing output pins that are not connected to a load device. For instance, the resistance R2 in figure 13.10 could represent the resistance of an output pin of a package that is meant to drive resistive loads. Hence, an actual physical implementation of the circuit of figure 13.11 would normally include a resistor between node 4 and ground, but, in creating the netlist, the presence of such an output load has been (either intentionally or unintentionally) left out.

```

Circuit with two dangling nodes, nodes 3 and 4

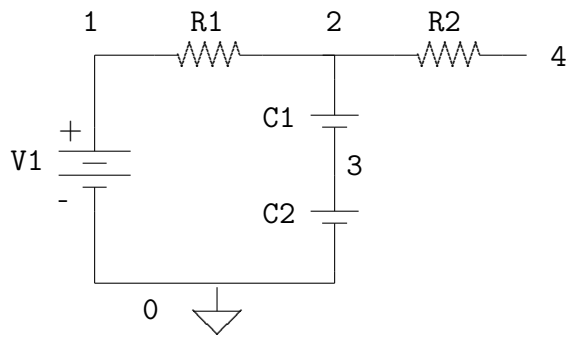
V1 1 0 1
R1 1 2 1
C1 2 3 1
C2 3 0 1
R2 2 4 1

.DC V1 0 1 0.1
.PRINT DC V(2)
.END

```

**Figure 13.10.** Netlist of circuit with two dangling nodes, nodes 3 and 4.

The second situation—where a node has no DC path to ground—is sometimes an effect that is purposely incorporated into a design (e.g., the design of switched capacitor integrators (e.g., see [22], chapter 10), but oftentimes it is also the result of some form of error in the process of creating the netlist. For instance, when graphical user interfaces (GUIs) are used to create circuit schematics that are then translated into netlists via software, one very common unintentional error



**Figure 13.11.** Schematic of netlist in figure 13.10.

is to fail to connect two nodes that are intended to be connected. To illustrate this point, consider the schematic of figure 13.12. The schematic seems to indicate that the lower terminal of resistor R2 should be connected to node 3. This is not the case as there is a small gap between node 3 and the line intended to connect node 3 to the resistor. Such an error can often go unnoticed when creating a schematic of the netlist in a GUI. Thus, when the schematic is translated into a netlist file, the resulting netlist would *not* connect the resistor to node 3 and would instead create a new node at the bottom of the resistor, resulting in the circuit depicted in figure 13.11.

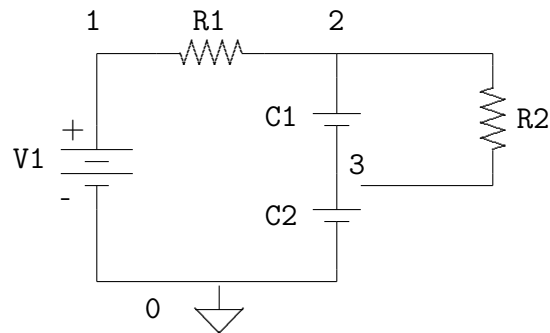
While neither of the previous situations is necessarily threatening (**Xyce** will run the figure 13.10 netlist successfully to completion), there are times when it is desirable to somehow make a dangling node *not* dangle. For instance, returning to the example in which the resistor R2 represents the resistance of an output pin, one may want to simulate the circuit when a 1K load is attached between node 4 and ground in figure 13.11. In the case where a node has no DC path to ground, the situation is slightly more dangerous if, for instance, the node in question is also connected to a high-gain device such as the gate of a MOSFET. As the DC gate bias has a great impact on the DC current traveling through the drain and source of the transistor, not having a well-defined DC gate voltage can greatly degrade the simulated performance of the circuit.

In both prior examples, the only true way to “fix” each of these issues is to find all dangling nodes in a particular netlist file and augment the netlist at/near these nodes to obtain the desired behavior. If, however, the number of components in a circuit is very large (say on the order of hundreds of thousands of components), manually augmenting the netlist file for each dangling node becomes a practical impossibility if the number of such nodes is large.

Hence, it is desirable for **Xyce** to be capable of automatically augmenting netlist files so as to help remove dangling nodes from a given netlist. The command `.PREPROCESS ADDRISISTORS` is designed to do just this. Assuming the netlist of figure 13.13 is stored in the file `filename`, the `.PREPROCESS ADDRISISTORS` statements will cause **Xyce** to create a new netlist file called `filename_xyce.cir` (depicted in figure 13.14). The line `.PREPROCESS ADDRISISTORS NODCPATH 1G` instructs **Xyce** to create a copy of the netlist file containing a set of resistors of value 1G that are connected between ground and nodes which currently have no DC path to ground. Similarly, the line `.PREPROCESS ADDRISISTORS ONETERMINAL 1M` instructs **Xyce** to add to the same netlist file a set of resistors of value 1M that are connected between ground and devices that are connected to only one terminal. The resistor `RNODCPATH1` in figure 13.14 achieves the first of these goals



while `RONETERM1` achieves the second. Figure 13.15 shows a schematic of the resulting circuit represented by the netlist in figure 13.14.



**Figure 13.12.** Schematic of a circuit with an incomplete connection between the resistor R2 and node 3.

```
Circuit with two dangling nodes, nodes 3 and 4

V1 1 0 1
R1 1 2 1
C1 2 3 1
C2 3 0 1
R2 2 4 1

.PREPROCESS ADDRESISTORS NODCPATH 1G
.PREPROCESS ADDRESISTORS ONETERMINAL 1M

.DC V1 0 1 0.1
.PRINT DC V(2)
.END
```

**Figure 13.13.** Netlist of circuit with two dangling nodes, nodes 3 and 4, with `.PREPROCESS ADDRESISTORS` statements.

Some general comments regarding the use of `.PREPROCESS ADDRESISTOR` statements include:

- **Xyce** does not terminate immediately after the netlist file is created. In other words, if **Xyce** is run on the filename of figure 13.13 netlist, it will attempt to execute this netlist as given (i.e., it tries to simulate the circuit of figure 13.11) and generates the file `filename_xyce.cir` as a byproduct. It is important to point out that the resistors that are added at the bottom of the netlist file `filename_xyce.cir` do **not** get added to the original netlist when **Xyce** is running on the file `filename`. If one wishes to simulate **Xyce** with these resistors in place, one must run **Xyce** on `filename_xyce.cir` explicitly.
- The naming convention for resistors which connect to ground nodes which do not have a DC

```

XYCE-generated Netlist file copy:  TIME='07:32:31 AM'
* DATE='Dec 19, 2007'
*Original Netlist Title:

*Circuit with two dangling nodes, nodes 3 and 4.

V1 1 0 1
R1 1 2 1
C1 2 3 1
C2 3 0 1
R2 2 4 1

*.PREPROCESS ADDRESISTORS NODCPATH 1G
*Yyce: ".PREPROCESS ADDRESISTORS" statement
* automatically commented out in netlist copy.
*.PREPROCESS ADDRESISTORS ONETERMINAL 1M
*Yyce: ".PREPROCESS ADDRESISTORS" statement
* automatically commented out in netlist copy.

.DC V1 0 1 0.1
.PRINT DC V(2)

*XYCE-GENERATED OUTPUT:  Adding resistors between ground
* and nodes connected to only 1 device terminal:

RONETERM1 4 0 1M

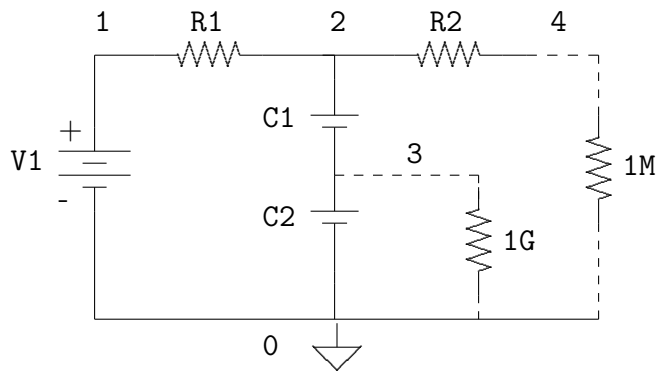
*XYCE-GENERATED OUTPUT:  Adding resistors between ground
* and nodes with no DC path to ground:

RNODCPATH1 3 0 1G

.END

```

**Figure 13.14.** Output file filename\_xyce.cir which results from the .PREPROCESS ADDRESISTOR statements for the netlist of figure 13.12 (with assumed file name filename).



**Figure 13.15.** Schematic corresponding to the **Xyce**-generated netlist of figure 13.14.

path to ground is `RNODCPATH<i>`, where *i* is an integer greater than 0; the naming convention is similar for nodes which are connected to only one device terminal (i.e., of the form `RONETERM<i>`). **Xyce** will not change this naming convention if a resistor with one of the above names already exists in the netlist.

Hence, if a resistor named `RNODCPATH1` exists in netlist file `filename`, and **Xyce** detects there is a node in this netlist file that has no DC path to ground, **Xyce** will add *another* resistor with name `RNODCPATH1` to the netlist file `filename_xyce.cir` (assuming that either `.PREPROCESS ADDRESSISTORS NODCPATH` or `.PREPROCESS ADDRESSISTORS ONETERMINAL` are present in `filename`). If **Xyce** is subsequently run on `filename_xyce.cir`, it will exit in error due to the presence of two resistors with the same name.

- Commands `.PREPROCESS ADDRESSISTORS NODCPATH` and `.PREPROCESS ADDRESSISTORS ONETERMINAL` do **not** have to be simultaneously present in a netlist file. The presence of either command will generate a file `filename_xyce.cir`, and the presence of both will not generate two separate files. As with other `.PREPROCESS` commands, however, a netlist file is allowed to contain only one `NODCPATH` and one `ONETERMINAL` command each. If multiple `NODCPATH` and/or `ONETERMINAL` lines are found in a single netlist file, **Xyce** will exit in error.
- It is possible that a single node can have no DC path to ground *and* be connected to only one device terminal. If a `NODCPATH` and `ONETERMINAL` command are present in a given netlist file, **only** the resistor corresponding to the `ONETERMINAL` command is added to the netlist file `filename_xyce.cir` and the resistor corresponding to the `NODCPATH` command is omitted. If a `NODCPATH` command is present but a `ONETERMINAL` command is not, then **Xyce** will add a resistor corresponding to the `NODCPATH` command to the netlist, as usual.
- In generating the file `filename_xyce.cir`, the original `.PREPROCESS ADDRESSISTOR` statements are commented out with a warning message. This is to prevent **Xyce** from creating the file `filename_xyce.cir_xyce.cir` when the file `filename_xyce.cir` is run.

NOTE: This act is put in place simply to avoid generating redundant files. While `filename_xyce.cir_xyce.cir` would be slightly different from `filename_xyce.cir` (e.g., a different date and time stamp), both files would functionally implement the same netlist.

# 14. TCAD (PDE Device) Simulation with **Xyce**

## Chapter Overview

This chapter provides guidance for using the mesh-based device simulation capability of **Xyce**. It includes the following sections:

- Section 14.1, *Introduction*
- Section 14.2, *One-Dimensional Example*
- Section 14.3, *Two-Dimensional Example*
- Section 14.4, *Doping Profile*
- Section 14.5, *Electrodes*
- Section 14.6, *Meshing*
- Section 14.8, *Mobility Models*
- Section 14.9, *Bulk Materials*
- Section ??, *Solver Options*
- Section 14.10, *Output and Visualization*

# 14.1 Introduction

This chapter describes how to use the mesh-based device simulation functionality of **Xyce**, which is based on the solution a coupled set of partial differential equations (PDEs), discretized on a mesh. Such devices are often referred to as Technology Computer-Aided Design (TCAD) devices. While the rest of **Xyce** is intended to be similar to analog circuit simulators such as SPICE, the TCAD device capability is intended to be similar to commercial device simulators, such as PISCES [23] and DaVinci [24].

**Xyce** offers two different TCAD devices — a one-dimensional device and a two-dimensional device — and enables both to be invoked in the same way as a conventional lumped parameter circuit device. Generally, this capability is intended for very detailed simulation of semiconductor devices, such as diodes, bipolar transistors, and MOSFETs. As the **Xyce** TCAD devices can be invoked from the netlist, they can be embedded in a circuit as part of a mixed-mode simulation.

The **Xyce** TCAD devices should be considered to be a beta-level capability. The primary focus of **Xyce** has been traditional analog circuit simulation, so these devices have not received the same level of attention. This capability should be regarded as a prototype for Charon([25]), a high-performance TCAD simulator under development at Sandia.

## 14.1.1 Equations

Kramer [26] and Selberherr [27], among others, describe device simulation equations. The most common formulation and the one used in **Xyce**, is the drift-diffusion (DD) formulation, which consists of three coupled PDEs (a single Poisson equation for electrostatic potential and two continuity equations; one each for electrons and holes).

### Poisson equation

The electrostatic potential  $\phi$  satisfies Poisson's equation:

$$-\nabla \cdot (\epsilon \nabla \phi(x)) = \rho(x) \tag{14.1}$$

where  $\rho$  is the charge density and  $\epsilon$  is the permittivity of the material. For semiconductor devices, local carrier densities and local doping determine charge density;

$$\rho(x) = q(p(x) - n(x) + C(x)) \tag{14.2}$$

Here,  $p(x)$  is the spatially dependent concentration of holes;  $n(x)$ , the concentration of electrons; and  $q$ , the magnitude of the charge on an electron.  $C(x)$  is the total doping concentration, which can also be represented as  $C(x) = N_D^+(x) - N_A^-(x)$ , where  $N_D^+$  the concentration of positively ionized donors,  $N_A^-$  the concentration of negatively ionized acceptors.

## Species continuity equations

Continuity equations relate the convective derivative of the species concentrations to the creation and destruction of particles (“recombination/generation”).

$$\frac{\partial n(x)}{\partial t} + \nabla \cdot \Gamma_n = -R(x) \quad (14.3)$$

$$\frac{\partial p(x)}{\partial t} + \nabla \cdot \Gamma_p = -R(x) \quad (14.4)$$

Here  $n$  is the electron concentration and  $p$  is the hole concentration.  $R$  is the recombination rate for both species.  $\Gamma_n$  and  $\Gamma_p$  are particle fluxes for electrons and holes, respectively.  $R$  is the recombination rate for both species, and the right hand sides are equal since creation and destruction of carriers occurs in pairs. The quantities  $\Gamma_n$  and  $\Gamma_p$  are electron and hole fluxes, and are determined from the following expressions:

$$\Gamma_n = n(x)\mu_n E(x) + D_n \nabla n(x) \quad (14.5)$$

$$\Gamma_p = p(x)\mu_p E(x) + D_p \nabla p(x) \quad (14.6)$$

$\mu_n$ ,  $\mu_p$  are mobilities for electrons and holes, and  $D_n$ ,  $D_p$  are diffusion constants.  $E(x)$  is the electric field, which is given by the gradient of the potential, or  $-\partial\phi/\partial x$ .

### 14.1.2 Discretization

**Xyce** uses a box-integration discretization, with the Scharfetter-Gummel method to model the flux of charged species. For a more-detailed description of this method, refer to [26] [27] [28].

## 14.2 One Dimensional Example

The one-dimensional device was the first PDE-based device to be implemented in **Xyce**. The single dimension limits its usefulness, but its simplicity makes it a good device to use for a preliminary example. One dimensional devices are almost always two-terminal diodes, and this fact allows for assumptions that simplify the specification and shorten the parameter list of the device.

Figure 14.2 provides an example netlist for a simulation of a one-dimensional diode, while figure 14.2 shows its corresponding schematic. This regulator circuit is based on the principle that connecting one or more diodes in series with a resistor and a power supply will produce a relatively constant voltage. The input voltage (node 2) is a sinewave, with a frequency of 50 Hz and an amplitude of 1 V. The expected output (node 3) signal should be (mostly) flat.

### 14.2.1 Netlist Explanation

Currently, there are almost no model parameters for PDE devices. The model line serves only to set the level. The default level is 1, for a one-dimensional device. Setting `level=2` will invoke

```

PDE Diode Regulator Circuit
VP 1 0 PULSE(0 5 0.0 2.0e-2 0.0 1.0e+20 1.2e+20)
VF 2 1 SIN(0 1 50 2.0e-2)
VT1 4 0 0V
R1 2 3 1k

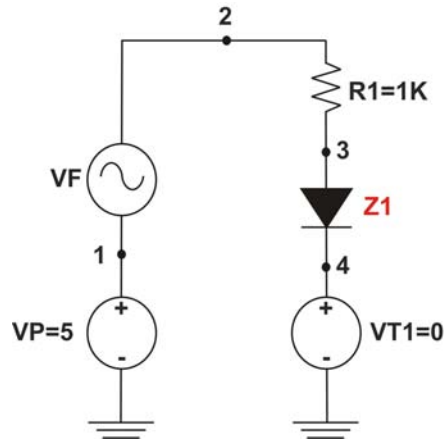
* TCAD/PDE Device
YPDE Z1 3 4 DIODE na=1.0e17 nd=1.0e17 graded=1
+ l=5.0e-4 nx=101
.MODEL DIODE ZOD

.TRAN 1.0e-3 12.0e-2
.print TRAN format=tecplot
+ v(1) v(2) v(3) v(4) I(VF) I(VT1)

.options NONLIN maxstep=100 maxsearchstep=3
+ searchmethod=2
.options TIMEINT reltol=1.0e-3 abstol=1.0e-6
.END

```

**Figure 14.1.** Voltage regulator circuit, using a one-dimensional TCAD diode. Figure 14.3 illustrates the result of this netlist. The PDE device instance line is in red, and the PDE device model line is in blue.



**Figure 14.2.** Voltage regulator schematic  
The diode, Z1, is the PDE device in this example.

two-dimensional devices. In this example, the level is not explicitly set, and so **Xyce** uses the default value (1).

The instance line is where most of the specific parameters are set for a TCAD device. In this example, the line appears as:

```
YPDE Z1 3 4 DIODE na=1.0e17 nd=1.0e17 graded=1 l=5.0e-4 nx=101
```

Doping parameters  $n_a$  and  $n_d$  represent the majority carrier doping levels on the N- and the P-sides of the junction, respectively.  $graded=1$  is also a doping parameter, and specifies that the junction is a graded junction, rather than an abrupt step-function junction.  $l=5.0e-4$  specifies the length of the device, in cm.  $nx=101$  specifies that there are 101 mesh points, including the two endpoints. For the one-dimensional device, the mesh is always uniform, so the size of each mesh cell,  $\Delta x$  will be:

$$\Delta x = \frac{l}{nx - 1} = \frac{5.0e-4 \text{ cm}}{100} = 5.0e-6 \text{ cm} \quad (14.7)$$

The mesh points  $i = 0 - 101$  will have the following locations,  $x_i$ :

$$\begin{aligned} x_i &= i\Delta x \\ x_0 &= 0.0 \text{ cm} \\ x_1 &= 5.0e-6 \text{ cm} \\ &\cdot \\ &\cdot \\ &\cdot \\ x_{101} &= 5.0e-4 \text{ cm} \end{aligned}$$



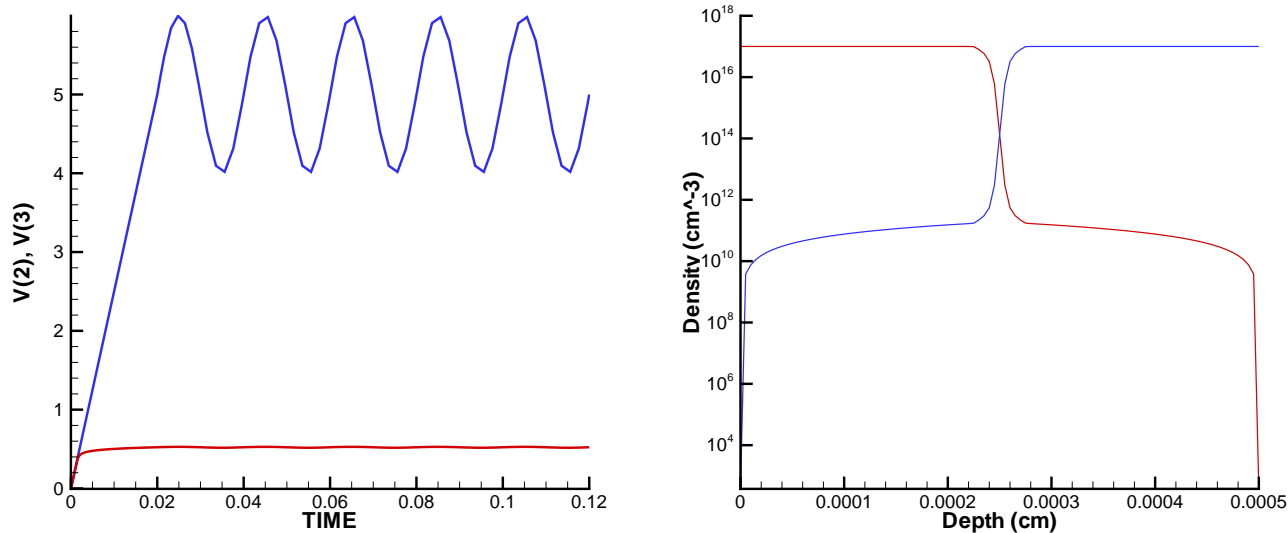
## 14.2.2 Boundary Conditions and Doping Profile

The cited netlist example relies mostly on default parameters; therefore, it specifies nothing about electrodes, or boundary conditions, and has a minimal doping specification. A one-dimensional device can have only two electrodes connected to the circuit. The electrodes are at opposite ends of the domain, one at the first mesh point ( $x=0.0$  cm,  $i=0$ ) and the other at the opposite end of the domain, at the last mesh point ( $x=5.0e-4$  cm,  $i=101$ ).

The electrode associated with the first mesh point ( $x=0.0$  cm) is connected to the *second* circuit node on the instance line, while the electrode associated with the last mesh point ( $x=1$ ) is connected to the *first* circuit node on the instance line. For the doping used in this example, the junction is in the exact center of the device ( $x=1/2$ ), and the n-side is the region defined by  $x < 1/2$ , and the p-side is the region defined by  $x > 1/2$ . This default doping, along with the electrode-circuit connectivity, result in the one-dimensional device to behave like a traditional SPICE-style diode. For a complete discussion of how to specify a doping profile see section 14.4.1. For a complete discussion of how to specify electrodes in detail (including boundary conditions), see section 14.5.

## 14.2.3 Results

Figure 14.3 shows the transient result of this circuit. The voltage drop across the diode ( $V(3)$ ) is nearly the same for a wide range of currents, and is nearly constant. The voltage drop across the series resistor,  $R1$ , is much more sensitive ( $V(2)-V(3)$ ), and so most of the voltage variation of the input sinewave is accounted for by  $R1$ .



**Figure 14.3.** Results for voltage regulator. In the left plot, the transient output is shown, in which the input voltage is blue and the output voltage is red. In the right plot, the initial carrier densities are shown, with the electron density in red and the hole density in blue.

## 14.3 Two-Dimensional Example

Figure 14.4 presents an example netlist for a simulation of a two-dimensional bipolar transistor. As before, the PDE device instance line is in red, while the PDE device model line is in blue. In this case, note that the model line specifies the level, which is set to 2. This is required for the two-dimensional device. This particular example is a DC sweep of a bipolar transistor device. Figure 14.5 presents a schematic illustrating this circuit.

```
Two-Dimensional Example
VPOS  1 0 DC 5V
VBB   6 0 DC -2V
RE    1 2 2K
RB    3 4 190K

  YPDE BJT 5 3 7 PDEBJT meshfile=internal.msh
+ node = {name = collector, base, emitter}
+ tecplotlevel=2 txtdatalevel=1
+ mobmodel=arora
+ l=2.0e-3 w=1.0e-3
+ nx=30    ny=15
.MODEL PDEBJT ZOD level=2

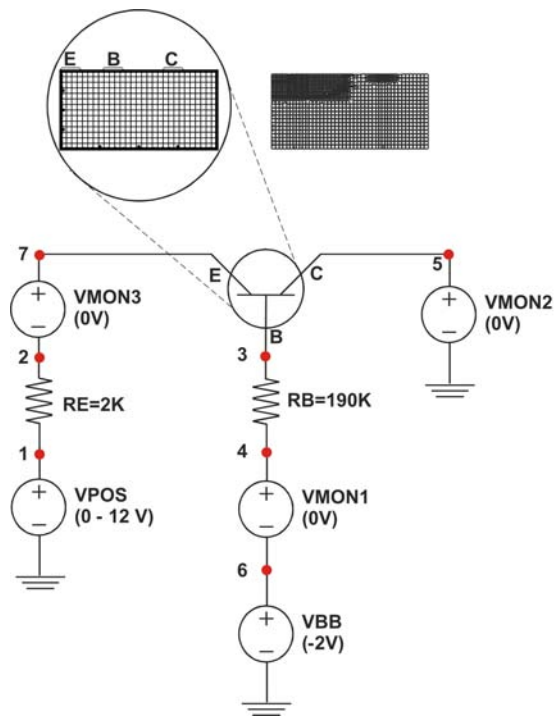
* Zero-volt sources acting as an ammeter to measure the
* base, collector, and emitter currents, respectively
VMON1 4 6 0
VMON2 5 0 0
VMON3 2 7 0

.DC VPOS 0.0 12.0 0.5 VBB -2.0 -2.0 1.0
.options NONLIN maxstep=70 maxsearchstep=1
+ searchmethod=2
.options TIMEINT reltol=1.0e-3 abstol=1.0e-6
+ firstdcopstep=0 lastdcopstep=1
.PRINT DC V(1) I(VMON1) I(VMON2) I(VMON3)
.END
```

**Figure 14.4.** Two-dimensional BJT netlist. Figures 14.6 and 14.7 provide some of the results of this netlist.

### 14.3.1 Netlist Explanation

The two-dimensional device can have 2 to 4 electrodes. In this example there are three; nodes 5, 3, and 7, corresponding to the three names on the “node” line, which appears as:



**Figure 14.5.** Two-dimensional BJT circuit schematic This schematic is for the circuit described by the netlist in figure 14.4. The mesh in the large circle is the mesh used in the example. The other mesh, which contains some mesh refinement, is included in the figure as an example of what is possible with an external mesh generator.

```
+ node = {name = collector, base, emitter}
```

This line specifies that node 5 is connected to an electrode named “collector,” node 3 is connected to an electrode named “base,” and node 7 is connected to an electrode named “emitter”. Although this example only contains the electrode names, the “node” specification can contain a lot of information. Section 14.5 provides a full explanation of the electrode parameters.

The next line contains parameters concerned with plotting the results, and appears as follows:

```
+ tecplotlevel=2 txtdatalevel=1
```

These are not related to the output specified by .PRINT, which outputs circuit data. The `tecplotlevel` command enables files to be output readable by Tecplot, which can then be used to create contour plots of quantities such as the electron density, electrostatic potential and the doping profile. Figures 14.6 and 14.7 contain examples of Tecplot-generated contour plots, which were generated from the results of this example.

The `txtdatalevel` command enables a text file with volume averaged information to be output to a file. Currently, **Xyce** will update both of these output files at each time step or DC sweep step.

The next line, `mobmodel=arora`, specifies which mobility model to use. Section 14.8 provides for more detail on available mobility models.

The last two lines, specify the mesh of the device, and are given by:

```
+ l=2.0e-3 w=1.0e-3  
+ nx=30 ny=15
```

These numbers are used in nearly the same way as the one-dimensional case used `l` and `nx` parameters. The mesh is Cartesian, and the spacing is uniform.

## 14.3.2 Doping Profile

As in the one-dimensional example, the two-dimensional example in figure 14.4 specifies nothing about the doping profile, and thus relies on default settings. In this case there are three specified electrodes, which by default results in the doping profile of the bipolar junction transistor (BJT). Section 14.4 provides a complete description of how to specify a doping profile in detail, and describes the various default impurity profiles.

## 14.3.3 Boundary Conditions and Electrode Configuration

As in the one- and two-dimensional examples in figure 14.4 specify nothing about the electrode configuration or the boundary conditions, and rely on default settings. To be consistent with the default three-terminal doping, the device has terminals that correspond to that of a BJT. All three electrodes (collector, base, emitter) are along the top of the device.

By default all electrodes are considered to be neutral contacts. The boundary conditions applied to the electron density, hole density, and electrostatic potential are all Dirichlet conditions.

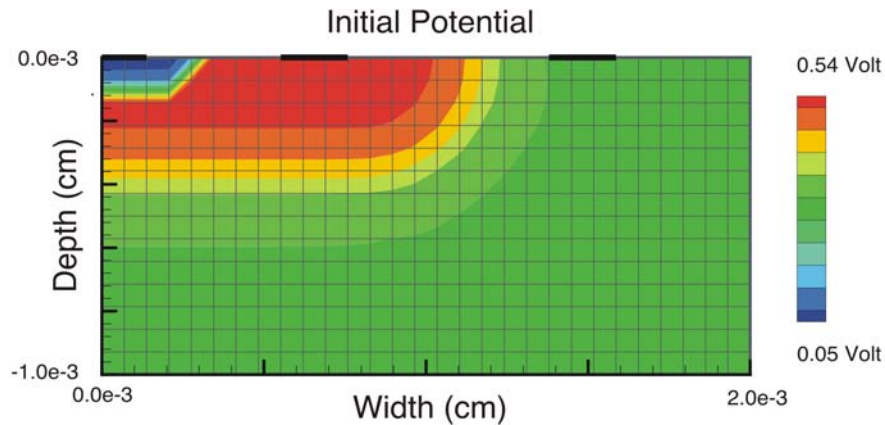
Section 14.5 discusses how to specify electrodes in detail (including boundary conditions).

## 14.3.4 Results

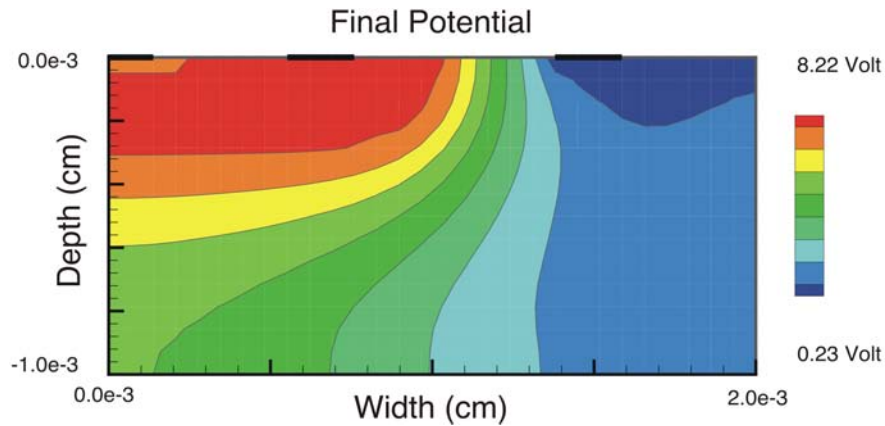
Figures 14.6, 14.7 and 14.8 provide results for the two-dimensional example. The first two figures are contour plots of the electrostatic potential. The first corresponds to the first DC sweep step, where `VPOS` is set to 0.0 Volts. The second corresponds to the final DC sweep step, in which `VPOS` has a value of 12.0 volts. The voltage source, `VPOS`, applies a voltage to the emitter load resistor, `RE`, so some of the 12.0V is dropped across `RE`, and the rest is applied to the BJT.

The third figure is an I-V curve of the dependence of the three terminal currents on applied emitter voltage. For the entire sweep,  $-2.0$  V has been applied to the base load resistor and, as this transistor is a PNP transistor, this results in the transistor being in an “on” state. The emitter-collector current varies nearly linearly with the applied emitter voltage. Also, as can be expected because of current conservation, the three currents sum to nearly zero.

Note that the mesh used to generate these results is visible in figure 14.6, and was generated using the internal “uniform mesh”. This mesh will not produce a very accurate result, as it does not resolve the depletion regions very well. Accuracy can, in theory, be improved using mesh refinement near the depletion regions. However, such meshes must be read in from an external mesh generator(currently unsupported).



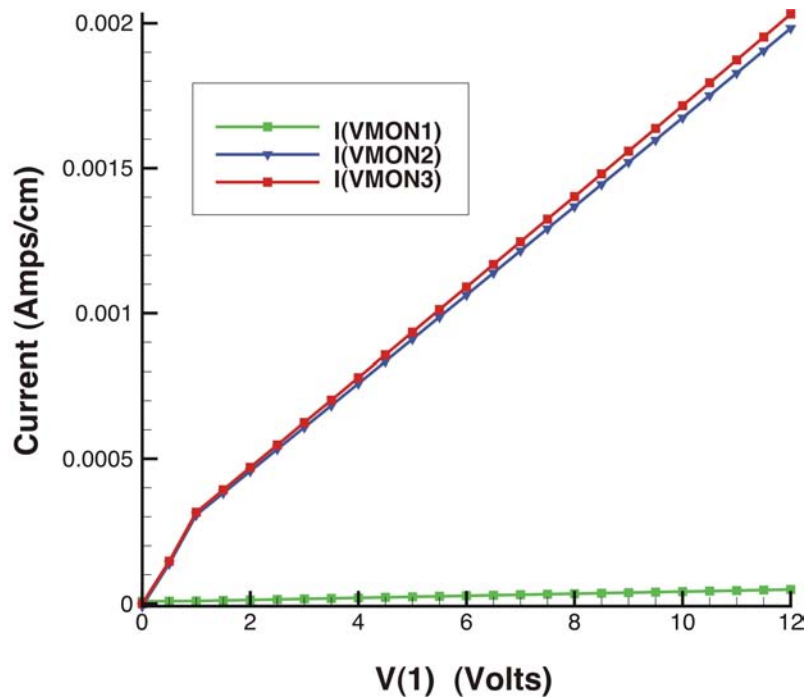
**Figure 14.6.** Initial two-dimensional BJT result  
A Tecplot-generated contour plot of the electrostatic potential at the first DC sweep step of the netlist in figure 14.4.



**Figure 14.7.** Final two-dimensional BJT result.  
A Tecplot-generated contour plot of the electrostatic potential at the last DC sweep step of the netlist in figure 14.4.

## 14.4 Doping Profile

**Xyce** used the defaults in the two examples as no doping parameters were specified. Default profiles are uniquely specified by the number of electrodes. In practice, especially for two-dimensional simulations, the user will generally need to specify the doping profile manually.



**Figure 14.8.** I-V two-dimensional BJT result for the netlist in figure 14.4. The three plotted currents are through the three BJT electrodes, and as expected they add (if corrected for sign) to zero. I(VMON1) is the base current, I(VMON2) the collector current, and I(VMON3) the emitter current. V(1) is the voltage applied to the emitter load resistor, RE.

### 14.4.1 Manually Specifying the Doping

Figure 14.9 shows a circuit netlist for a one-dimensional device with a detailed, manual specification of the doping profile. Figure 14.11 illustrates a similar, two-dimensional version of this problem. For this discussion, the one-dimensional example will be referred to, but information conveyed is equally applicable to the two-dimensional case.

In both examples, the parameters associated with doping are in red text. The doping is specified with one or more regions, which are summed together to obtain the total profile. Doping regions are specified in a tabular format, with each column representing a different region.

In the one-dimensional example, there are three regions, which are illustrated in figure 14.10. Region 1 is a uniform n-type doping, with a constant magnitude of  $4.0e+12$  donors per cubic cm. This magnitude is set by the parameter `nmax`. As the doping in this region is spatially uniform, the only meaningful parameters are `function` (which in this case specifies a spatially uniform distribution), `type` (n-type or p-type) and `nmax`. The other parameters, `nmin` through `flatx` (1D) or `flaty` (2D), are ignored for a spatially uniform region.

Region 2 is a more complicated region, in that the profile varies with space. This region is doped

```

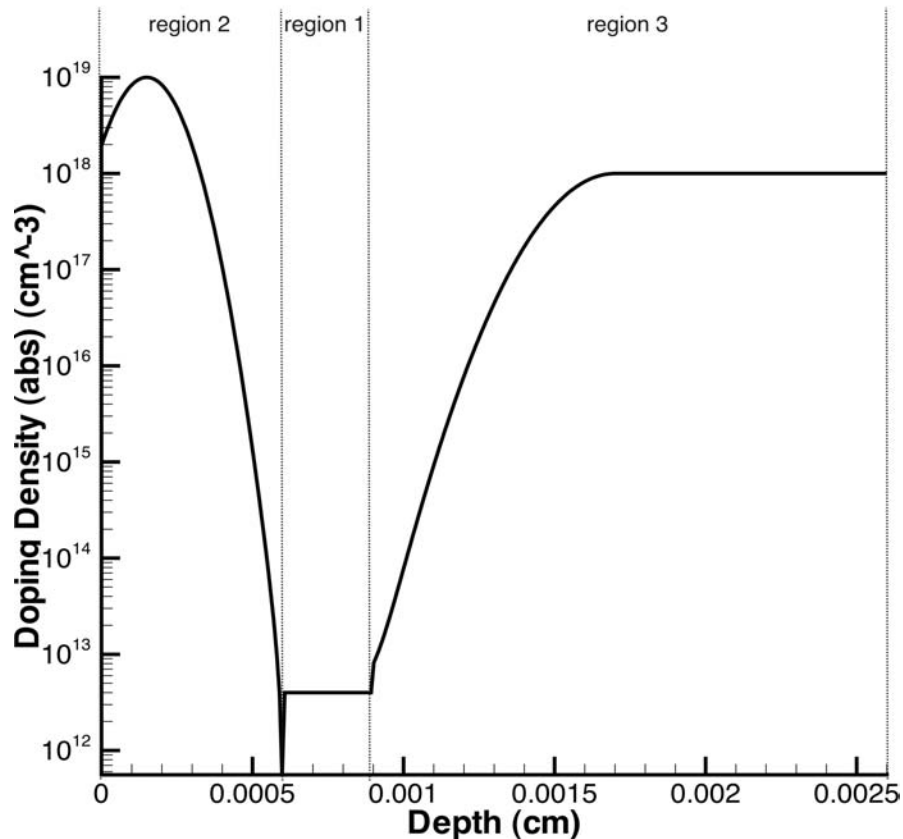
Doping and Electrode specification example
vscope 0 1 0.0
rscope 2 1 50.0
cid 3 0 1.0u
r1 4 3 1515.0
vid 4 0 5.00
YPDE Z1DIODE 2 3 PDEDIODE nx=301 l=26.0e-4
* DOPING REGIONS: region 1, region 2, region 3
+ region= {name = reg1, reg2, reg3
+ function = uniform, gaussian, gaussian
+ type = ntype, ptype, ntype
+ nmax = 4.0e+12, 1.0e+19, 1.0e+18
+ nmin = 0.0e+00, 4.0e+12, 4.0e+12
+ xloc = 0.0 , 24.5e-04, 9.0e-04
+ xwidth = 0.0 , 4.5e-04, 8.0e-04
+ flatx = 0 , 0 , -1 }
*-----end of Diode PDE device -----
.MODEL PDEDIODE ZOD level=1
.options NONLIN maxsearchstep=1 searchmethod=2
.options TIMEINT reltol=1.0e-3 abstol=1.0e-6
.DC vscope 0 0 1
.print DC v(1) v(2) v(3) v(4) I(vscope) I(vid)
.END

```

**Figure 14.9.** One-dimensional example, with detailed doping

with p-type impurities, and has a Gaussian shape. Semiconductor processing often consists of an implant followed by an anneal, which results in a diffusive profile. The Gaussian function is a solution to the diffusion problem, when it is assumed that the impurity exists in a fixed quantity.

The peak of the Region 2 doping profile is given by the parameter  $n_{max}$ , and is  $1.0e+19$  acceptors per cubic cm. This peak has a location in the device specified by  $x_{loc}=24.5e-04$  cm. The parameters  $n_{min}$  and  $x_{width}$  are fitting parameters.



**Figure 14.10.** Doping profile, absolute value  
This corresponds to the doping specified by the netlist in figure 14.9



Region 3 is also based on a Gaussian function, but unlike Region 2, it is flat on one side of the peak. This is set by the  $flatx$  parameter. Table 14.1 lists conventions for “flat” parameters.

Table 14.1: Description of the  $flatx$ ,  $flaty$  doping parameters

$flatx$ or $flaty$ value	Description	1D Cross Section
0	Gaussian on both sides of the peak ( $x_{loc}$ ) location.	



Table 14.1: Description of the flatx, flaty doping parameters

flatx or flaty value	Description	1D Cross Section
+1	Gaussian if $x > x_{loc}$ , flat (constant at the peak value) if $x < x_{loc}$ .	
-1	Gaussian if $x < x_{loc}$ , flat (constant at the peak value) if $x > x_{loc}$ .	

## 14.4.2 Default Doping Profiles

**Xyce** has a few default doping profiles that are invoked when the user doesn't specify detailed doping information. The default doping profiles are an artifact of early TCAD device development in **Xyce**, but are sometimes still useful. In particular, the simple step-junction diode is often a useful canonical problem. It is convenient to invoke a step-junction doping without having to use the more complex region tabular specification.

Most real devices will have doping profiles that do not exactly match the default profiles. When attempting to simulate a realistic device, it will be necessary to skip the defaults and use the region tables described in the previous section.

### One-Dimensional Case

For the one-dimensional case, **Xyce** assumes that the doping profile is a simple junction diode, with the junction location exactly in the middle. The acceptor and donor concentrations are given by the parameters  $N_a$  and  $N_d$ , respectively.

The use of  $N_a$  and  $N_d$ , implicitly specifies a step junction doping profile, and is mutually exclusive with the more complex "doping region" table specification, described in section 14.4.1. If a netlist is input to **Xyce** with a region table and  $N_a$  (or  $N_d$ ), the code will immediately exit with an error.

### Two-Dimensional Case

Doping level defaults in the two-dimensional case are somewhat more complicated than in the one-dimensional case, because having two-dimensions allows for more configurations, and an arbitrary number (2 to 4) of electrodes. During **Xyce** development, it was decided default doping profiles would be determined uniquely by the number of electrodes present. Table 14.2 provides the three available default dopings. In the case of the BJT and MOSFET dopings, it is possible to specify either n-type or p-type using the `type` instance parameter. If the detailed, manual doping is used, then the `type` parameter is ignored.

For a two-electrode device, the default doping is that of a simple diode. **Xyce** uses the acceptor and donor doping parameters,  $N_a$  and  $N_d$ , in the same manner as in the one-dimensional device—the junction is assumed to be exactly in the middle of the domain.

For a three-electrode device (as shown in the example), the default doping is that of a bipolar junction transistor (BJT). By default the transistor is a PNP, but by setting the instance parameter

`type=NPN`, an NPN transistor can be specified instead. The two-dimensional example in section 14.3 relies on this default.

For a four-terminal device, the default doping is that of a metal-oxide-semiconductor (MOSFET). The maximum number of electrodes is four, and no default profiles are available for more than four electrodes. By default this transistor is assumed to be NMOS, rather than PMOS.

Table 14.2: Default doping profiles for different numbers of electrodes

<b>Number of Electrodes</b>	<b>Doping Profile</b>
2	Step Function Diode
3	Bipolar Junction Transistor (BJT)
4	Metal-Oxide Semiconductor Field-Effect Transistor(MOSFET)

## 14.5 Electrodes

Because minimal electrodes were specified in the two examples, **Xyce** used the defaults. In practice, especially for two-dimensional simulations, the user must specify the electrodes in more detail.

### 14.5.1 Electrode Specification

A detailed electrode specification is specified in blue text in figure 14.11. As with the doping parameters, the electrode parameters are specified in a tabular format, in which each table column specifies the different electrode parameters. The `name` parameter is the only required parameter.

The number of specified electrodes must match the number of connected circuit nodes, and the order of the electrode columns, from left to right, is in the same order as the circuit nodes, also from left to right. In the figure 14.11 example, the first electrode column, which specifies an electrode named “anode,” is connected to the circuit through circuit node 2. Respectively, the second column, for the “cathode” electrode, is connected to the circuit via circuit node 3.

#### Boundary Conditions

In the example, the default `bc` parameter has been set to “Dirichlet” on all the electrodes. The `bc` parameter sets the type of boundary condition applied to the density variables, the electron density and the hole density. Dirichlet and Neumann are two possible settings for the `bc` parameter. If Dirichlet is specified, the electron and hole densities are set to a specific value at the contact, and the applied values enforce charge neutrality. See the **Xyce** Reference Guide [3] provides the charge-neutral equation. If Neumann is specified, **Xyce** applies a zero-flux condition, which enforces that the current through the electrode will be zero.

This parameter does not affect the electrostatic potential boundary condition. The boundary condition applied to the potential is always Dirichlet, and is (in part) determined from the connected nodal voltage. To apply a specific voltage to an electrode contact, a voltage source should be attached to it, such as `VBB` in figure 14.5.

#### Electrode Material

Table 14.3 lists several different electrode materials that can be specified. The main effect of any metal (nonneutral) material is that **Xyce** imposes a Schottky barrier at the contact, generally making numerical solutions more difficult, so materials should be applied with caution.

The **Xyce** Reference Guide [3] provides a detailed description of Schottky barriers and how they are imposed on contacts in **Xyce**. The guide also provides values for electron affinities of various bulk materials and workfunction values for the various metal contacts.

```

Doping and electrode specification example
vscope 1 0 0.0
rscope 2 1 50.0
cid 3 0 1.0u
r1 4 3 1515.0
vid 4 0 1.00
*----- Diode PDE device -----
YPDE Z1DIODE 2 3 PDEDIODE
+ tecplotlevel=1 txtdatalevel=1 cyl=1
+ meshfile=internal.msh
+ nx=25 l=70.0e-4 ny=40 w=26.0e-4
* ELECTRODES:          ckt node 2, ckt node 3
+ node = {name        = anode, cathode
+          bc         = dirichlet, dirichlet
+          start      = 0.002, 0.002
+          end        = 0.005, 0.005
+          side       = top, bottom
+          material   = neutral, neutral
+          oxideBndryFlag = 0, 0 }
* DOPING REGIONS:    region 1, region 2, region 3
+ region= {name      = reg1, reg2, reg3
+          function = uniform, gaussian, gaussian
+          type     = ntype, ptype, ntype
+          nmax    = 4.0e+12, 1.0e+19, 1.0e+18
+          nmin    = 0.0e+00, 4.0e+12, 4.0e+12
+          xloc    = 0.0 , 60.0e-04, 100.0
+          xwidth  = 0.0 , 4.0e-04, 1.0
+          yloc    = 0.0 , 24.5e-04, 9.0e-04
+          ywidth  = 0.0 , 4.5e-04, 8.0e-04
+          flatx   = 0 , -1 , -1
+          flaty   = 0 , 0 , -1 }
*-----end of Diode PDE device -----
.MODEL PDEDIODE ZOD level=2
.options NONLIN maxsearchstep=1 searchmethod=2
.options TIMEINT reltol=1.0e-3 abstol=1.0e-6
.DC vscope 0 0 1
.print DC v(1) v(2) v(3) v(4) I(vscope) I(vid)
.END

```

**Figure 14.11.** Two-dimensional example, with detailed doping and detailed electrodes.

Table 14.3: Electrode Material Options. NOTE: Neutral contacts are the default, and pose the least problem to the solvers.

Material	Symbol	Comments
neutral	neutral	Default
aluminum	al	
p+-polysilicon	ppoly	
n+-polysilicon	npoly	
molybdenum	mo	
tungsten	w	
molybdenum disilicide	modi	
tungsten disilicide	wdi	
copper	cu	
platinum	pt	
gold	au	

There is also an `oxideBndryFlag` parameter, which if set to true (1), will model the contact as having an oxide layer in between the metal contact and the bulk semiconductor. By default, `oxideBndryFlag` is false (0).

## Location Parameters

Each electrode has three location parameters: `start`, `end`, and `side`.

**Xyce** assumes the internal mesh to be rectangular, with electrodes on any of the sides. The four side possibilities are: `top`, `bottom`, `right` and `left`. These four sides are parallel to mesh directions. The `start` and `end` parameters are floating-point numbers that specify the starting and ending location of an electrode, in centimeters.

The lower left hand corner of the mesh rectangle is located at the origin. A `side=bottom` electrode with `start=0.0` and `end=1.0e-4` will originate at the lower left hand corner of the mesh ( $x=0.0$ ,  $y=0.0$ ) and end at ( $x=1.0e-4$ ,  $y=0.0$ ).

**Xyce** will attempt to match the specified electrode to the specified mesh. However, if the user specifies a mesh that is not consistent with the electrode locations, the electrodes will not be able to have the exact length specified. For example, if the mesh spacing is  $\Delta x = 1.0e-5$ , then the electrodes can only have a length that is a multiple of  $1.0e-5$ .

## 14.5.2 Electrode Defaults

Defaults exist for each electrode parameter other than names. In practice, the electrode locations are usually explicitly specified using the electrode table. Default electrode locations were created to correspond with the default dopings; they should only be used in that context.

## Location Parameters

In practice, the electrode locations will usually be explicitly specified, but they have defaults to correspond with the default dopings. The default electrode locations in one-dimensional devices are for a diode. One electrode is located at  $x=x_{\min}$ , while the other is located at  $x=x_{\max}$ .

The default electrode locations in two-dimensional devices depend on the number of electrodes, similar to the default dopings. Table 14.2 can be used to determine such configurations. For the two-terminal diode, the two electrodes are along the  $y$ -axis, at the  $x=x_{\min}$  and  $x=x_{\max}$  extrema. For the three-terminal BJT, all three electrodes are parallel to the  $x$ -axis, along the top, at  $y=y_{\max}$ . For the four-terminal MOSFET, the drain, gate, and source electrodes are also along the top, but the bulk electrode spans the entire length of the bottom of the mesh, at  $y=y_{\min}$ .

## 14.6 Meshes

One- and two-dimensional devices can create Cartesian meshes. For two-dimensional devices, users must specify `meshfile=internal.msh` to invoke the Cartesian meshing capability (this is necessary for historical reasons). Meshes generated in this manner are very simple as there are only two parameters per dimension, and the resulting mesh is uniform. Figure 14.6 provides an example of such a mesh. Mesh spacing is determined from the following expressions:

$$\Delta x = \frac{l}{nx - 1} \quad (14.8)$$

$$\Delta y = \frac{w}{ny - 1} \quad (14.9)$$

This mesh specification assumes the domain is a rectangle. Nonrectangular domains can only be described using an external mesh program. However, externally-generated meshes are not currently supported.

## 14.7 Cylindrical meshes

For two-dimensional devices, the simulation area may be a cylinder slice. This capability is turned on by the instance parameter `cy1=1`. It is assumed that the axis of the cylinder corresponds to the minimum radius (or  $x$ -axis value) of the mesh, while the circumference corresponds to the maximum radius (or maximum  $x$ -axis value).

## 14.8 Mobility Models

There are several mobility models available to the one- and two-dimensional devices, and they are listed in Table 14.4. These models are fairly common, and can be found in most device simulators. [23] [24]. The **Xyce** Reference Guide [3] describes these models in more detail.

Table 14.4: Mobility models available for PDE devices

Mobility Name	Description	Reference
arora	Basic mobility model	Arora, et al. [29]
analytic or caughey-thomas	Basic mobility model	Caughy and Thomas [30]
carr	Includes carrier-carrier interactions	Dorkel and Leturq [31]
philips	Philips model	Klassen [32, 33]

Setting the `mobmodel` parameter to the name of the model (as provided in the first column of table 14.4) specifies the mobility model from the netlist. The mobility model is specified as an instance parameter on the device instance line, as (typically) `mobmodel=arora`. Figure 14.4 provides a more detailed example.

The default mobility is “arora”, which is a basic model lacking carrier or field dependence. Because it lacks these dependencies, it generally is more numerically robust. The “carr” model include carrier-carrier dependence, as does the “philips” model. For all of these models, field dependence can be optionally turned on from the netlist, using the `fielddep=true` parameter.

## 14.9 Bulk Materials

The bulk material is specified using the `bulkmaterial` instance parameter. **Xyce** supports Silicon (`si`) as a default bulk material. It can also simulate several III-V materials, including Gallium Arsenide (`gaas`), Germanium (`ge`), Indium Aluminum Arsenide (`inalas` or `alinas`) Indium Galium Arsenide (`ingaas` or `gainas`), Indium Phosphide (`inp`), and Indium Galium Phosphide (`ingap`); but these materials have not been extensively tested. The mobility models described in the previous section each support most of these materials.

## 14.10 Output and Visualization

### 14.10.1 Using the .PRINT Command

For simple plots (such as I-V curves), output results for **Xyce** can be generated with the `.PRINT` statement, which is described in detail in section 9.1.1. Figures 14.3 and 14.8 are examples of the kind of data that is produced with `.PRINT` statement netlist commands. These particular figures were plotted in Tecplot, but many other plotting programs would also have worked, including XDAMP [34].

### 14.10.2 Multidimensional Plots

Device simulation has visualization needs which go beyond that of conventional circuit simulation. Multidimensional perspective and/or contour plots are often desirable. **Xyce** is capable of out-

putting multi-dimensional plot data in several formats, including Tecplot (available for purchase from <http://www.tecplot.com>), gnuplot (available free from <http://www.gnuplot.info>), and Sgplot. Currently, the options for each of these formats can only enable or disable the output of files, and when enabled, a new file (or a new append to an existing file) will happen at every time step or DC sweep step.

For long simulations, this may produce a prohibitive number of files. Currently, there is no equivalent to the `.OPTIONS OUTPUT INITIAL_INTERVAL` command, nor does the output of plot data currently use this command. Plot files are either output at every step or not at all.

For each type of plot file, the file is placed in the execution directory. Each individual device instance is given a unique file, or files, and the file names are derived from the name of the PDE device instance. The instance names provides the prefix, and the file type (Tecplot, gnuplot, Sgplot) determines the suffix.

## Tecplot Data

Tecplot is a commercial plotting program from Amtec Engineering, Inc., and is the best choice for creating contour plots of spatially dependent data. All of the graphical examples in this chapter were created with Tecplot. (see figures 14.6 and 14.7 for examples) The output of Tecplot files is enabled using the instance parameter, `tecplotlevel=1`. If set to zero, no Tecplot files are output. If set to one, **Xyce** outputs a separate Tecplot file for each nonlinear solve. If set to two, **Xyce** creates a single Tecplot file containing data for every nonlinear solve and appends the file at the end of each solve.

By default `tecplotlevel` is set to one, meaning the code will produce a separate Tecplot file for each time step or DC sweep step. The suffix for a Tecplot (ASCII text) data file is `*.dat`.

## Gnuplot Data

Gnuplot is an open source plotting program available on most Linux/Unix platforms. The parameter for this type of output is `gnuplotlevel=1`. This type of output file is off (zero) by default, meaning no gnuplot files will be output. The suffix for gnuplot files is `*gnu.dat`. Like Tecplot files, gnuplot files are also in ASCII text format.

## 14.10.3 Additional Text Data

**Xyce** can also output additional information for each PDE device by setting the instance parameter, `txtdatalevel=1`. It is on (1) by default, so this output will happen unless specifically disabled by setting the parameter to zero. A typical output file (associated with the netlist given in figure 14.4) is shown in figure 14.12.



```
Global data for DC step 1:
Current Time = 0.0000e+00
  Vmin = -8.6931e-06
  Vmax = 5.4030e-01
  NnMin = 0.0000e+00
  NnMax = 1.0000e+16
  NpMin = 3.9240e+03
  NpMax = 1.0000e+19

Information for electrode: COLLECTOR
potential: 2.9795e-01
  current: 8.5365e-06
  charge: -6.6211e-15
  dIdVckt: 3.7993e-02
  dQdVckt: 0.0000e+00

Information for electrode: BASE
potential: 5.4030e-01
  current: -8.5408e-06
  charge: 1.5958e-14
  dIdVckt: 1.0463e+01
  dQdVckt: 0.0000e+00

Information for electrode: EMITTER
potential: -8.6931e-06
  current: 4.3465e-09
  charge: -2.3232e-13
  dIdVckt: 7.2130e+01
  dQdVckt: 0.0000e+00
```

**Figure 14.12.** Text output, from the circuit given in figure 14.4.



## References

- [1] Laurence Nagel and Ronald Rohrer. Computer analysis of nonlinear circuits, excluding radiation (cancer). *IEEE Journal of Solid-State Circuits*, sc-6(4):166–182, 1971.
- [2] Tom Quarles. Spice3f5 users' guide. Technical report, University of California-Berkeley, Berkeley, California, 1994.
- [3] Eric R. Keiter, Thomas V. Russo, Ting Mei, Eric L. Rankin, Roger P. Pawlowski, Richard L. Schiek, Keith R. Santarelli, Todd S. Coffey, Heidi K. Thornquist, Jason C. Verley, Christina E. Warrender, and Deborah A. Fixel. Xyce parallel electronic simulator: Reference guide, version 6.0. Technical Report SAND2013-XXXX, Sandia National Laboratories, Albuquerque, NM, 2013.
- [4] Orcad PSpice User's Guide. Technical report, Orcad, Inc., 1998.
- [5] *gEDA Project Home Page*.  
<http://www.geda.seul.org/> .
- [6] A. S. Grove. *Physics and Technology of Semiconductor Devices*. John Wiley and Sons, Inc., 1967.
- [7] H. A. Watts, E. R. Keiter, S. A. Hutchinson, and R. J. Hoekstra. Time integration for the Xyce parallel electronic simulator. In *ISCAS 01*, October 2000.
- [8] K.E. Brenan, S.L Campbell, and L.R. Petzold. *Numerical Solution of Initial-Value Problems in Differential-Algebraic Equations*. Society for Industrial and Applied Mathematics, Philadelphia, 1996.
- [9] Ljiljuna Trujkovic, Robert C. Melville, and Sun-Chin Fang. Passivity and no-gain properties establish global convergence of a homotopy method for dc operating points. *Proceedings - IEEE International Symposium on Circuits and Systems*, 2:914–917, 1990.
- [10] Robert C. Melville, Ljiljana Trajkovic, San-Chin Fang, and Layne T. Watson. Artificial parameter homotopy methods for the dc operating point problem. *IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems*, 12(6):861–877, 1993.
- [11] J. Roychowdhury. *Private Communication*, 2003.
- [12] Eric R. Keiter, Heidi K. Thornquist, Robert J. Hoekstra, Thomas V. Russo, Richard L. Schiek, and Eric L. Rankin. Parallel transistor-level circuit simulation. In Peng Li, Lus Miguel Silveira, and Peter Feldmann, editors, *Simulation and Verification of Electronic and Biological Systems*, pages 1–21. Springer Netherlands, 2011. 10.1007/978-94-007-0149-6\_1.

- [13] M. Heroux, et. al. An overview of the Trilinos project. *ACM TOMS*, 31(3):397–423, 2005. <http://trilinos.sandia.gov>.
- [14] Y. Saad and M. H. Schultz. GMRES: a generalized minimal residual algorithm for solving nonsymmetric linear systems. 7(3):856–869, 1986.
- [15] Y. Saad. *Iterative Methods for Sparse Linear Systems*. SIAM, Philadelphia, PA., second edition, 2003.
- [16] Heidi K. Thornquist, Eric R. Keiter, Robert J. Hoekstra, David M. Day, and Erik G. Boman. A parallel preconditioning strategy for efficient transistor-level circuit simulation. In *ICCAD '09: Proceedings of the 2009 International Conference on Computer-Aided Design*, pages 410–417, New York, NY, USA, 2009. ACM.
- [17] S. Rajamanickam, E.G. Boman, and M.A. Heroux. ShyLU: A hybrid-hybrid solver for multicore platforms. In *Parallel Distributed Processing Symposium (IPDPS), 2012 IEEE 26th International*, pages 631 –643, may 2012.
- [18] C. Bomhof and H. vanderVorst. A parallel linear system solver for circuit simulation problems. *Num. Lin. Alg. Appl.*, 7(7-8):649–665, 2000.
- [19] Erik Boman, Karen Device, Robert Heaphy, Bruce Hendrickson, William F. Mitchell, Matthew St. John, and Courtenay Vaughan. *Zoltan: Data-Management Services for Parallel Applications:User's Guide*. <http://www.cs.sandia.gov/zoltan>, 2004.
- [20] Eric R. Keiter, Scott A. Hutchinson, Robert J. Hoekstra, Eric L. Rankin, Thomas V. Russo, and Lon J. Waters. Computational algorithms for device-circuit coupling. Technical Report SAND2003-0080, Sandia National Laboratories, Albuquerque, NM, January 2003.
- [21] Kartikeya Mayaram and Donald O. Pederson. Coupling algorithms for mixed-level circuit and device simulation. *IEEE Transactions on Computer Aided Design*, 11(8):1003–1012, 1992.
- [22] David A. Johns and Ken Martin. *Analog Integrated Circuit Design*. John Wiley & Sons, Inc., 1997.
- [23] Z. Yu, D. CHen, L. So, and R. W. Dutton. Pisces-2et-two dimensional device simulation for silicon and heterostructures. Technical report, Stanford University, 1994.
- [24] Davinci User's Manual. Technical report, TCAD Business Unit, Avanti! Corporation, 1998.
- [25] *Charon Device Simulator*. <http://micro.sandia.gov/charon.html>.
- [26] Kevin M. Kramer and W. Nicholas G. Hitchon. *Semiconductor Devices: A Simulation Approach*. Prentice-Hall, Upper Saddle River, New Jersey, 1997.
- [27] S. Selberherr. *Analysis and Simulation of Semiconductor Devices*. Springer-Verlag, New York, 1984.
- [28] Eric R. Keiter, Scott A. Hutchinson, Robert J. Hoekstra, Eric L. Rankin, Thomas V. Russo, and Lon J. Waters. Computational algorithms for device-circuit coupling. Technical Report SAND2003-0080, Sandia National Laboratories, Albuquerque, NM, January 2003.

- [29] N.D. Arora, J.R. Hauser, and D.J. Roulston. Electron and hole mobilities in silicon as a function of concentration and temperature. *IEEE Transactions on Electron Devices*, ED-29:292–295, 1982.
- [30] D.M. Caughey and R.E. Thomas. Carrier mobilities in silicon empirically related to doping and field. *Proc. IEEE*, 55:2192–2193, 1967.
- [31] J.M. Dorkel and Ph. Leturq. Carrier mobilities in silicon semi-empirically related to temperature, doping, and injection level. *Solid-State Electronics*, 24(9):821–825, 1981.
- [32] D.B.M. Klaassen. A unified mobility model for device simulation - i. *Solid State Electronics*, 35:953–959, 1992.
- [33] D.B.M. Klaassen. A unified mobility model for device simulation - ii. *Solid State Electronics*, 35:961–967, 1992.
- [34] *XDAMP Graphical User Interface*. <http://www.cs.sandia.gov/esimtools/xdamp.html> .



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